TEXAS INSTRUMENTS INCORPORATED
Apparatus Division
13500 North Central Expressway
Dallas, Texas

FINAL ENGINEERING REPORT

INTEGRATED CIRCUIT SEQUENCE GENERATOR

8-66348-Final

JPL Contract No. 950693

25 June 1964

This work was performed for the Jet Propulsion Laboratory, California Indicate of Technology, sponsored by the National Aeronautics and Space Administration under Contract NAS7-100.

Prepared for Jet Propulsion Laboratory California Institute of Technology Pasadena, California

, of 154

# TABLE OF CONTENTS

Section	Title	Page
ı.	INTRODUCTION	1
II.	PLANETARY RANGING SYSTEM DISCUSSION	3
	A. General	3 3
III.	SYSTEM DESCRIPTION	7
	A. General.  B. Electrical  1. SOLID CIRCUIT® Semiconductor Networks  2. Subsystem Description  3. Subsystem Specifications.  C. Mechanical  1. General  2. 1X Modules  3. 2X Modules  4. Connector Assembly  5. Subsystem Assembly	7 7 7 13 13 29 29 30 30 30 30
IV.	PROGRAM HISTORY	37
<b>v.</b>	TESTING AND CALIBRATION	39
VI.	RECOMMENDATIONS	41
	A. Electrical	41 43
VII.	CONCLUSION	47
	APPENDIX	
	<ul> <li>A. Specification Index</li> <li>B. Drawing Index</li> <li>C. Network Reliability</li> <li>D. Network Applications</li> <li>E. Test Procedures</li> </ul>	

# LIST OF ILLUSTRATIONS

Figure	Title	Page
1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15. 16. 17. 18.	Integrated Circuit Sequence Generator - Top View	2 8 9 14 15 17 19 21 22 23 24 25 27 31 31 33 45
	LIST OF TABLES	_
Table	Title	Pag
I. II. IV.	Code-Component Generation	10 11 12 35

# TEXAS INSTRUMENTS INCORPORATED Apparatus Division 13500 North Central Expressway Dallas, Texas

25 June 1964

# FINAL ENGINEERING REPORT INTEGRATED CIRCUIT SEQUENCE GENERATOR

#### 8-66348-Final

References:

- (a) Texas Instruments Proposal No. A63-109, dated 13 May 1963
- (b) Jet Propulsion Laboratory Contract No. 950693, dated 26 September 1963

#### SECTION I

# INTRODUCTION

Texas Instruments has delivered an Integrated Circuit Sequence Generator to Jet Propulsion Laboratory in accordance with References (a) and (b). The sequence generator described in JPL Design Specification Number 31243 was designed and built using only integrated circuits. The specification relating to this effort is shown in Appendix A. The primary design objective was to minimize the size and weight of the system while maintaining an economical throw-away level. The module configuration conforms to the standard Mariner B modules which makes it compatible with discrete components.

Texas Instruments has fabricated the integrated circuit sequence generator subsystem using the Series 53 SOLID CIRCUIT® semiconductor networks as logic building blocks. This approach has resulted in a subsystem of minimum size and weight. In addition, Texas Instruments has taken full advantage of past experience in the design, development and application of the SOLID CIRCUIT networks to supply a sequence generator with high reliability and minimum power consumption. Figures 1 and 2 show the complete subsystem.

This report is the Final Engineering Report required by the contract and has been written in accordance with JPL General Specification Number 20017.

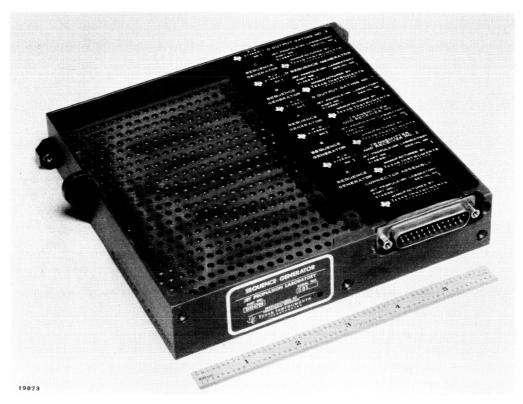


Figure 1. Integrated Circuit Sequence Generator - Top View



Figure 2. Integrated Circuit Sequence Generator - Bottom View

# SECTION II

# PLANETARY RANGING SYSTEM DISCUSSION

#### A. General

Prior to the description of the Integrated Circuit Sequence Generator, the problem of long-distance ranging will be discussed. This will serve as a foundation for the abbreviated discussion of the subsystem details that follow.

# B. Long-Distance Ranging Problem

The conventional method of determining distance to a target or object is one using radar apparatus in which a pulse of rf energy is transmitted, and the round-trip time T for the reflected pulse is measured, converted to range units, and displayed. The range is computed according to the equation

r = Tc/2

where c is the radio propagation velocity in the medium.

A problem arises, however, when the returned signal drops below the threshold of detectability; therefore, some means of increasing the energy of the transmitted (and received) pulse must be devised in order to increase the maximum range capability of the system. Several possibilities are:

- 1. Increasing the peak power of the transmitter
- 2. Increasing the pulsewidth
- 3. Increasing the prf and correlate over a number of pulses
- 4. Using a higher gain antenna
- 5. Installing a transponder on the vehicle being ranged.

Some of these approaches will alter the performance of the system. For example, the second alternative (longer pulsewidth) will reduce the range-resolution capability of the system in general (an exception will be discussed later). Increasing the pulse repetition rate (prf) and correlating would provide a considerable improvement in the detection of weak signals from relatively longer ranges; however, since range ambiguity is a function of c/prf, then a means of tracking (a priori information) must be used to establish the correct range category.

The chief alternative to the basic method discussed previously is one called a coded-pulse system, which takes advantage of certain desirable correlation properties of the transmitted signal. In fact, at certain extremely long distances in our planetary system, it appears that there may be no alternative to ranging other than a coded-pulse system of the type to be discussed. The coded-pulse radar or ranging system accomplishes a greater range by using alternative 2 in the following manner:\* A longer pulse is transmitted which is made

<sup>\*</sup>A transponder is also used.

up of many shorter pulses coded (e.g., in binary fashion) in such a way that when the received pulse arrives at the receiver, the out-of-phase correlation with a locally generated (or stored) version of the code maintains a relatively stable, low mean value in comparison with the in-phase correlation which produces a maximum value. The peak is used to mark the arrival of the return pulse and may be resolved easily within a fraction of the time period of a single bit of the code. Thus, the usual compromise with range resolution in using a longer pulsewidth is avoided.

In the system developed at JPL, the coded-pulse ranging signal is transmitted continuously so that the range ambiguity of the system is a function of the time period of the code. In short, the code-repetition rate is similar to the pulse-repetition rate in a conventional radar in defining the range ambiguity of the system. To increase the maximum unambiguous range  $r_{\text{max}}$  capability of the system, the code period P must be increased as indicated in the following equation:

 $r_{max} = (1/2)Pct$ 

where

P = the period of the code in symbols or bits

c = the propagation velocity

t = the symbol or bit period.

The range accuracy  $r_a$  of the system is a function primarily of the code symbol or bit period (i.e., bandwidth) input signal-to-noise ratio and the integration time constant in the correlation detector (for vernier resolution).\* For greater range accuracy, the code or bit period must be reduced, and/or the effective signal-to-noise ratio must be increased.

As in all systems which offer solutions to major problems, other problems may arise; in the coded ranging system, the primary problem ordinarily is one of acquiring the received code. In particular, this is a problem when it must be done in real time and in a relatively short period of time. In theory, to mark one symbol out of P symbols requires only logoP information bits. For example, ten information bits define unambiguously any one of 1024 symbols, provided the ten information bits are without error. Since the received signal is degraded by noise, it would be unrealistic to expect that logoP bits would be received without error with a high probability; hence, some means of error correction of the received bits would be necessary to recover accurately log2P bits. Presently, no simple or relatively straightforward technique is known to do this with a reasonable amount of equipment. On the other hand (and at the other extreme), the received code could be acquired by exhaustive trial correlation of each bit or symbol position of the sequence. Each trial would consist of comparing the locally generated code with the received code from which the clock rate has been recovered for driving the local code generator. This comparison or correlation is performed for a period of time depending on the signal-to-noise ratio and desired confidence level, both of which specify the time interval of the correlator integrator; then the output of the integrator is sampled to determine whether the requisite threshold has been exceeded. If not exceeded, the

<sup>\*</sup>The signal-to-noise ratio is increased (effectively) by increasing the integrator time constant; thus, the two are related.

next trial consists of shifting the phase of the locally generated code by one bit (with reference to the received code) and repeating the process just described. A scanning operation is, thereby, performed until the correct phase is determined, at which time the output of the integrator will exceed the predetermined threshold and the received code will have been acquired. To maintain track or, in other words, to produce a continuous readout of the range, it is necessary to continue to step the local code generator at the same clock rate as that of the received code by using a clock phase-locked loop in the receiver. The range is directly proportional to the displacement, in bit periods, between the transmitter and receiver code by using a clock phase-locked loop in the receiver. The range is directly proportional to the displacement, in bit periods, between the transmitter and receiver code generators.

To show how impractical such an exhaustive trial process would be, consider the following example. The coded sequence is 1.435 billion bits long, which is adequate for unambiguous ranging up to approximately 133.4 million miles at a megabit transmitter rate; the time constant in the integrator is 1 second, and a sampling or scanning interval of 1 second is used (thus, the signal is correlated over an interval of 1 million bits). In the worst possible case (no a priori range information), it would take 45.5 years, or an average of 22.75 years, to acquire this sequence.

A means of avoiding this exhaustive trial process is mandatory. An excellent alternative devised by communications systems research scientists at JPL is summarized briefly in the following list.  $^{1,2,3}$ 

1. Select j sequences (code components) with the desired ideal or two-level autocorrelation function (maximal-length shift register generator sequences and Legendre sequences) of length p<sub>i</sub> such that each p<sub>i</sub> is relatively prime to all the others and such that the following inequality is satisfied:

$$P_i P_2 \cdots P_j = \prod_{i=1}^j p_i \ge P$$

where P is the minimum code period required to achieve a specified maximum unambiguous range. Since each of the j sequences is relatively prime to every other, a composite sequence will have a period equal to the product of the individual periods of the j sequences (least-common multiple). In addition, it is best if each pi is as close as possible to the jth root of P.4

<sup>1</sup> S.W. Golomb, "Deep Space Range Measurement," Research Summary, No. 36-1 (JPL, 15 February 1960).

<sup>2</sup> M. Easterling, "Acquisition Ranging Codes and Noise," Research Summary, No. 36-2 (JPL, 15 April 1960).

<sup>3 &</sup>quot;A Long Range Precision Ranging System," Technical Report No. 32-80 (JPL,10 July 1961)

<sup>4</sup> R.C.Titsworth, "Optimal Ranging Codes," <u>Technical Report No. 32-411</u> (JPL,15 April 1963).

2. By suitable combination of these sequences bit-by-bit (preferably majority logic), it is relatively simple for the receiver to acquire the phasing on each one independently by correlating it with the received composite sequence and determining the shift position which produced the highest correlation integral. Therefore, the entire combined sequence is acquired (with a nominal S/N) in no more than N trials where N is defined by

$$N = p_1 + p_2 + \cdots + p_j = \sum_{i=1}^{j} p_i$$

In the case of the coded sequence used in a planetary ranging system which contains 1.435 billion bits, N represents 304 trials (2+7+11+23+31+103+127), or about 5 minutes at most using a 1-second integration period per trial.

# SECTION III

# SYSTEM DESCRIPTION

# A. General

The integrated circuit sequence generator is an integral part of the complete ranging system. The function of the subsystem, described by Figure 3, is to generate the long binary codes mentioned in the previous section. In the following paragraphs, the electrical and mechanical characteristics will be discussed briefly since the basic design and been accomplished by JPL. The drawing index, Appendix B, gives a complete listing of all the drawings generated during this program.

#### B. Electrical

The subsystem generates six pseudorandom codes with feedback shift registers as shown in Figure 4 and Table I. The period lengths and symbol sequences of the six codes are listed in Table II. These pseudorandom codes are combined as shown in Table IIIA and IIIB. The three modes of operation of the subsystem are dictated by the acquisition (Ac) and correlation (Co) variables which are also included in Table IIIA and IIIB.

# 1. SOLID CIRCUIT Semiconductor Networks

The Series 53 SOLID CIRCUIT semiconductor networks are similar to the more familiar Series 51. The Series 53 networks were designed specifically for operation at clock frequencies to 3 megacycles. This increase in speed was accompanied by a proportional increase in power. However, the sequence generator described by this report will require a maximum of 2.1 watts. All of the logic functions described in the design specification have been implemented using the Series 53 SOLID CIRCUIT in the NAND/NOR configuration. This configuration requires only one positive supply voltage, whereas the AND/OR configuration requires an additional negative supply voltage.

With the J-K Flip-Flop SN530, no inverter is required for steering since both the normal and the complimentary inputs are available. This results in a savings in power and circuitry. The other logic implementation is straightforward.

All six types of networks were used in the sequence generator. SN531 and SN533 NAND Gates were used for all feedback and combination logic. The SN535 was used for the clock driver and inverter. SN532 and SN534 AND Gates were used for word detector logic. In addition, the SN532 was used to increase the fan-in of SN531.

Reliability data on the SOLID CIRCUIT semiconductor networks is presented in Appendix C. This data is applicable to the Series 53 as well as the Series 51.

In July, the Series 53 application report will be published and will be forwarded to be included as Appendix D.

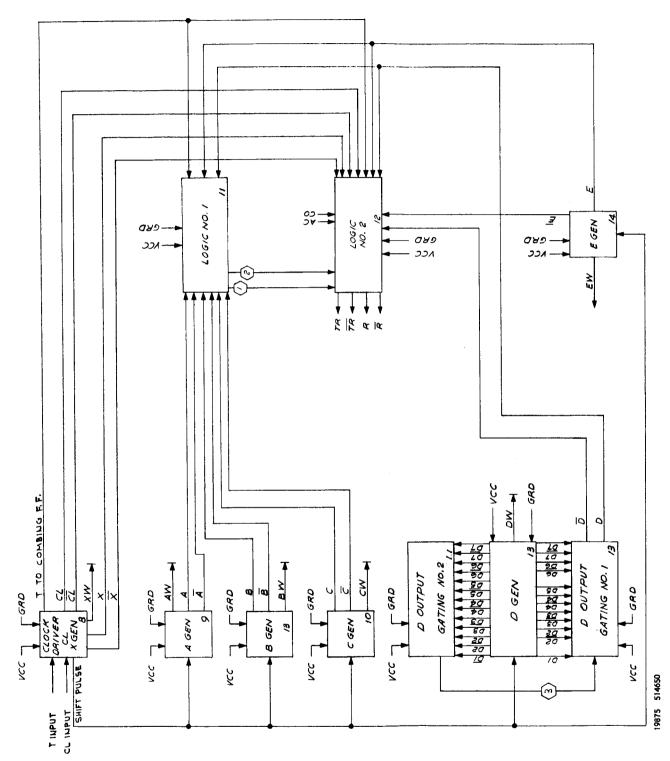


Figure 3. Block Diagram - Integrated Circuit Sequence Generator

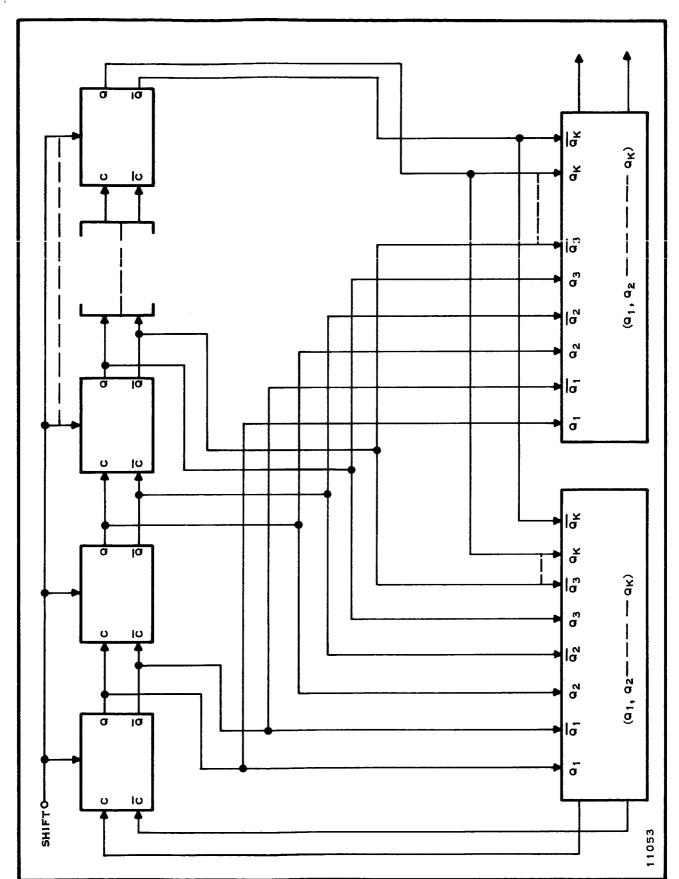


Figure 4. Code-Component Generator

Table I. Code-Component Generation

Code Component	*	Feedback f ( )	Output g ( )
×	3	$x_1\bar{x}_3 + \bar{x}_1x_3 + \bar{x}_1\bar{x}_2$	
4	'n	$\bar{A}_1\bar{A}_4 + \bar{A}_2\bar{A}_5 + \bar{A}_3A_4A_5$	
Д	~	$B_3B_5\bar{B}_6 + \bar{B}_3B_4\bar{B}_5 + B_1B_4B_6 +$	$+ B_1 B_4 B_6 + B_1 B_5 \overline{B}_7 + \overline{B}_5 B_6 B_7$
v	r.	$c_2\bar{c}_5 + \bar{c}_2c_5 + \bar{c}_1\bar{c}_2\bar{c}_3\bar{c}_4$	
Д	2	$D_6\bar{D}_7 + \bar{D}_6D_7 + \bar{D}_1\bar{D}_2\bar{D}_3\bar{D}_5\bar{D}_6$	$D_{1}\bar{D}_{2}\bar{D}_{3}\bar{D}_{4}D_{5}+D_{1}D_{2}D_{3}\bar{D}_{4}\bar{D}_{6}+D_{1}\bar{D}_{2}D_{3}\bar{D}_{6}\bar{D}_{7}+D_{1}D_{2}D_{3}D_{5}D_{7}$
			$+\bar{D}_{1}\bar{D}_{2}\bar{D}_{3}D_{4}+\bar{D}_{2}\bar{D}_{4}D_{6}\bar{D}_{7}+\bar{D}_{1}\bar{D}_{2}D_{4}\bar{D}_{6}D_{7}+\bar{D}_{1}D_{2}D_{3}\bar{D}_{4}D_{6}\\ +D_{2}\bar{D}_{3}\bar{D}_{4}D_{5}D_{7}+\bar{D}_{1}\bar{D}_{2}\bar{D}_{4}\bar{D}_{5}D_{7}+\bar{D}_{1}\bar{D}_{3}D_{4}\bar{D}_{7}+\bar{D}_{2}D_{5}D_{6}\bar{D}_{7}$
			$+\bar{\mathbf{D}}_{1}\mathbf{D}_{2}\mathbf{D}_{4}\bar{\mathbf{D}}_{5}\mathbf{D}_{7}+\bar{\mathbf{D}}_{1}\bar{\mathbf{D}}_{3}\mathbf{D}_{5}\bar{\mathbf{D}}_{6}\bar{\mathbf{D}}_{7}+\mathbf{D}_{2}\bar{\mathbf{D}}_{3}\mathbf{D}_{4}\mathbf{D}_{5}\bar{\mathbf{D}}_{6}\bar{\mathbf{D}}_{7}$
			$+D_3D_5D_6\overline{D}_7+\overline{D}_1D_4\overline{D}_5\overline{D}_6+\overline{D}_3\overline{D}_4\overline{D}_5D_6$
ы	9	$E_1\bar{E}_7 + \bar{E}_1E_7$	
		$+\bar{\mathbf{E}}_{1}\bar{\mathbf{E}}_{2}\bar{\mathbf{E}}_{3}\bar{\mathbf{E}}_{4}\bar{\mathbf{E}}_{5}\bar{\mathbf{E}}_{6}$	
	·		
	<del> </del>		

Table II. Code-Component Definition

Code	Length	Binary Sequence
$c_1$	2	01
×	7	1110100
Ą	11	11100010110
Д	23	111110101100110010
υ	31	11111001101100100001010111011000
Q	103	0110100111000111111110001011101110111011010
		110110101000100010010111000000011100011010
ப	127	000000111111101010100110011101110111011101111
		001000111000010111100101111001110011110001111

# Table III. Combinational Logic

Table IIIa. Receiver and Transmitter Code Combinations

Output	Code Combination
Receiver	$A \oplus B \oplus C \oplus D \oplus E \oplus X$
Transmitter	$X \cdot C1 + \overline{X} [G(A, B, C, D, E) \oplus C1]$

Table IIIb. G (A, B, C, D, E) Vs. Control State

Mode	Control State	G (A, B, C, D, E)
1	A <sub>c</sub>	0
2	A <sub>c</sub> C <sub>o</sub>	ABC + ABD + ABE + ACD
		+ ACE + ADE + BCD + BCE
		+ BDE + CDE
3	A <sub>c</sub> C <sub>o</sub>	A $\oplus$ B $\oplus$ C $\oplus$ D $\oplus$ E

# 2. Subsystem Description

# a. Clock Shaper and Driver

The clock shaper and driver is composed of two inverter circuits tied in parallel and feeding into three additional inverters in parallel. The output of these three inverters is common to each of the code-component generators. The output of the two parallel inverters is used to clock the combining logic flip-flops. These clock inverters are physically located in the X Sequence Generator Module along with the CL Flip-Flop. The logic diagram for this module is shown in Figure 5.

# b. Code-Component Generators

The maximal-length sequences X, C and E are generated with linear feedback. Legende sequences A and B are generated with non-linear feedback which derives the output from the shift register. The Legende sequence D is generated indirectly by short-cycling the linear feedback and deriving the output with combination logic. The logic diagrams of the code generators are shown in Figures 5, 6, 7, 8, 9, 10, 11 and 12.

Investigation has shown that this logic design requires the minimum total circuitry which insures maximum reliability. The number of shift registers in generators A and B may be reduced, but an increase in feedback logic is required; hence, no gain would be realized.

# c. Code-Component Combiners

The code-component combiners, Figures 13 and 14, are designed to require a minimum number of Series 53 SOLID CIRCUIT building blocks. Tables IIIA and IIIB show the code combination generated in each of the three modes of operation.

# d. Output Timing

To insure that the code outputs are in phase with the system timing, the final code combination is followed by flip-flops which are clocked by the input timing.

# 3. Subsystem Specifications

The sequence generator will meet or exceed the following specifications:

# a. Timing Input

Square 50% duty cyc:	Le
lmc nominal	
+3 volts	
Ground	
<1K ohm	
	+3 volts Ground

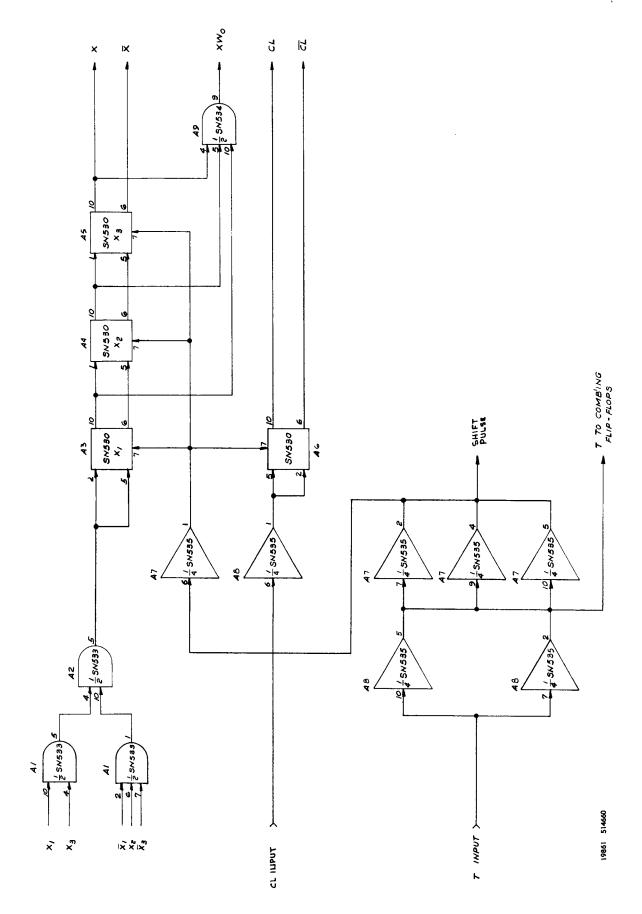
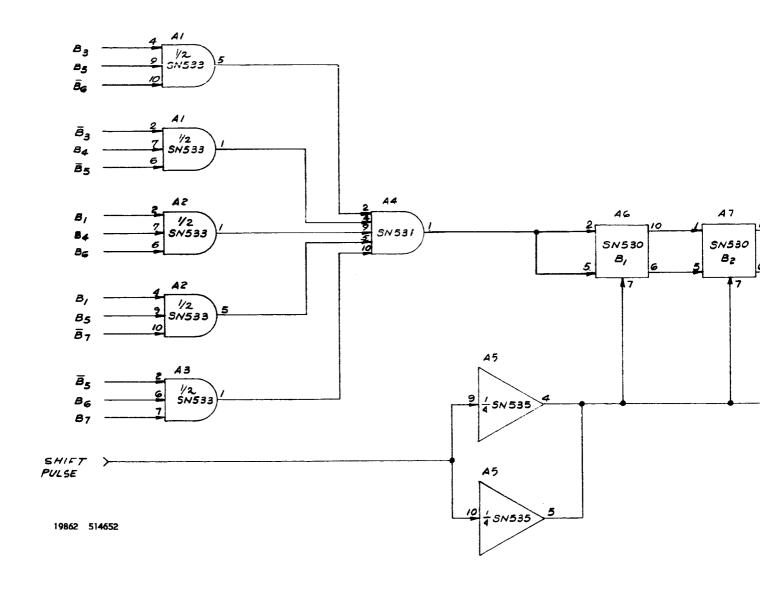


Figure 5. X Sequence Generator



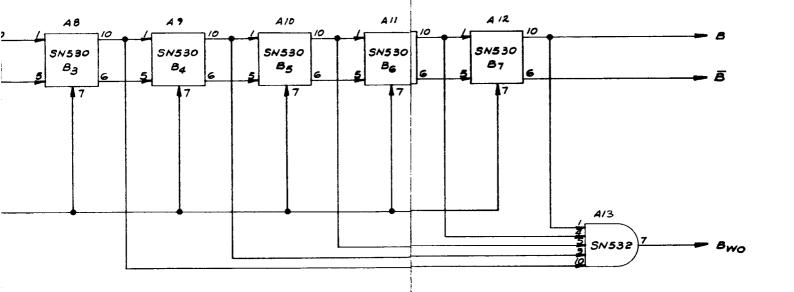


Figure 6. B Sequence Generator

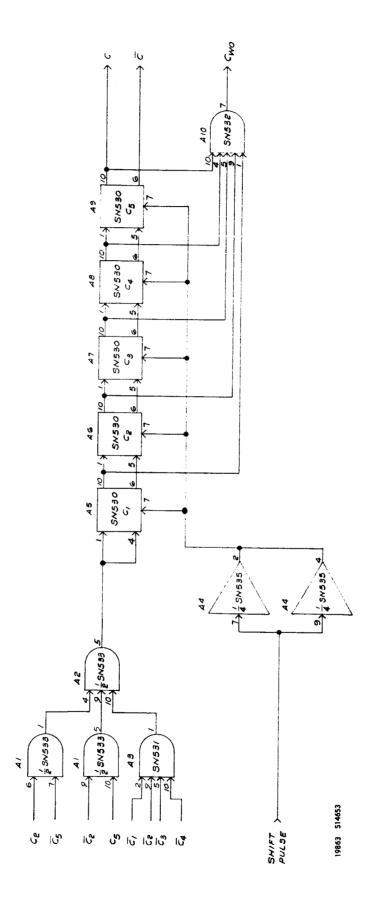
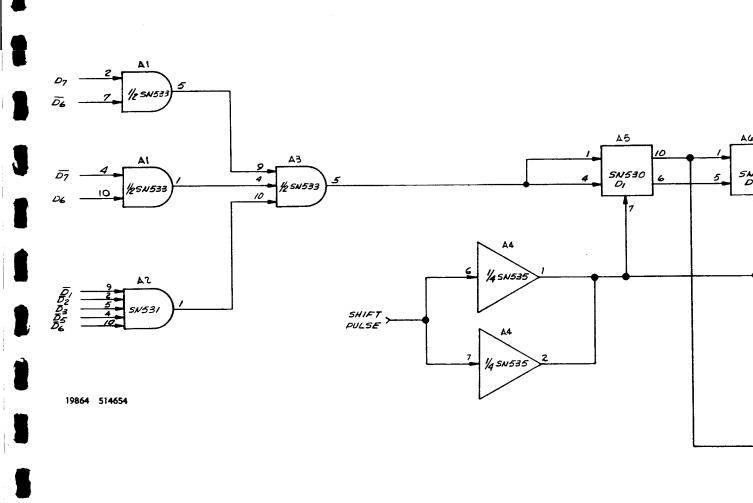
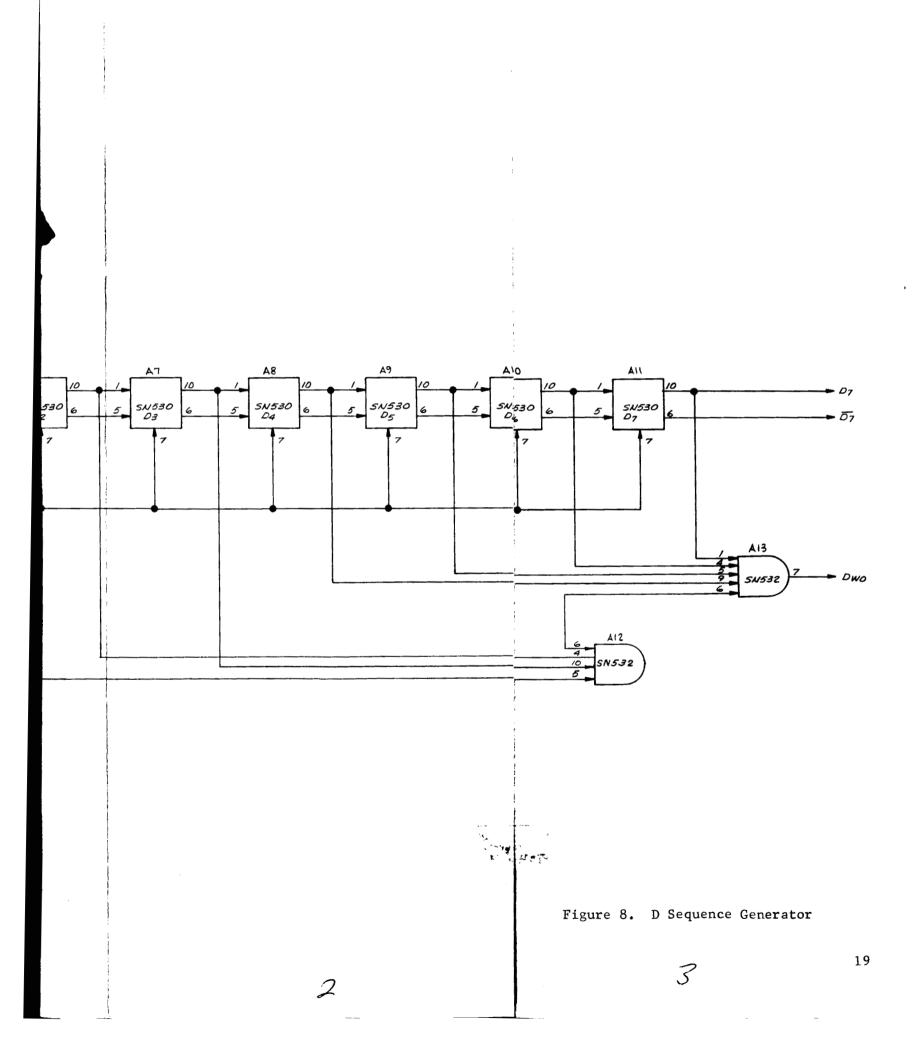


Figure 7. C Sequence Generator





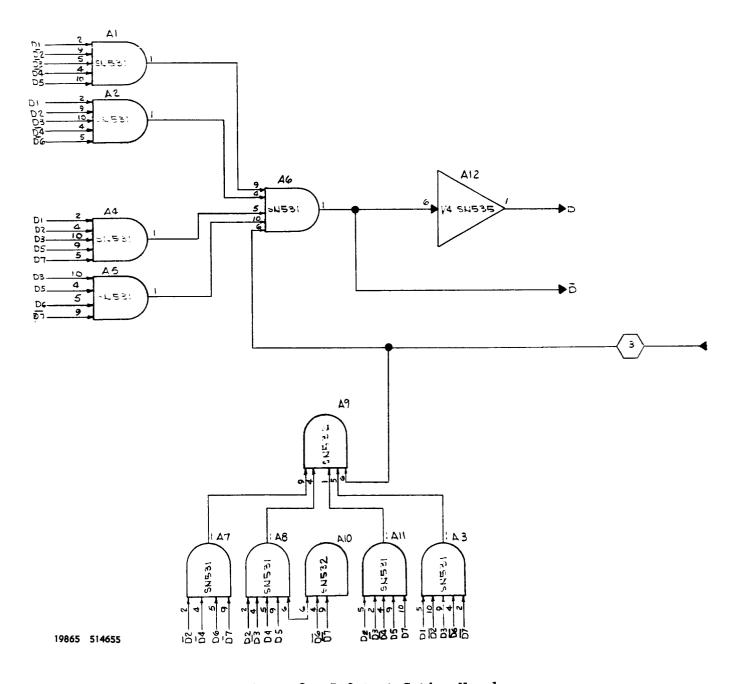


Figure 9. D Output Gating No. 1

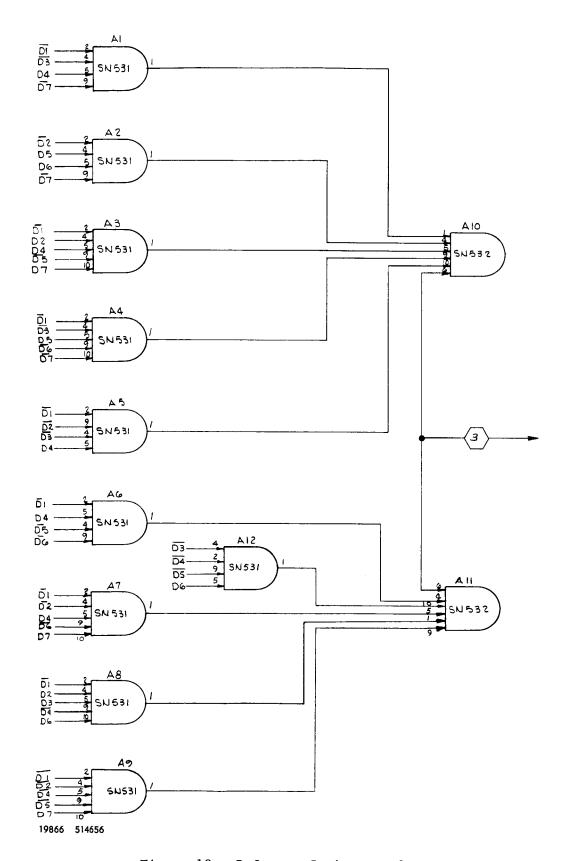


Figure 10. D Output Gating No. 2

Figure 11. E Sequence Generator

Figure 12. A Sequence Generator

7

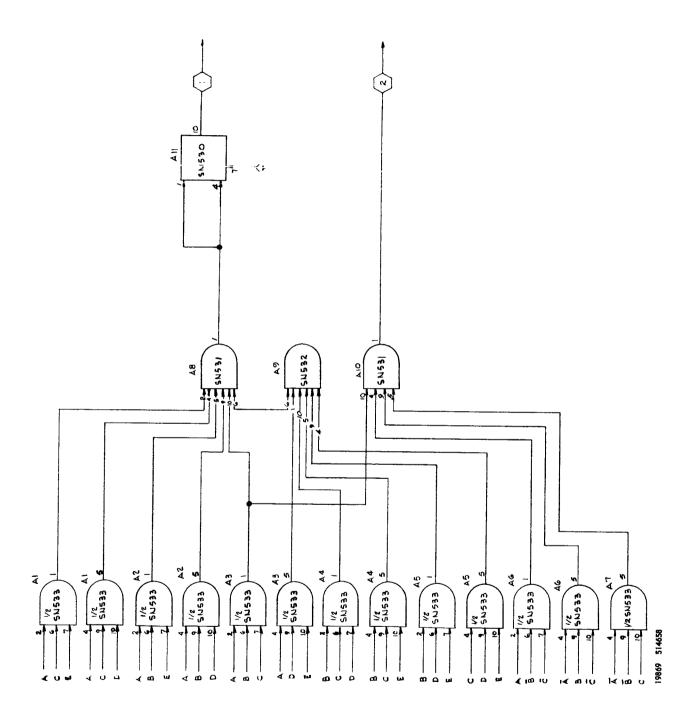
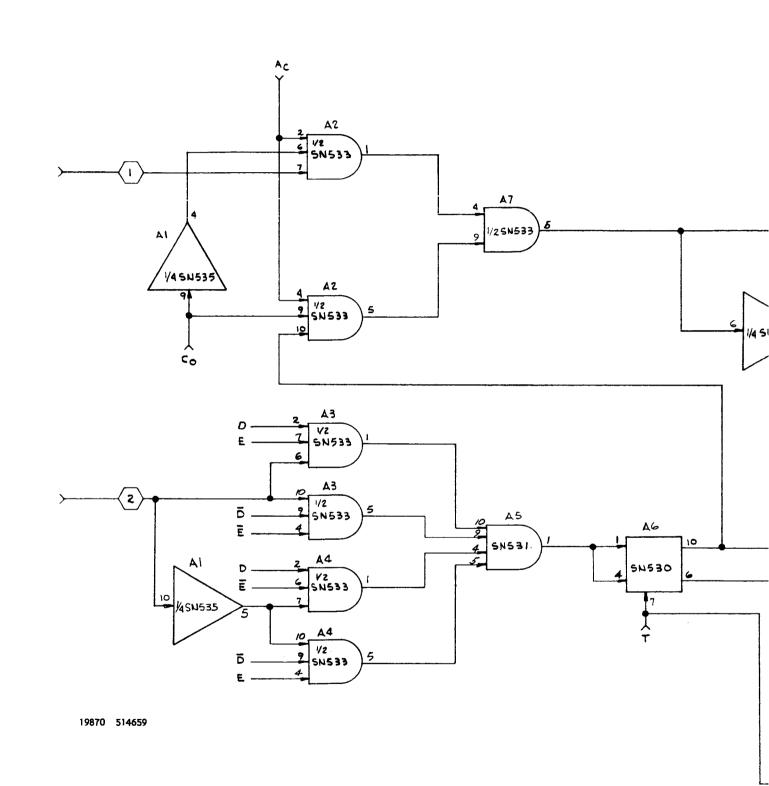


Figure 13. Transmitter and Receiver No. 1



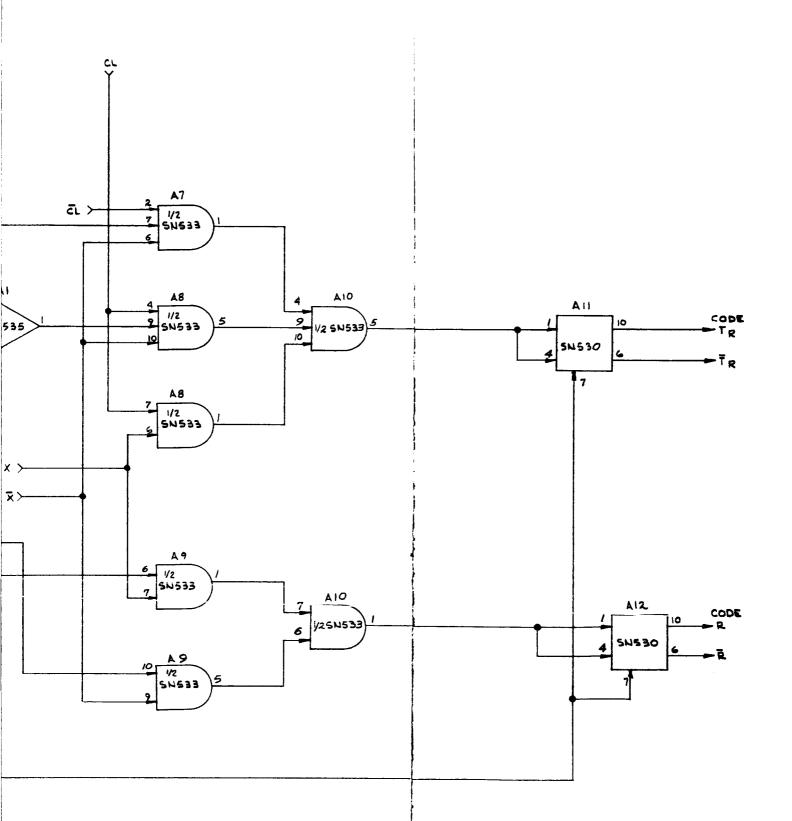


Figure 14. Transmitter and Receiver No.2

# b. Clock Input

Waveform Square 50% duty cycle
Frequency 500KC nominal
Amplitude +3 Volts
Reference Ground
Source <1K ohm
Phase In phase with 1mc squarewave

c. Acquisition and Correlation Inputs

Waveform Either of two dc voltage levels

Logic Levels +3 Volts = true (1)

0 Volts = false (0)

d. Transmitter and Receiver Code Outputs

Waveform NRZ binary voltage waveform switch nominal 1 usec bit period. Signal and complement is provided.

Logic Levels 3 Volts = 1 0 Volts = 0

Transition Timing In phase with system timing.

e. Test Outputs

Test points are provided for each code component, its associated word detector, and the internal timing pulse.

f. Power Voltage 3.2 volts ± 5% Current 650 ma
Power 2.1 watts

g. Packaging
The entire sequence generator is mounted on one standard JPL subchassis referenced in JPL Specification Number 31224. Almost twothirds of the chassis is not used.

# C. Mechanical

# 1. General

The component parts of the sequence generator, the modules, are broken into functional parts of the total system. The system is broken into five 1X modules, five 2X modules, and one connector module. The breakdown of these modules is shown in Figure 3. The interconnections from module to module is made by a double sided nickle printed circuit board with all welded construction. All interconnections in the complete system are made by either tweezer, parallel-gap, or butt welding technique.

# 2. 1X Modules

The five 1X modules contain the A, B, C, E and X code component generators. The X code component generator module also contains the clock flip-flop and the clock driver circuits.

These 1X modules each contain one TI stack of networks. The number of networks per stack varies from nine to fourteen. The modules are standard in size, i.e., .918  $\times$  .750  $\times$  .575.

The TI stacks are mounted on an epoxy coated fiber glass header board for adapting the stack leads to the final module lead configuration. The package is shown in Figures 15 and 16 which readily show the amount of space and weight wasted in conforming to the standard subchassis.

After assembly and test, the modules are dip coated with RTV 11 silicon rubber. This coating was used to provide a thin cushion for the networks. Final encapsulation of the modules was made using Stycast 2850 FT.

# 3. 2X Modules

In order to provide sufficient lead holes in the standard JPL subchassis for all inputs and outputs and maintain an economical throw-away level, the other functions, i.e., D code-component generator and the code-component combiners, were made into 2X modules which were .918 x 1.518 x .575. Each of these modules contain two standard TI stacks side by side with interconnections between the stacks made across the top of the stack as well as under the header board. The D code-component generator is contained in three of the 2X modules labeled D Sequence Generator, D Output Gating No. 1 and D Output Gating No. 2. This splitting of the function was necessary to maintain an economical throwaway level of fifteen networks or less. However, the complexity of the interconnection board was increased considerably. The remaining two 2X modules contain the code-component combining logic. These modules are labeled Transmitter and Receiver No. 1 and Transmitter and Receiver No. 2.

As in the 1X modules, these modules were dip coated with silicon rubber prior to encapsulation in Stycast  $2850\ FT$ .

# 4. Connector Assembly

The connector assembly is an all welded connection. The connector, Cannon Type DBM-25P-NMB-Bl, has terminals which provide for butt welding of the .020 nickle wire. This subassembly was potted in Silastic 881 prior to encapsulation in Stycast 1090 to allow the pins to float. The Stycast 1090 was used to reduce the overall weight of the system since no power was dissipated in this connector.

# 5. Subsystem Assembly

The assembly of the subsystem was unique as for as interconnections of the modules. The modules were held mechanically in the subchassis in the normal manner by bonding them to the subchassis, then inserting a stainless steel No. 2-56 screw into the insert encapsulated in the module.

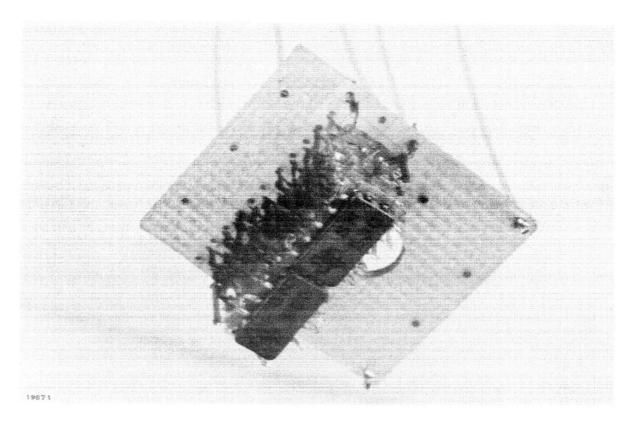


Figure 15. 1X Module - Top View

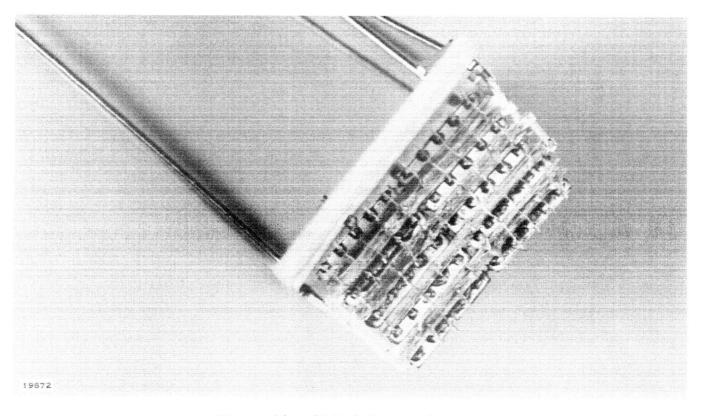


Figure 16. 1X Module - Side View

The interconnecting board was a double-sided nickle board. The etch on the two sides of the board was connected by using kovar ribbon feed-throughs that are parallel-gap welded to the etch. The backing or insulation sheet was then bonded to the printed circuit board. Finally the riser connections are parallel-gap welded to the printed circuit board approximately .020 to .050 inches from the module lead holes. Thus, when the modules are installed in the subchassis, the risers are beside and perpendicular to the module leads for easy tweezer welding. There are many ways to remove and replace a module. The best is to cut the riser ahead of the weld to the module lead and splice in a small piece of ribbon when the new module is installed.

The riser connections mentioned above are in a configuration as shown: 7 The shank portion of the riser is parallel-gap welded to the printed circuit board. The riser is then bent 90° to align the upper portion with the module leads that are protruding through the board. This procedure allows for an all welded construction while maintaining the simplicity of a conventional printed circuit board. The technique is illustrated in Figure 2 quite clearly.

After final assembly, the printed circuit board and connections are conformal coated with Solithane 113. This process provides mechanical support for the interconnections as well as insulation.

The functions that are accessible on the bottom of the subsystem can be located by the use of Figure 17 and Table IV. Figure 17 shows the location of each module lead. Table IV gives the functions associated with each module lead and also gives the connector pin numbers associated with each function.

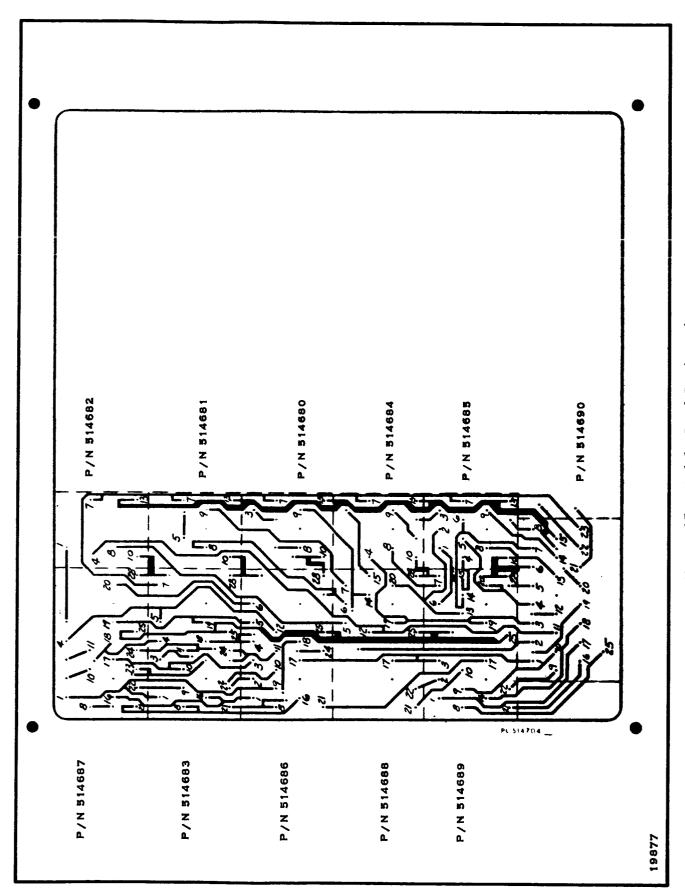


Figure 17. Module Lead Designation

Module	P/N 514680	P/N 514681	P/N 514682	P/N 514683	P/N 514684	P/N
Lead No.	A Seq. Gen.	B Seq. Gen.	C Seq. Gen.	D Seq. Gen.	E Seq. Gen.	X S
1			C Word	D <sub>6</sub>		CLC
2						Tin
3	A Code			D Word		CLC
4			C Code	<u>D</u> 5	E Code	$\overline{\mathbf{x}}$
5		B Word		D7		X C
6						CTC
7	Shift Pulse	Shift Pulse	Shift Pulse	Shift Pulse	Shift Pulse	Shi
8	A Word	B Code	C Code	D <sub>2</sub>	E Code	X W
9	A Code	B Code		$\overline{\mathtt{D_1}}$	E Word	Tim
10	GROUND	GROUND	GROUND	D4	GROUND	GRC
11				D <sub>5</sub>		
12						
13	VCC	V <sub>CC</sub>	<sup>V</sup> CC		V <sub>CC</sub>	A <sup>CC</sup>
14						
15						
16				D3		
17				$\overline{\mathtt{D3}}$		
18				D <sub>6</sub>		
19				D <sub>7</sub>		
20					:	
21				$\overline{\mathtt{D}_2}$		
22				$\overline{\mathtt{D_1}}$		
23						
24				$\overline{\mathrm{D_4}}$		
25				V <sub>CC</sub>		
26						
27						
28				GROUND		

# pdule Lead Designation

514685 eq. Gen.	P/N 514686 D Output	P/N 514687 D Output	P/N 514688 Trans. & Recvr.	P/N 514689 Trans. & Recvr.	P/N 514690 Assemi	Connector
_	Gating No.1	Gating No.2	No. 1	No. 2	Function	Connector Pin Number
CK	D <sub>3</sub>	D <sub>6</sub>		Acquire	D Code	12
Lng	$D_1$		:	1	C Word	10
ek in	D <sub>4</sub>		:	D Code	E Code	8
ode	D <sub>6</sub>	D7			X Code	6
de	$\overline{D_7}$		C Code		B Code	5
CK	3		B Code	CLOCK	GROUND	3
ft Pulse			B Code	E Code	CLOCK	2
ord	$\overline{\mathtt{D_2}}$	$\overline{\mathtt{D}_2}$		T <sub>R</sub> Code	CLOCK IN	1
In	<del>D</del> 6			Correlation	R Code	13
DND	$\overline{\mathtt{D}_3}$	$\overline{D_4}$	· · ·	2	Correlation	11
	D <sub>4</sub>	D <sub>6</sub>	:		C Code	9
	D7		C Code		A Code	7
			;	Timing	X Word	4
			A Code	CLOCK	Time In	17
			A Code	X Code	$v_{CC}$	15
	D <sub>2</sub>	D <sub>3</sub>		TR Code	R Code	24
	D	D4	D Code	D Code	Acquire	22
		D <sub>5</sub>			TR Code	21
		D <sub>7</sub>	E Code	E Code	D Word	20
		3	Timing	X Code	A Word	19
	D	$D_2$	2	R Code	B Word	18
		$\overline{D_1}$	1	R Code	E Word	16
		$\overline{\mathtt{D}_3}$			Shift Pulse	14
	D <sub>5</sub>	D <sub>5</sub>	:			
	v <sub>CC</sub>	VCC	VCC	v <sub>CC</sub>	TR Code	23
			; •			
	GROUND	GROUND	GROUND	GROUND		

#### SECTION IV

#### PROGRAM HISTORY

During the early portion of the program, implementation of the logic expressions was investigated. Since the Series 53 SOLID CIRCUIT gives the designer the option of using either NAND/NOR or AND/OR, investigation of the two approaches was warranted. The results of this investigation revealed an advantage in power and network if the AND/OR approach were used. However, providing two supply voltages offsets this advantage and the NAND/NOR approach was used.

The sequence generator in its entirety was breadboarded during November and December. However, difficulty in acquiring the SN531, 5 Input NAND Gate, delayed evaluation of the breadboard in any great detail.

During this time, the problem of power dissipation was investigated. The results of the investigation implied that use of the Stycast 2850 FT was warranted instead of the Stycast 1090. However, the assumption that all the heat would be conducted only through the potting compound was extremely conservative since each of the modules have at least six leads which are excellent heat conductors. Also, a laboratory test of a module disputed the calculations. This test, however, was not conducted in a vacuum and was, therefore, not conclusive either. Quite possibly, Stycast 1090 would be sufficient since the leads were not taken into account and since with Vcc of +3 volts the total maximum power per module is only 300 milliwatts. For a  $\Delta T$  of 30°C, the maximum power that could be dissipated using only the Stycast 1090 potting compound was 154 milliwatts. Taking the leads into account, this would rise to at least Therefore, by taking the leads into account and by using the 300 milliwatts. minimum  $V_{cc}$  supply voltage, the use of Stycast 1090 or some other light potting compound could be used with little difficulty. However, since this was a development contract and was the first time the Series 53 SOLID CIRCUITS were used, encapsulating the modules in the Stycast 2850 FT was warranted.

Development of a completely weldable printed circuit board and interconnection arrangement was accomplished during the next phase of the program. The use of parallel-gap welding of kovar risers to the nickle etch and of the kovar feed-throughs to connect both sides of the board has proved quite satisfactory. These connections have been vibrated according to or in excess of the high frequency vibration requirements called out in JPL Specification 30257.

After completion of the interconnection board layout, module and stack layouts were made and fabrication of these units begun. The printed circuit board was also being fabricated during this time.

The assembled modules after prepot testing were potted in Stycast 2850 FT, but had difficulty in temperature after potting. It was found after careful evaluation that the potting was too severe on the package. Therefore, prior to potting the modules in the Stycast 2850 FT, they were dip coated in RTV 11 silicon rubber.

The potted modules were finally symbolized and installed in the subchassis. The module leads were welded to the printed circuit board risers and the system was tested from -25°C to +100°C.

For a more detailed history of the program, refer to Progress Reports No. 1 through No. 7.

#### SECTION V

## TESTING AND CALIBRATION

The testing involved in this program other than breadboard evaluation was in the form of prepot and postpot testing of the modules and system test. The test procedures for each of these tests, prepot and postpot, are shown in Appendix E.

Some mention of the exact prepot testing is in order due to the rigorous thermal shock given the units. After assembly, the modules are tested in the following manner:

- Perform all performance tests at room temperature.
- 2. Place unit in -55°C chamber for one-half hour and perform all performance tests.
- 3. Take immediately from -55°C chamber to +110°C chamber and leave for one-half hour. Perform all tests.
- 4. Immediately return unit to -55°C chamber for one-half hour and perform all tests.
- 5. Take from -55°C chamber back to +110°C chamber and leave for one-half hour. Perform all performance tests.

This sequence was performed on each module prior to dip-coating in RTV 11 and again prior to encapsulation in Stycast 2850 FT.

Prior to assembly of the system, the modules were installed on a printed circuit board with the module leads soldered to the long ribbons welded to a printed circuit board. They were then given a room temperature system test to verify that the modules and the printed circuit board were correct.

## SECTION VI

## RECOMMENDATIONS

#### A. Electrical

If the present Series 53 networks are considered, the first recommended change involves loading the D code output with an inverter stage to clean the output when it is in the ONE state. At present, when the inverter output assumes the ONE state, its level changes as the other inputs to the driven gates switch. This is due to the top transistor in the inverter stage operating below the knee of its V<sub>C VS iC</sub> curve since there is virtually no load on the circuit. Thus, any leakage current needed by the driven gates produces a noticable voltage change at the output of the inverter. Therefore, the number of gates disabled by other signals determines the amount of leakage current drawn from the inverter which in turn determines the voltage level at which any particular ONE will be. The inverter load or a 5 to 10K load causes this inverter to operate beyond the knee of its V<sub>C VS iC</sub> curve and thus, these changes in ic are not evident in the output voltage level. Since this was not discovered until systems test and has no effect on the reliability of the system, it was felt that any corrective action at this stage could only be time consuming and expensive with no real purpose being gained.

Second, the word detector pulse for the X code component generator could be generated in a different manner and save one network. This would be done by using half of SN533 A2 and inverting its output with the unused circuit in SN535 A8.

When the new additions to the standard Series 53 line are developed and available (sometime in August) a savings of between 20 and 30 networks can be realized in implementing the logic expressions. This in turn will result in a less complex package.

The proposed new standard networks to be added to the standard line are as follows:

- 1. 4-2 input NAND
- 2. 3-3 input NAND
- 3. 2-5 input NAND
- 4. 3-2 input AND
- 5. 2-EX OR
- 1-ONE SHOT

Some of the networks would be in the 14 lead package.

The modules resulting from this addition would require the following quantities of networks.

<u>Module</u>	P SN530	resent SN531	Network SN532		SN535	N 1.		evice 3.		Total No.	No. Leads
X Seq. Gen.	4				2		2			8	11
A Seq. Gen.	5			1	1		1			8	6
B Seq. Gen.	7			1	1		1	1		11	6
C Seq. Gen.	5				1		1	1		8	6
D Seq. Gen.	7	2	1		1		1			12	18
D Out Gating		2	4					9		15	18
T and Rcvr.	4	1	1	1	1	1	5		2	16	23
E Seq. Gen.	7	2	2		1		1			13	6
TOTAL	39	7	8	3	8	1	12	11	2	91	Networks

This is a savings of 24 networks over the present system. Each function could be generated in one module while still maintaining a throw-away level of 16 networks.

The logic functions would be generated in the same manner as the present system except for the word detector pulses and the combination logic. The word detector pulses would be generated using NAND Gates followed by inverter stages. If the polarity of the word detector pulse was not important, the inverter could be left off.

The code-component combining logic would only be changed in the area of performing the function  $A \oplus B \oplus C \oplus D \oplus E$ . At present, this function is generated by the following manipulation:

$$[A \oplus B \oplus C] \oplus [D \oplus E]$$

The new EX OR network would allow this expression to be generated with less networks in the following manner:

The system logic design could be tailored a little more to the new networks with further investigation and save a few additional networks.

The circuits for these new devices are identical to those of the present NAND and AND gates except that each emitter output pull-down resistor of the AND gates are brought out on individual leads to  $-V_{\rm EE}$ . The EX OR device is similar to two AND gates tied together feeding an inverter.

The modules using the 10 lead network package measures 0.350 x 1.100 inches for the three network stack. With the 14 lead package the length would be increased to 1.400 inches. The height of the module would be determined by the number of network and interconnections involved. A sample using 15 networks was only 0.350 inches in height prior to encapsulation. The height of an 18 network module would be about 0.425 inches unpotted. This allows 0.150 for potting compound and header board or carrier board before the 0.575 standard module height is reached. An example of the modified stack is shown in Figure 18.

#### 3. Stacked Printed Circuit Boards

The second approach to packaging the networks is to use small etched printed circuit boards to interconnect the networks. The printed circuit boards would be small enough to be encapsulated in one module. Four networks would be attached to each printed circuit board and interconnections would be made around the periphery. These boards would then be connected to a header board if a predesigned hole pattern were used and if not, there would be no need for a header board. The leads would protrude from the package as they were spaced inside around the printed circuit boards.

This system would be very advantageous in a high volume production contract. The assembly time of a module would be greatly shortened.

The one shot is very similar to the J-K Flip-Flop. The range of delay within the one shot has not been disclosed. Like the J-K Flip-Flop, the normal and complement inputs are available to allow the device to be triggered by either a positive or negative pulse.

## B. Mechanical

## 1. General

Due to the configuration of the integrated circuit package, the general packaging philosophy must be investigated. This investigation must be conducted at the system level, although subsystem and module packaging changes could take better advantage of the small network package.

Restraining the package configuration to the subchassis is in itself not detrimental to miniature packaging. However, confining the modules to the standard hole pattern places extreme limitations on the packaging. Given complete freedom within the subchassis, Texas Instruments can produce a much smaller and lighter sequence generator than was produced during this contract period. However, all interconnections between modules would be made on the same side of the chassis where the modules are located. There are several approaches that can be taken to package the individual units. The two most attractive to Texas Instruments at this time are a modified network stack and a stacked printed circuit board package.

#### 2. Modified Stack

The modified stack takes advantage of Texas Instruments past experience in three dimensional network packaging. The stacks would be three networks in width thus accommodating more circuitry in a shorter stack. The interconnections would be made using a sheet of kovar etched with leads spaced on .050 centers and located to align with the network leads. The insulation tape between these interconnections would be increased in width and length to prevent shorts from occurring. There would be an overlay of tape at least .015 on each side of the network and .030 between interconnection wafers. This coupled with the experience of the layout personnel would eliminate any shorting problems.

This type of stack could easily house 15 networks and could incorporate as many as 18 networks. The stack leads could be adapted to the standard module lead pattern, but this creates unnecessary use of space and involves two more welds per lead. A better approach and the one recommended by Texas Instruments is to use the stack leads as module leads and not feed them through the subchassis hole pattern. This would double the packaging space by allowing components to be mounted on each side of the subchassis.

The modules would be mounted to a carrier board in a manner similar to that used on the sequence generator. The complete assembly would then be mounted in the subchassis by means of screws and studs. Prior to being installed in the subchassis, the modules are bonded to the board.

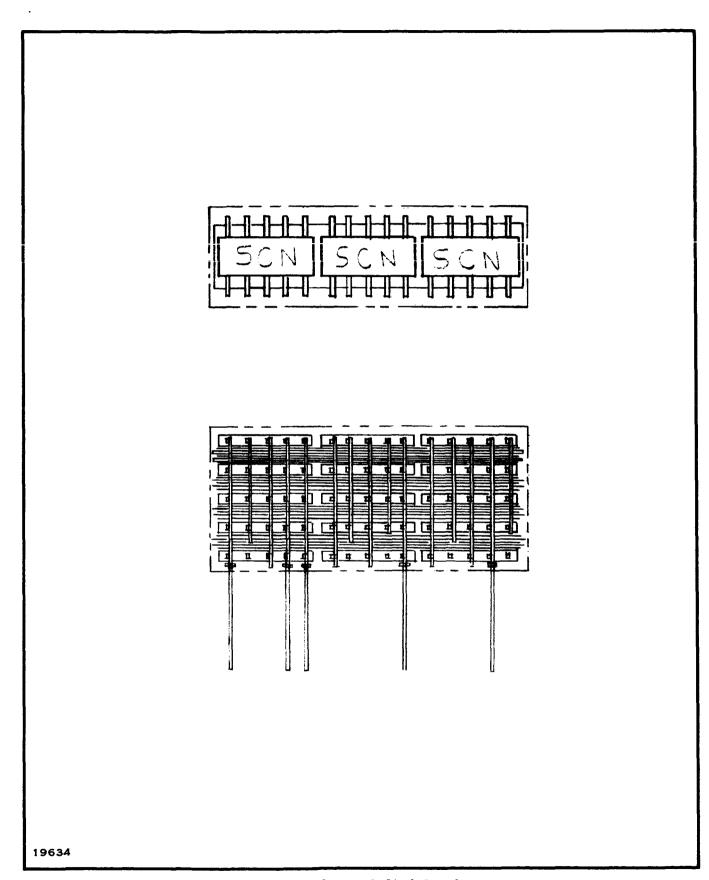


Figure 18. Modified Stack

#### SECTION VII

#### CONCLUSION

The contents of this report were not designed to present a complete picture of the work done by Texas Instruments Incorporated on the Integrated Circuit Sequence Generator contract. However, it is hoped that by giving the program highlights and making specific recommendations for improvements, some redundancy in effort and time can be eliminated in future programs of similar nature.

The equipment delivered to Jet Propulsion Laboratory is regarded with a high degree of confidence. However, it is our policy to continually strive for improved reliability, quality, and performance. It is in this realm that the recommendations were made for improvement in the existing equipment.

Texas Instruments has been pleased to work with Jet Propulsion Laboratory on this contract. It is hoped that our experience, technology and insight developed in this effort may be applied to future programs.

F. D. CLARK

Engineer

Space Instrumentation Systems

W. D. THOMAS

Project Engineer

Space Instrumentation Systems

WDT:FDC:jb

APPENDIX A
SPECIFICATION INDEX

# SPECIFICATION INDEX

The integrated circuit sequence generator and associated documentation was designed and built to meet the requirements of the following JPL specifications.

20016	General Specification, Workmanship Requirements for Electronic Equipment as applicable to the stack method of SOLID CIRCUIT semiconductor welded modules
20017	General Specification, Preparation of Reports of Contractors
20064	General Specification, Packing Equipment for Shipment Within the Continental United States
30257	Environmental Specification, Mariner B Flight Equipment as specified in JPL Specification No. 31243 Section 3.5.7.1
31224	Design Specification, Flight Equipment Telecommunication Development, Component Packaging
31243	Design Specification, Spacecraft Flight Equipment Telecommunication Development, Integrated Circuit Sequence Generator.

APPENDIX B

DRAWING INDEX

						V					
DASH NO.					RE	VIS	ION	S			
Ω 7.	SYM	ZONE			DESC	CRIPTION	1			DATE	APPROVE
Ø	-{										
Ģ										1	j
NEXT ASSY NO.											
₹											
SIZE	1										
	1										
PROJ NO.											
	<b></b>				DRAWING	G INDE	X				
					F	OR					
				3	NTEGRATE	D CIRC	UIT				
				S	SEQUENCE (	GENERA	TOR				
-2 -1	'''5^		TEXAS INS	TRUMENTS	GOVT OR	INDUST	RY	NOM	FNCI ATIL	DE OB DESC	PRINTION
-2 -1 QTY REQD	'''=^^		PAR	T OR IDE	NTIFYING N	0.			ENCLATU	RE OR DESC	CRIPTION
QTY REQD	NO	. SIZE	PAR L	T OR IDE	NTIFYING N	O. \	RIA	LS			
OTY REQU	NO	. SIZE	PAR	T OR IDE	NTIFYING N	o. \	ERIA EXAS	LS S INS	TRU	MENTS	6
DR J K	NO	. SIZE	PAR L	T OR IDE	NTIFYING N	o. \	ERIA EXAS	LS S INS	TRU	MENTS	6
OTY REQU	NO	. SIZE	PAR L	T OR IDE	O F M	o. N A T E	EXAS IN	L S S INS C O R P JS DIVISION	TRU	MENTS	6
DR J K	NO	. SIZE	PAR L	T OR IDE	O F M	O.  A TE  A  K, INTE	E R I A  EXAS  I N  PPARATU	L S S INS C O R P JS DIVISION	TRU ORA ON DA	MENTS TED LLAS. TEXA	6
DR J SEC CKD	NO	. SIZE	PAR L	T OR IDE	O F M	O.  A TE  A  K, INTE	E R I A  EXAS  I N  PPARATU	L S S INS C O R P JS DIVISION	TRU ORA ON DA	MENTS TED LLAS. TEXA	6
DR SECOND	cana	SIZE	PAR L	T OR IDE	O F M  INDEX	O.  A A T E  A  K, INTI  JIT SEC	ERIA EXAS IN PPARATE EGRATED QUENCE	L S S INS C ORP JS DIVISION GENERATO	TRU ORA ON DA	MENTS TED LLAS. TEXA	6
DR J SEC CKD	cana	SIZE	PAR L	TOR IDE	O F M  INDEX CIRCU	O.  A A T E  A  A  K, INTI  JIT SEC	E R I A  EXAS  I N  PPARATU	L S S INS C ORP JS DIVISION GENERATO	TRU ORA ON DA	MENTS TED LLAS. TEXA	6
DR SECOND	cana	SIZE	PAR L	TOR IDE	O F M  INDEX	O.  A A T E  A  A  K, INTI  JIT SEC	ERIA EXAS IN PPARATE EGRATED QUENCE	L S S INS C ORP JS DIVISION GENERATO	TRU ORA ON DA	MENTS TED LLAS. TEXA	6

Dt. 96214 CODE IDENT SHEET 2 OF 5 SHEETS REV DATE: SPECIFICATION MODEL ITEM NOMENCLATURE GOVT INTEGRATED CIRCUIT CONTR SEQUENCE GENERATOR CONTRACT NO: 950693 DOCUMENT CODE DWG REV DOCUMENT NOMENCLATURE SIZE IDENT IDENT NO. TIN PLATE F-48 Α ENAMEL, LIGHT GRAY F-59 Α MARKING F-100A INSULATION SLEEVING, ELECTRICAL 410499 Α PLASTIC SHEET, LAMINATED 411329 Α RESIN, EPOXY 412599 Α HARDENER, EPOXY RESIN 412600 INSULATION SHEET, ELECTRICAL 415218 WIRE, NICKEL, FLAT 415501 Α INSULATION VARNISH, ELECTRICAL 415528 Α 415572 WIRE, NICKEL, ROUND NICKEL-COBALT-IRON ALLOY STRIP 415584 Α COMPOUND, EPOXY RESIN, CURED 415593 Α WIRE, FLAT, NICKEL-COBALT-IRON ALLOY 415806 Α WIRE, ELECTRICAL, NICKEL, ROUND, MODIFIED 490861 В BLOCK DIAGRAM, SEQUENCE GENERATOR 514650 D DIAGRAM, LOGIC, A SEQUENCE GENERATOR 514651 С DIAGRAM, LOGIC, B SEQUENCE GENERATOR 514652 D DIAGRAM, LOGIC, C SEQUENCE GENERATOR С 514653 DIAGRAM, LOGIC, D SEQUENCE GENERATOR 514654 D DIAGRAM, LOGIC, D OUTPUT GATING NO. 1 514655 С 514708 CODE 1DENT NO. 96214

Dt 96214 CODE IDENT SHEET 3 OF 5 SHEETS REV DATE: SPECIFICATION MODEL ITEM NOMENCLATURE GOVT INTEGRATED CIRCUIT CONTR SEQUENCE GENERATOR CONTRACT NO: 950693 DOCUMENT DWG CODE REV DOCUMENT NOMENCLATURE IDENT NO. IDENT SIZE 514656 DIACRAM, LOGIC, D OUTPUT GATING NO. 2 C DIAGRAM, LOGIC, E SEQUENCE GENERATOR D 514657 DIAGRAM, LOGIC, TRANSMITTER AND RECEIVER NO. 1 514658 C DIAGRAM, LOGIC, TRANSMITTER AND RECEIVER NO. 2 D 514659 DIAGRAM, LOGIC, X SEQUENCE GENERATOR 514660 D SUBCHASSIS, MODIFIED 514661 D SEMICONDUCTOR NETWORK, A SEQUENCE GENERATOR 514662 D SEMICONDUCTOR NETWORK, E SEQUENCE GENERATOR 514663 D SEMICONDUCTOR NETWORK, C SEQUENCE GENERATOR 514664 D SEMICONDUCTOR NETWORK, X SEQUENCE GENERATOR D 514665 SEMICONDUCTOR NETWORK, B SEQUENCE GENERATOR 514666 D SEMICONDUCTOR NETWORK, TRANSMITTER AND RECEIVER D 514667 NO. 1 (STACK NO. 2) SEMICONDUCTOR NETWORK, D OUTPUT GATING NO. 2 D 514668 (STACK NO. 1) SEMICONDUCTOR NETWORK, D OUTPUT GATING NO. 2 514669 D (STACK NO. 2) SEMICONDUCTOR NETWORK, TRANSMITTER AND RECEIVER D 514670 NO. 2 (STACK NO. 1) SEMICONDUCTOR NETWORK, TRANSMITTER AND RECEIVER 514671 D NO. 2 (STACK NO. 2) MODULE HEADER BOARD NO. 1 C 514672 STACK INSULATOR В 514673 INSULATION SHEET, PRINTED CIRCUIT BOARD 514674 C NO. DE TEXAS INSTRUMENTS
INCORPORATED
APPARATUS DIVISION
DALLAS, TEXAS 514708 IDENT NO. 96214 SHEET

								-		962	214	Ðŧ	-				
DATE	2:									CODE	IDENT	SHE	ET	4 OF	5 SHEETS	REV	
		SP	ECIFIC	CA	TIOI	1	M	ODE:	L	ITEM NOMENCLATURE							
GOV									INTEGRATED CIRCUIT SEQUENCE GENERATOR								
CON						<u> </u>											
DWG	COD		DOC	_	0693		T				·						
SIZE	IDE				TNO		RE	V		DOC	CUMEN	TNC	MEN	ICLAT	URE		
D			5	140	675			:	SEMICONDUCTOR NETWORK, D SEQUENCE GENERATOR (STACK NO. 1)								
D			5	14	676			ļ		ONDUCTO K NO. 2		RK, D	SEQU	ENCE G	ENERATOR		
Ď			5	14	6 <b>7</b> 7						R NETWO		RANSM	IITTER	AND RECEIVER		
D		ı	5	14	678		į			ONDUCTO K NO. 1		RK, D	OUTF	UT GAT	ING NO. 1		
D			5	14	679		į.			ONDUCTO K NO. 2		RK, D	OUTE	UT GAI	ring No. 1		
D			5	514	680				A SEQUENCE GENERATOR								
D			5	14	681			ļ	B SEQ	UENCE G	ENERATO	R					
D			5	514	682				C. SEQUENCE GENERATOR								
D			5	514	683				D SEQ	UENCE G	ENERATO	R					
D			5	514	684				E SEQ	UENCE G	ENERATO	R					
D	į		5	514	685				X SEQUENCE GENERATOR								
D			5	514	686				D OUT	PUT GAT	ING NO.	. 1					
D			5	514	687				D OUTPUT GATING NO. 2								
D			5	514	688				TRANS	MITTER	AND REC	CEIVER	R NO.	1			
D				514	689				TRANS	MITTER	AND REG	CEIVER	R NO.	2			
С			<u> </u>	514	<b>•</b> 690				CONNE	CTOR AS	SSEMBLY	25 PI	ĽΝ				
D	1			514	¥691				MODUI	E HEADI	ER BOAR	D NO.	2				
A				514	¥692				MARK]	NG, A	SEQUENC	E GENE	ERATO	R			
A				514	4693				MARK]	MARKING, B SEQUENCE GENERATOR							
۸ <u>۳</u> ۲۱-1786								,	Ti	EXAS INS	STRUME PORAT US DIVISIONS, TEXAS	ENTS E D ON	DWG NO CODE IDENT N	<b>DL</b> o. 962	514708 <b>14</b> sheet 4		

Ðŧ 96214 SHEET 5 OF 5 CODE IDENT DATE: SHEETS REV **SPECIFICATION** MODEL ITEM NOMENCLATURE GOVT INTEGRATED CIRCUIT CONTR SEQUENCE GENERATOR CONTRACT NO: 950693 DWG CODE DOCUMENT REV DOCUMENT NOMENCLATURE SIZE IDENT IDENT NO. MARKING, C SEQUENCE GENERATOR 514694 A 514695 MARKING, D SEQUENCE GENERATOR A MARKING, E SEQUENCE GENERATOR 514696 A MARKING, X SEQUENCE GENERATOR 514697 Α MARKING, D OUTPUT GATING NO. 1 514698 A MARKING, D OUTPUT GATING NO. 2 514699 Α 514700 SEQUENCE GENERATOR ASSEMBLY D MARKING, TRANSMITTER AND RECEIVER NO. 1 514701 Α 514702 MARKING, TRANSMITTER AND RECEIVER NO. 2 A MARKING, CONNECTOR ASSEMBLY 514703 A PRINTED CIRCUIT BOARD, SEQUENCE GENERATOR 514704 D CONNECTOR SUBASSEMBLY, 25 PIN 514705 В RISER CONNECTIONS, KOVAR 514706 Α MARKING, SEQUENCE GENERATOR 514707 Α 514708 IDENT NO. 96214

APPENDIX C

NETWORK RELIABILITY

1963

# RELIABILITY REPORT

MATED BY
MATEURABILITY ASSURANCE DEPARTMENT

SOLID CIRCUIT

# SEMICONDUCTOR NETWORKS

TEXAS INSTRUMENTS INCORPORATED

P.O. BOX 5012 • DALLAS 22, TEXAS

# SEMICONDUCTOR NETWORK REPORT ON RELIABILITY

1963



Prepared by

QUALITY & RELIABILITY ASSURANCE DEPARTMENT

SEMICONDUCTOR-COMPONENTS DIVISION

TEXAS INSTRUMENTS INCORPORATED

# FOREWORD

This report contains reliability test results on SOLID CIRCUIT® semiconductor net works. It was prepared by the Quality and Reliability Assurance Department, Semiconductor-Components Division, Texas Instruments Incorporated.

The semiconductor networks tested were production units of the Series 51 family, manufactured during the period January 1963 through March 1964.

This data is presented to assist in the use of Texas Instruments Semiconductor Networks. While the data presented is accurate to the best of our knowledge, it is not intended to constitute a guarantee of product reliability.

Samuel L. Carrell, Manager

Quality and Reliability Assurance Department Semiconductor - Components Division

# TABLE OF CONTENTS

ITEN	<b>A</b>	PAGE
SUM	IMARY	1
	ICONDUCTOR NETWORKS RELIABILITY TEST GRAM AND TEST RESULTS	2
Α.	HIGH TEMPERATURE STORAGE LIFE TESTS	8
В.	WEEKLY-ADD-TO TESTS	15
C.	FIELD DATA REVIEW	20
D.	STEP STRESS TESTS	21
Ε.	ENVIRONMENTAL TESTS	24
F.	FAILURE ANALYSIS	34

## SUMMARY

The 1963 SOLID CIRCUIT® Semiconductor Network Reliability Report contains reliability information on over 9000 Series 51 semiconductor networks. This extensive reliability program, initiated over three years ago by Texas Instruments Incorporated, produced resultant data and information from manufacturing facilities that were constructed with specially designed equipment for increased production. With this increased production rate, the reliability of semiconductor networks continues to improve.

Implementation of process improvements and increased number of components per package will continue to give improved reliability. More and more circuit functions are being designed into a single network package. This has the advantage of giving a potentially lower cost per function and an improvement in reliability. This reliability improvement is due to the fact that the reliability of a single circuit on a master bar would have approximately the same reliability as if several circuits were incorporated into the same bar.

The table below summarizes the results of test performed on Series 51 semiconductor networks.

Type Test	Units on Test	Total Equivalent Network Hours	Failure Rate
Weekly-Add-To and Accelerated Testing at 125°C and 200°C	1454	9,151,000 at 85°C	0.06%/1000 hours thru 1st quarter 1964
Operational Field Data	7116	5,643,492	0.018%/1000 hours
Environmental Testing	605		Capability in excess of Mil test levels

All test results shown in this report have been obtained on semiconductor networks tested as a complete circuit. Each network is the equivalent of approximately 20 discrete components (transistors, diodes, resistors, and capacitors) interconnected as a circuit.

Although test results are for Series 51 semiconductor networks, all networks are made on the same process lines using the same process controls. Consequently, similar test results are expected from test programs on Series 52 and Series 53.

# SEMICONDUCTOR NETWORKS RELIABILITY TEST PROGRAM AND TEST RESULTS

This brochure summarizes the results of the reliability test program conducted on semiconductor networks for the period January 1963 through March 1964. The tests are designed to obtain information on the reliability of semiconductor networks, to determine device capability under severe stress, to determine existing failure modes, and to indicate corrective action in the process necessary for continued improvement of product reliability.

# TEST METHODS AND FAILURE CRITERIA

Networks under test go through initial and post stress parameter testing. The conditions for parameters chosen are per the applicable Series 51 network type data sheet. To give consistent test results the criteria for failure on all internal testing is kept the same. The parameters selected are those which are most indicative of satisfactory performance in use conditions. They are measured using maximum temperature (125°C) and worst case input voltages.

Criteria for failure are as follows:

Catastrophic Failure: A network which becomes inoperative (short or open)

or degrades sufficiently to cause definite circuit mal-

function.

Degradation Failure:

Input Current changes more than ± 20% from initial reading.

Output Voltage

On Level changes more than +20% from initial reading and ex-

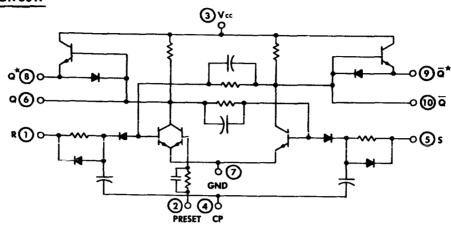
ceeding 0.30 volts.

Off Level changes more than -20% from initial reading.

# Circuit Diagram and Test Conditions

SN510 R-S Flip Flop SN511A R-S Flip Flop with emitter follower output.

# Circuit

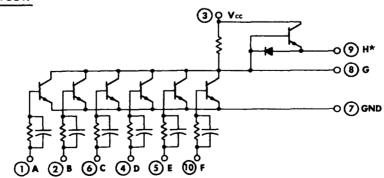


# Test Conditions

$$\begin{split} & V_{OFF} \text{ at } V_{CC} = 6 \text{ v, } V_{in} = 0.30 \text{ v, } N = 0, \ T_A = 125 ^{\circ}\text{C} \\ & V_{OFF} \text{ at } V_{CC} = 6 \text{ v, } V_{in} = 0.30 \text{ v, } N = 4, \ T_A = 125 ^{\circ}\text{C} \\ & V_{ON} \text{ at } V_{CC} = 6 \text{ v, } V_{in} = 2.0 \text{ v, } N = 4, \ T_A = 125 ^{\circ}\text{C} \\ & I_{in} \quad \text{at } V_{CC} = 6 \text{ v, } V_{in} = 2.0 \text{ v, } N = 0, \ T_A = 125 ^{\circ}\text{C} \end{split}$$

SN512 6 Input NOR/NAND Gate SN513A 6 Input NOR/NAND Gate

# Circuit

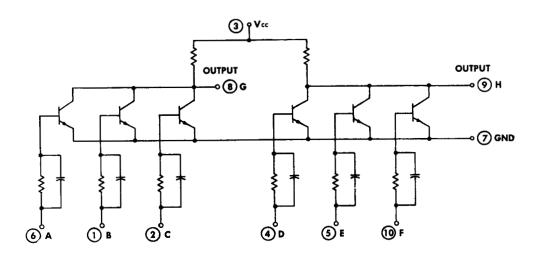


# Test Conditions

$$\begin{split} & V_{OFF} \text{ at } V_{CC} = 6 \text{ v}, \ V_{in} = 0.30 \text{ v}, \ N = 0, \ T_A = 125 ^{\circ}\text{C} \\ & V_{OFF} \text{ at } V_{CC} = 6 \text{ v}, \ V_{in} = 0.30 \text{ v}, \ N = 5, \ T_A = 125 ^{\circ}\text{C} \\ & V_{ON} \text{ at } V_{CC} = 6 \text{ v}, \ V_{in} = 2.0 \text{ v}, \ N = 0, \ T_A = 125 ^{\circ}\text{C} \\ & I_{in} \quad \text{at } V_{CC} = 6 \text{ v}, \ V_{in} = 2.0 \text{ v}, \ N = 0, \ T_A = 125 ^{\circ}\text{C} \end{split}$$

# SN514A Dual NOR/NAND Gate

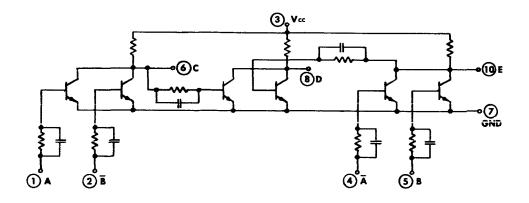
# Circuit



# Test Conditions

$$\begin{split} & \forall_{\text{OFF}} \text{ at } \forall_{\text{CC}} = 6 \text{ v}, \ \forall_{\text{in}} = 0.30 \text{ v}, \ \text{N} = 0, \ \text{T}_{\text{A}} = 125^{\circ}\text{C} \\ & \forall_{\text{OFF}} \text{ at } \forall_{\text{CC}} = 6 \text{ v}, \ \forall_{\text{in}} = 0.30 \text{ v}, \ \text{N} = 5, \ \text{T}_{\text{A}} = 125^{\circ}\text{C} \\ & \forall_{\text{ON}} \text{ at } \forall_{\text{CC}} = 6 \text{ v}, \ \forall_{\text{in}} = 2.0 \text{ v}, \ \text{N} = 0, \ \text{T}_{\text{A}} = 125^{\circ}\text{C} \\ & \textbf{I}_{\text{in}} \quad \text{at } \forall_{\text{CC}} = 6 \text{ v}, \ \forall_{\text{in}} = 2.0 \text{ v}, \ \text{N} = 0, \ \text{T}_{\text{A}} = 125^{\circ}\text{C} \end{split}$$

# Circuit

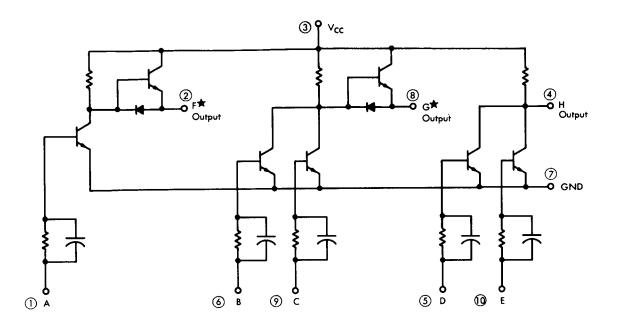


# Test Conditions

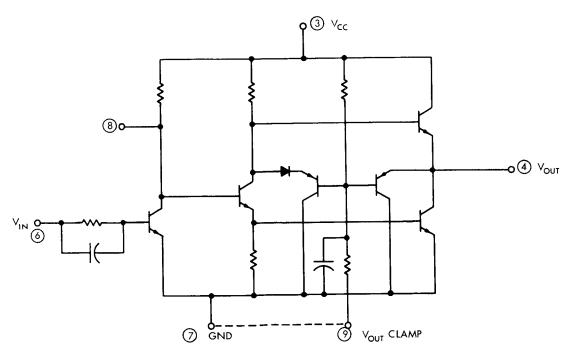
$$V_{OFF}$$
 at  $V_{CC} = 6 \text{ v}$ ,  $V_{in} = 0.30 \text{ v}$ ,  $N = 0$ ,  $T_A = 125 ^{\circ}\text{C}$ 
 $V_{OFF}$  at  $V_{CC} = 6 \text{ v}$ ,  $V_{in} = 0.30 \text{ v}$ ,  $N = 4$ ,  $T_A = 125 ^{\circ}\text{C}$ 
 $V_{ON}$  at  $V_{CC} = 6 \text{ v}$ ,  $V_{in} = 2.0 \text{ v}$ ,  $N = 0$ ,  $T_A = 125 ^{\circ}\text{C}$ 

Although the following devices are not represented in the tests presented, they are catalog device types made from the same master slice as the devices tested. As such, they utilize the same technology, the same process controls, and the same production line. It is expected that the reliability of these devices is the same as that of the devices tested and presented.

# SN516A DIFFUSED SILICON "TRIPLE GATE" LOGIC NETWORK CIRCUIT

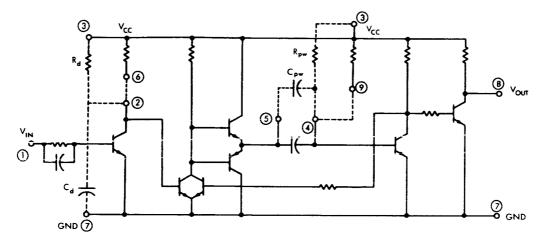


# SN517A DIFFUSED SILICON "CLOCK DRIVER" NETWORK CIRCUIT



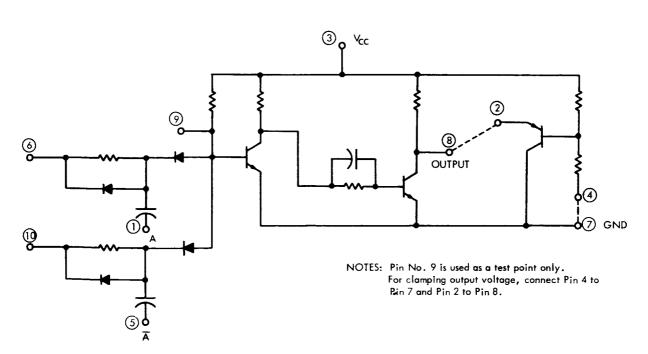
NOTE: Dotted connection shows clamped condition

# SN518A DIFFUSED SILICON "ONE SHOT" NETWORK CIRCUIT



NOTE: When using internal timing, Pin No. 2 should be connected to Pin No. 6, Pin No. 4 should be connected to Pin No. 9, and Pin No. 5 should be left unconnected.

# SN519A DIFFUSED SILICON "PULSE EXCLUSIVE OR" NETWORK CIRCUIT



# A. HIGH TEMPERATURE STORAGE LIFE TESTS

Storage life tests on semiconductor networks are performed for the following reasons:

To determine failure mechanisms in shorter test times than would be necessary at conditions during normal use.

Failure rates obtained by accelerated tests can be extrapolated to fit normal use conditions.

Complexity of tests performed, considering quantity and time, can be reduced through accelerated test methods.

# Test Methods

Networks are first tested on failure indicative parameters and then placed on high temperature storage. These parameters are monitored at periodic test intervals. The storage temperatures used are 125°C, 200°C, and 300°C.

# Summary

The table below summarizes the test results on accelerated testing at 125°C, 200°C, and 300°C storage conditions.

Type Test	Units on Test	Number Failed	Network Hours	Failure Rate %/1000 Hours
125°C Storage	100 48	2 0	934,000	0.21 (0.078 at 85°C
200°C Storage	44	0	44,000	0
300°C Storage	20	0	20,000	0

These tests continue to show capability far in excess of normal use condition storage temperatures.

# Test Results

In the 1962 Reliability Brochure, test results were presented for two groups of 50 networks tested to 3000 hours at 125°C. In this report two cracked bars were noted after 2000 hours of testing. These same two groups of networks were extended to 9000 hours with no additional failures. Pages 10 and 11 show parameter distributions on these networks to 9000 hours. The corrective action steps shown in Fig. 4 under code 3 have been effective in reducing the cracked bar failure mechanism in subsequent tests.

The remainder of the following pages show six weeks of testing at 125°C, 200°C, and 300°C. These tests were performed on the new lead pattern material which eliminates the Au-Al interface that can result in formation of "purple plague." No failures occurred on the three storage tests shown.



TEST PERFORMED:	ORAGE LIFE @+1	25°C	TYPE TEST SN512	SIZE 50			
INITIAL DISTRIBUTION	PARAMETER B	EHAVIOR ANALY	SIS				
INTER- VALS	6 WEEKS	12 WEEKS	18 WEEKS	24 WEEKS	30 WEEKS	36 WEEKS	54 WEEKS
INPUT CURREN	T_AT V <sub>CC</sub> = 6V. V	IN = 2.0 N = 0,	TA = 125°C				
JI AMP S							
≥ 67,5 65							
60							
55 50							<del>                                     </del>
45							
35							
25							
20 £17.5							
ON LEVEL AT V	cc = 6V, VIN = 2.	0, N = 0 , TA = 12	25°C	<del></del>	<del></del>		<del></del>
VOLTS							
≥.30							
.29							
. 25							
.19							
. 17							
.15							
₹.10							
OFF LEVEL AT	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0	.30 , N = 0, TA =	125°C				
VOLTS							
≥ 5.9							
5.8							
5.6 5.4 5.2							
5.0							
4.6							
4.4							
\$ 4.1	<del></del>	ļ					
OFF LEVEL (LO	ADED) AT VCC =	6V, VIN = 0.30,	N = 5 T <sub>A</sub> = 12	25°C			
VOLTS							
3.5							
3.3							
2.9							
2.7							
2.3							
1.9							
<u> </u>	<del></del>	<del>└─┰╌┰╶┰┈┰┈</del> ┩╴ <sup>╽</sup>	<del></del>	<del></del>	<del></del>	<del></del>	<del></del>



TEST PERFORMED:	STORAGE LIF	E @ + 125°C	TYPE TESTE SN510	SAMPLE SIZE 50			
INITIAL DISTRIBUTION	PARAMETER	BEHAVIOR ANALY	515				
INTER- VALS	6 WEEKS	12 WEEKS	18 WEEKS	24 WEEKS	30 WEEKS	36 WEEKS	54 WEEKS
INPUT CURREN	TAT VCC = 6V.	V <sub>IN</sub> = 2.0 N = 0.	A = 128°C				
267.5							
65							
55 50							
40							
35 30							
25 20 ≤17.5							
	/cc = 6V, VIN = 2	.0, N = 4, TA = 12	<del></del>	<del></del>	<del></del>	<del></del>	++++
VOLTS							
≥.30 .29							
.27							
.23							
.19 .17							
.13							
≤.10			-0-1-1				
VOLTS VOLTS	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0	0.30 , N = 0, T <sub>A</sub> =	128 C				
≥ 5.9							
5. 8 5. 6 5. 4							
5.2 5.0							
4, 8							
4.6 4.4 4.2							
\$ 4.1							
OFFI EVEL (10	ADEDIAT Voc	6V. VIN = 0.30. N	= 4 To = 125	<del></del>	L	<u></u>	
VOLTS							
≥ 3.6							
3.3 3.1 2.9							
2.7							
2.5							
2.1 1.9 ≤1.8							



TEST PERFORMED:	2.200		SIZE 48	
STORAGE LIFE	g + 125 C	SN510	48	
	EHAVIOR ANALYS	15		
INTER- VALS	1 WEEK		3 WEEKS	6 WEEKS
INPUT CURRENT AT VCC = 6V. V	TIN = 2.0 N = 0, T	A ≈ 125°C		
ILAMPS				
≥ 67,5 65				
60				
55 50				
45				
35 30				
25 20				
£17.5				
ON LEVEL AT VCC = 6V, VIN = 2.	0. N = 4 . T <sub>A</sub> = 125	о°c		
VOLTS				
2.30				
.29				
.25				
.19				
.13				
.11 £.10				
OFF LEVEL AT VCC = 6V, VIN = 0	.30 , N = 0, TA = 1	25 <sup>0</sup> C		
VOLTS				
≥ 5.9				
5.8 5.6				
5. 4 5. 2				
5.0 4.8				
4.6				
4.2				
\$ 4.1				
	<u></u>		<u></u>	<u></u>
OFF LEVEL (LOADED) AT VCC =	6V. VIN = 0.30, N	= 4 , TA = 12	* C	
₹3.6				
3.5				
3.3				
2.9				
2.5				
2, 1				
1.9 ≤1.8				
			<del></del>	<del></del>



			STORAGE LIFE	€+ 200°C	SN 5 10	SIZE 44		
INITIAL	DISTRIBUTION	1	TPARAMETER E	EHAVIOR ANAL	V 818		<del></del>	
INTER-		$\vdash$		1 WEEK	, 5,5	3 WEEKS		6 WEEKS
<b></b>	INPUT CURRE	L N I	L AT Vec = 6V. 1	/ <sub>IN</sub> = 2.0 N = 0,	T <sub>A</sub> = 128°C	L	<u> </u>	L
//AMPS	1	}						
≥67.5 65		1						
60 55	<b></b>	}						
50 45		Ì						
40 35		İ						
30 25								
20 517.5								
VOLTS	ON LEVEL AT	٧,	C = 6V, VIN = 2.	0, N = 4, TA = 1	25 <sup>0</sup> C			
≥.30 .29 .27								
.25 23								
.17								
.13 .11 \$.10								
	OFF LEVEL A	i TV	/cc = 6V, V:N = 0	.30 , N = 0, TA =	125 <sup>0°</sup> C			
VOLTS								
≥ 5,9 5.8								
5.6 5.4								
5.2 5.0								
4.8 4.6 4.4								
4.2								
3 4,1								
	OFF LEVEL (L	O A	DED) AT Vcc =	6V, V <sub>IN</sub> = 0.30,	N = 4 , TA = 121	<u> </u>		<del></del>
VOLTS								
2 3.6 3.5								
3.3 3.1								
2.9								
2.5								
2.1 1.9 ≤1.8								
<u> </u>								
<u> </u>	<del></del>			<del></del>		<del></del>		



TEST PERFORMED:				TYPE TEST	ED SAMPLE	٦	
		STORAGE LIFE	@ + 300°C	SN514	SIZE 20		
<u> </u>				<u></u>		J	
	_	<b>,</b>			<del></del>		
INITIAL DISTRIBUTION	1	PARAMETER B	EHAVIOR ANALYSI	5 			
INTER- VALS	Τ		1 WEEK		3 WEEKS		6 WEEKS
l	L	<u> </u>			O WEEKS	<u> </u>	0 # 22 # 0
INPUT CURRI	EN:	T AT VCC = 6V. 1	YIN = 2.0 N = 0, TA	= 128 <sup>0</sup> C			
ITAMPS	7					]	
≥ 67.5	1						
65 60	7				<u> </u>	ł	
55	1						
45	4				<b>}</b>		
40	1					]	
35	┨					1	
25	7					1	
20 £17.5	1					İ	
ON LEVEL AT	· v.	cc = 6V, VIN = 2.	0, N = 0, TA = 125	°c			
VOLTS	]					]	
<b>2</b> .30	+					<b>{</b>	
.29	1						
.27	1					}	
. 23	7					}	
.19	1					j	
.17	-}		<b></b>			ł	
13	1						
.11 5.10	Ŀ						
OFF LEVEL A	T	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 6	0.30 , N = 0, TA = 12	25 <sup>0</sup> C		•	
VOLTS	7					}	
≥ 5.9	┨		<u> </u>				
5.8	7						
5.4	<b>1</b>					Í	
5.2 5.0	1		<del></del>				<del></del>
4.8	1						
4.6	1						
4.2 5 4.1	4				ļ		<b></b>
3 4.1	1						
	J				<del></del>		L
OFF LEVEL (	50	ADED) AT V <sub>CC</sub> =	6V, VIN = 0.30, N	= 5 , T <sub>A</sub> = 12	15°C	7	
VOLTS	1						
3.5	7						
3.3	1					1	
3.1	-		<del> </del>				
2.7	7						
2.5	-					Ì	
2,1	7						<b></b>
\$1.8	1						
	-					,	
	4		<del></del>			7	<del> </del>

#### B. WEEKLY-ADD-TO TESTS

### **Test Program**

The Weekly-Add-To test program is a continuous reliability control test of production networks. Each week a random sample of twenty Series 51 semiconductor networks is taken from devices produced in the previous week and placed on operating life at  $T_A = 125$ °C,  $V_{CC} = 6$  v, and storage life at  $T_A = 200$ °C. Ten networks are subjected to each test. The networks remain on test for twelve weeks. They are then removed and the tests are discontinued except for those units which each quarter are extended on test indefinitely to obtain long-term reliability data.

Defect analysis of all Weekly-Add-To failures is performed so that the information obtained can be passed back to the Integrated Circuits Department and/or Process Control Stations, as appropriate, for implementation of necessary corrective action.

### Summary

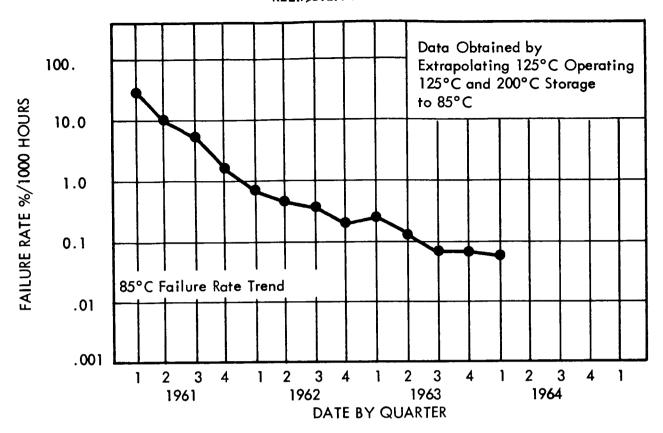
The reliability trend shows failure rates currently below 0.1%/1000 hours. Indications are that network failure rates are approaching those of discrete components. Recent articles comparing systems composed of networks versus discrete component counterparts verify that this is the case — quotes of MTBF improvements ranging from 6.6 to 30 have been noted.

#### Test Results

A combined summary of 125°C operating life and 200°C storage life results by quarter is given in Fig. 1. The points are obtained by considering the relationship of failure rate versus temperature. Testing performed at 200°C and/or 125°C is related to 85°C by use of the appropriate acceleration factor. These acceleration factors are given below:

Temperature	Factor
300°C	20.0
200°C	7.5
125°C	2.7
85°C	1.0
55°C	0.4
25°C	0.15

# SERIES 51 SEMICONDUCTOR NETWORK RELIABILITY TREND



UNITS TESTED - DEVICE HOURS SUMMARY

Year	Quarter	Number of Units Tested	Number Failed	Actual Device Hours (000)	Equivalent 85°C Device Hours (000)
1962	First	200	5	275	743
	Second	55	1	85	230
	Third	50	1	95 .5	258
	Fourth	158	2	368	994
1963	First	219	3	239	1217
	Second	160	2	317.5	1618
	Third	76	0	152	948
	Fourth	204*	0	358	967
1964	First Second Third Fourth	240*	0	183	108 <i>7</i>

<sup>\*</sup>Tests in progress

To convert failure rates at one temperature to 85°C, divide the failure rate by the appropriate factor, or alternately, multiply the hours accumulated by the same factor. Where no failures occurred, it was not possible to divide the number of failures by test hours to obtain failure rate. In these cases, the 50% confidence level point was used. In general this is slightly more conservative than the failures divided by hours method.

Due to the fact that tests in the fourth quarter of 1963 and the first quarter quarter of 1964 are still underway, parameter plots for fourth quarter, on subsequent pages, are done only on devices completing 12 weeks of testing.

### Test Failures

Condition	Production Date	Discussion	Corrective Action
Operating at 125°C	1/5/63	Unit not bistable. Surface leakage, suspect inversion layer.	Implementation of welded package has eliminated solder flux. Improved clean up technique. Improved heat treating after aluminum evaporation. Added 200°C post can bake.
	1/12/63	Input current degradation. Surface leakage caused by either contamination or inversion layer.	Same as above.
	4/13/63	Unit not bistable, input current degradation. Contamination caused input resistor degradation.	Same as above.
	2/2/63	Open. Aluminum oxide formation. Bonds mechan-ically but not electrically sound.	produce or explain this
Storage at 200°C	4/13/63	Open pins. Formation of Au-Al compound caused open bonds.	Added 200°C post can bake. Installed hot tip bonding capillaries for positive temperature control. Studies currently underway to eliminate Au-Al interface by use of new lead pattern material.



## SEMICONDUCTOR NETWORKS RELIABILITY DATA QUALITY AND RELIABILITY ASSURANCE DEPARTMENT

SN511 SAMPLE TEST PERFORMED: OPERATING LIFE @ +125°C, VCC = 6 SN 511 PARAMETER BEHAVIOR ANALYSIS INITIAL DISTRIBUTION INTER-1 WEEK 3 WEEKS 6 WEEKS 12 WEEKS INPUT CURRENT AT V<sub>CC</sub> = 6V, V<sub>IN</sub> = 2.0 N = 0, T<sub>A</sub> = 125°C [[AMPS ON LEVEL AT VCC = 6V, VIN = 2.0, N = 4, TA = 125°C VOLTS OFF LEVEL AT VCC = 6V, VIN = 0.30 , N = 0, TA = 125°C VOLTS 5.0

5 4.1	L	
	<del></del>	<del></del>
OFF LEVEL (Le	DADED) AT $V_{cc} \approx 6V$ ,	VIN = 0.30, N = 4 , TA = 125°C
VOLTS	[	
₹3.6		
		<b></b>
3.5		
3.3		<u></u>
3.1		
2.9		
2.7		ž į
2.5	-	
2.3		
2. 1		
1.9		
≤1.8	<del>                                     </del>	<del></del>
<del></del>	<del>                                     </del>	
<del> </del>	<del></del>	
<u> </u>	<del></del>	<del></del>



TEST PERFORMED:	ERATING LIFE @ +125°C, VCC	= 6 SN513 SAMPLE SIZE 25		
INITIAL DISTRIBUTION	PARAMETER BEHAVIOR ANAI	_YSIS		
INTER-	1 WEEK	3 WEEKS	6 WEEKS	12 WEEKS
INPUT CURREN	T AT VCC = 6V, VIN = 2.0 N = 0	T <sub>A</sub> = 125 <sup>0</sup> C		
JIAMPS				
≥67.5 65				
60 55				
50 45				
40				
30				
25 20				
517.5	<del></del>	0-1-1-1		
VOLTS VOLTS	CC = 6V, VIN = 2.0, N = 0 , TA =	125 C		
≥.30				
.29				
.25				
,21				
. 17				
.13				
.11 £.10				
OFF LEVEL AT	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30 , N = 0, T <sub>A</sub>	= 125°C		
5.8 5.6				
5.4				
5.2 5.0				
4.6				
4.4				
5 4,1				
OFF LEVEL (LO	ADED) AT VCC = 6V, VIN = 0.30.	N = 5 , TA = 128 C		
VOLTS				
≥ 3. 6				
3.3				
2.9 2.7 2.5				
2.3				
2,1				

#### C. FIELD DATA REVIEW

Actual use condition testing performed by networks consumers offers the potential of many hours of test data. Applications of 7116 networks have accumulated 5,643,492 hours of test data.

These applications are typically shift registers, computers, and counters operating near 25°C. A failure is considered to be observed when the equipment ceases functional operation due to a network failure. Failures which occur due to mechanical stressing in system checkout are not considered as life or operating failures. In the hours accumulated one failure has occurred. This failure was due to difficulties with the solder seal on the old Series 51 device. Implementation of the welded package eliminates this mechanism.

One failure out of 5,643,492 hours gives a failure rate estimate of 0.018%/1000 hours, with 60% confidence this proves a use condition failure rate of 0.032%/1000 hours.

The curve in Fig. 2 indicates the 0.032% graphically, along with 90% and 95% confidence limits.

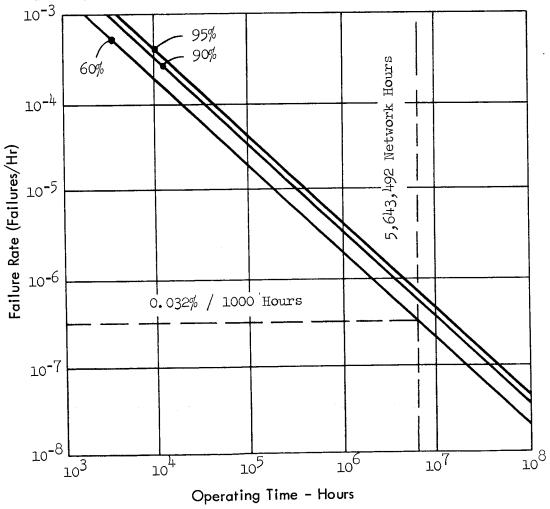


Fig. 2. Upper Confidence Limits - Operational Field Application Data

#### D. STEP STRESS TESTS

Temperature step stress testing is performed to indicate product capability and to confirm process improvements. However, as a product's capability improves, this indicator becomes less sensitive since very few failures are observed up to temperatures that induce total failure. Consequently, testing during 1963 was limited to the amount necessary to show no degradation from previous levels had occurred.

The applicability and use of operating step stress is being investigated to determine if its use will give a more sensitive indicator of product capability.

### Test Methods

Networks are measured on failure indicative parameters initially. The first level of stress (temperature or operating power) is then applied for a specified step length — generally four to twenty four hours. Parameters are measured after this stress, and the same units are stressed to the next higher step level. This sequence of testing continues to predetermine percent failure. Failures are removed after the level where failure is indicated.

### Summary

Step stressing shows product capability far in excess of normal storage temperature levels. Repetition of the same tests over a period in time shows that process improvements have been effective in extending the temperature capability and reducing percent failure under extreme temperature stresses.

#### Test Results

Figure 3 shows the curve of percent failures versus temperature for tests performed in 1962 and 1963. Because the major failure mode uncovered was open ball bonds, specific emphasis was placed on developing new contact materials by the Integrated Circuits Department. These materials are being incorporated into the construction of extensively tested and evaluated samples which are being used in the reliability investigations in progress.

The results of the most recent test are shown on page 23. It is significant to note that these networks show capability in excess of 377°C, the silicon-gold eutectic point. This was not previously the case. Even higher temperature capabilities are contemplated for the new lead pattern material.

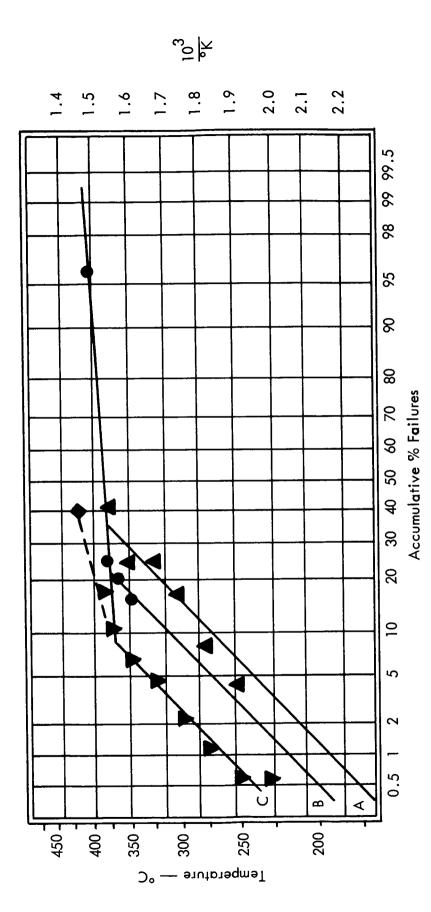


Fig. 3. Semiconductor Networks Step Stress Test Results



## SEMICONDUCTOR NETWORKS RELIABILITY DATA QUALITY AND RELIABILITY ASSURANCE DEPARTMENT

TEST PERFORMED:				ED SAMPLE		
TEMP	ERATURE STEP	STRESS, 4 HOURS	SN513	SIZE 10		
INITIAL DISTRIBUTION	PARAMETER B	EHAVIOR ANALYS	15			
INTER- VALS	+ <b>200</b> °C	+250°C	+300°C	+350°C	+375 <sup>°</sup> C	+425°C
INPUT CURRENT	TAT VCC = 6V, V	/tN = 2.0 N = 0, T	= 128 <sup>0</sup> C			
/LAMPS						
≥67.5						
65 60		<del></del>		<del></del>	<b></b>	
55						
45						
35						
30 25						
20 517.5						
	CC = 6V, VIN = 2.	0, N = 0, TA = 125	2, 1, 1, 1,			
VOLTS						
2.30 .29						
.27						
.25						
.19						
.17						
.13						
110						
OFF LEVEL AT	V <sub>CC</sub> = 6V. V <sub>IN</sub> = 0	.30 , N = 0, TA = 1:	25°C			
VOCIS						
≥ 5.9 5.8	*					
5, 6 5, 4						
5.2						
4.8						
4.6						
4.2 5 4.1		<del>      </del>				
OFF LEVEL (LO	ADEDI AT VCC =	6V. VIN = 0.30. N	= 5. TA = 12	<u> </u>		
VOLTS						
≥ 3. 6						
3.5						
2.9						L
2.7						
2.3						
2,1						
\$1.8						
<u> </u>	<u> </u>			<del></del>	<del></del>	<del></del>

 $\star$  The shift in Voff readings after the first two levels of stress was due to improper readings initially and after the 200°C step.

#### E. ENVIRONMENTAL TESTS

### Test Program

Environmental tests are performed to demonstrate the ability of the semi-conductor networks to withstand mechanical and physical stresses. The results illustrate compliance with existing environmental requirements of Mil-S-19500. The tests were then extended to even higher levels to demonstrate the ability to withstand even higher stress conditions.

### Test Results

Figure 4 summarizes the tests run and the failures found in tests performed in 1962 and 1963. Failure modes are indicated and corrective action noted. Subsequent pages report detail results of each test performed including the initial and post test parameter behavior patterns. Tests performed on over 600 networks prove capability in excess of standard military testing levels.

It should be pointed out that the failures at 20,000 G and 35,000 G occurred in 1962. Since the date of those failures, 45 units have been tested at 20,000 G with no additional failures, indicating that the implemented corrective action steps have been effective.

Fig. 4. Series 51 — Semiconductor Networks Environmental Evaluation

		NUMBER				
	TEST	TESTED	CONDITIONS	FAIL	CODE	
Thermal	Shock	50*	5 Cycles -0°C to +100°	C 0		
		30	45 Cycles	0		
		30	135 Cycles	1	1	
		9	270 Cycles	0		
Tempero	iture Cycling	73*	5 Cycles -55°C to +125	5°C 0		
•		40	45 Cycles	0		
		40	135 Cycles	0		
		20	160 Cycles	0		
Shock		93*	1,500 G, 0.5MS, Total 20	Blows		
				lanes 0		
		<del>4</del> 0	2,000 G	0		
		70	3,000 G	0		
		40	3,500 G, 0.2MS	0		
Vibratio	on Variable	103*	20 G, 100-2000CPS, 3	Planes 0		
Frequen	су	50	30 G	1	2	
		40	40 G	0		
		50	50 G	0		
Vibratio	on Fatigue	50*	20 G, 60 CPS, 96 Hours	0		
		50	30 G 9 Hours	. 0		
		40	40 G 9 Hours			
		40	50 G 9 Hours	. 0		
Constan	t Acceleration	108*	20,000 G	1	3	
		32	35,000 G	. 1	4	
		124	40,000 G (98 Y1 Plane Only		3,4	
		24	45,000 G	1	5	
		28	50,000 G	1	4	
Moisture	e Resistance	20*	10 Cycles	0		
		10	20 Cycles	0	_	
		20	30 Cycles	1	6	
		9	40 Cycles	1	6	
c 1	,	8	50 Cycles	1	6	
Salt Atn	nosphere	30*	24 Hours, 5% Solution	0		
		10	48 Hours	0		
* Tests	at MIL-S-19500	Level				
CODE	FAILURE /	MODE	SUBSEQUENT PROC	ESS CHANGES		
1	Degradation Fa	ilure	Eliminated Solder Flux by Go	oina to Welded P	ackaae	
2	Open Bond		Added QRA Bonding Controls			
	•		Hot Tip Bonder and Insulated			
3 Broken Bar			Increased Bar Thickness, Cha	nged Mounting (	Glass	
			& Improved Operator Procedu	ire by X-ray Mor	nitor	
4	Package or Lea	d Failure	Test Fixture Caused Problems — Fixture Redesigned			
_	De se dettes las	C t	New Welded Package Is More Rigid			

High Temperature Slice Bake, Installed 100% 48-Hour 200°C Bake and 10 Cycles of Temperature Cycling (-55°C to +150°C), Added Welded Package

Current Welded Package Results Indicate Improve-

ment on Salt Atmosphere and Moisture Resistance

5

6

Degradation Input Current

Lead Failure



TEST PERFORMED:	THERMAL SHOCK, +100°C to 0	°C SN515 SIZE 10	
INITIAL DISTRIBUTION	N PARAMETER BEHAVIOR	ANALYSIS	
INTER- VALS		5 Cycles	45 Cycles
ON LEVEL AT	T Vcc = 6V, VIN = 2.0, N = 0 ,	TA = 125°C	
VOLTS ≥.30			
.29 .27 .25 .23			
.19			
.17 .15 .13 .11			
S.10 OFF LEVEL A	AT Vcc = 6V, VIN = 0.30 , N = 0.	TA = 125°C	
≥ 5.9			
5. 8 5. 6 5. 4			
5.2 5.0 4.8			
4.6 4.4 4.2 54.1			
	=		
OFF LEVEL (	(LOADED) AT V <sub>CC</sub> = 6V, V <sub>IN</sub> =	0.30, N = 4 , TA = 125 C	
2 3. 6 3. 5 3. 3			
3. 1 2. 9 2. 7			
2.5 2.3 2.1			
1.9			

Fig. 4. Series 51 — Semiconductor Networks Environmental Evaluation

TEST	NUMBER TESTED	CONDITIONS	FAIL	CODE
Thermal Shock	50*			V
memai snock	30	5 Cycles -0°C to +100°C	0	
	30	45 Cycles	0	
	9	135 Cycles	1	ì
Temperature Cycling	73*	270 Cycles	0	
remperatore Cycling	40	5 Cycles -55°C to +125°C	0	
	40	45 Cycles	0	
	20	135 Cycles	-	
Shock	93*	160 Cycles	0	
SHOCK	73	1,500 G, 0.5MS, Total 20 Blows	0	
	40	4 Planes 2,000 G	0	
	<del>7</del> 0	3,000 G	0	
	40		0	
Vibration Variable	103*	3,500 G, 0.2MS	0	
Frequency	50	20 G, 100–2000CPS, 3 Planes 30 G	0	^
rrequency	40	40 G	1	2
	<del>40</del> 50	50 G	0	
Vibration Fatigue	50*	_ · · -	0	
Vibiation Langue	50 50	20 G, 60 CPS, 96 Hours 30 G 9 Hours	0	
	40	40 G 9 Hours	0	
	40	50 G 9 Hours	0	
Constant Acceleration	108*	20,000 G		^
Consider Acceleration	32	35,000 G	1 1	3
	124	40,000 G (98 Yl Plane Only)	3	4
	24	45,000 G (78 11 Flane Only)	ى 1	3,4
	28	50,000 G	}	5 4
Moisture Resistance	20*	10 Cycles	Ó	4
Wiorstore Resistance	10	20 Cycles	0	
	20	30 Cycles	1	4
	9	40 Cycles	1	6 6
	8	50 Cycles	i	6
Salt Atmosphere	30*	24 Hours, 5% Solution	0	O
Tati i initrophici c	10	48 Hours	0	
* Tests at MII _S_10500		10 (1001)	J	

<sup>\*</sup> Tests at MIL-S-19500 Level

CODE

ODE	FAILURE MODE
1 2	Degradation Failure Open Bond
3	Broken Bar
4	Package or Lead Failure
5	Degradation Input Curren
6	Lead Failure

#### SUBSEQUENT PROCESS CHANGES

Eliminated Solder Flux by Going to Welded Package Added QRA Bonding Controls, Expanded Contacts Hot Tip Bonder and Insulated Base Plate Increased Bar Thickness, Changed Mounting Glass & Improved Operator Procedure by X-ray Monitor Test Fixture Caused Problems — Fixture Redesigned New Welded Package Is More Rigid High Temperature Slice Bake, Installed 100% 48-Hour 200°C Bake and 10 Cycles of Temperature Cycling (-55°C to +150°C), Added Welded Package Current Welded Package Results Indicate Improvement on Salt Atmosphere and Moisture Resistance



TEST PERFORMED:	THERMAL SHOCK, +100°C to 0°C	SN515 SAMPLE SIZE 10	
INITIAL DISTRIBUTION	PARAMETER BEHAVIOR AND	ALYSIS	
INTER- VALS		5 Cycles	45 Cycles
ON LEVEL AT	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 2.0, N = 0 , T <sub>A</sub>	= 128°C	
VOLTS 2.30			
.29			
.25			
.19 .17 .15			
.13 .11 5.10			
OFF LEVEL A	<i>t</i> T v <sub>cc</sub> = 6v, v <sub>in</sub> = 0.30 , n = 0, T, 1	A = 125 C	
2 5.9			
5.8 5.6 5.4			
5.2 5.0 4.8			
4.6 4.4 4.2			
≤ 4.1			
OFF LEVEL (L	OADED) AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.3	10, N = 4 . TA = 125°C	<del></del>
VOLTS 23.6			
3.5			
3.1 2.9 2.7			
2.5			
1.9 ≤1.8			
<u> </u>	<del>{</del>		



TEST PE	RFORMED:	EM	PERATURE CYCLIN	G, +125°C to -55°C	SN515	SIZE 10	
INITIAL	DISTRIBUTION	ı	PARAMETER B	EHAVIOR ANALYSI	s		
INTER- VALS					5 Cycles		45 Cycles
L		L.,					1 0 0,010
VOLTS	ON LEVEL AT	<b>,</b> ,	C - 64, AIN - 2.0	), N = 0 , T <sub>A</sub> = 125 <sup>0</sup>			
2.30 .29 .27							
.25 .23 .21							
.19							
.15 .13							
₹.10	OFF LEVEL A	ΓV	CC = 6V, VIN = 0.	ہــا 12 = ۸ . 30 ، N = 0. 30 .	5°C		L
≥ 5.9							
5.8 5.6 5.4							
5.2 5.0 4.8							
4.6 4.4 4.2							
\$ 4.1							
	FF LEVEL (L	OA	DED) AT VCC = 6	بسا = ۲۷, V <sub>IN</sub> = 0.30, N	4 , TA = 128	s°c	L
VOLTS ≥ 3.6							
3.5 3.3 3.1							
2.9 2.7 2.5							
2.3 2.1 1.9							
\$1.0							



TEST PERFORMED:	SUCCE OF A LOSS	TYPE TESTED SAMPLE	
L	SHOCK, 0.5 msec duration	SN514 STZE 10	
INITIAL DISTRIBUTION	PARAMETER BEHAVIOR ANALY	SIS	
INTER~		1500 G	3000 G
INPUT CURREN	T AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 2.0 N = 0,	TA = 125°C	
ILAMPS			
65			
60			
55			
45			
35			
25 20			
<u>20</u> ≤17.5			
ON LEVEL AT V	CC = 6V, VIN = 2.0, N = 0 , TA = 12	. 5°C	
VOLTS			
≥.30			
.27			
. 25	,		
. 21			
.17			
.13			
≤.10			
OFF LEVEL AT	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30 , N = 0, T <sub>A</sub> =	125°C	
VOLTS			
≥ 5, 9 5, 8			
5.6			
5.4			
5.0 4.8			
4.6			
4.2 5 4.1			
34.7			
05515751	ADEDLAT V 6V. V 0.20 A		<u> </u>
VOLTS	ADED) AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30, I	- 5 , 1 <u>A</u> - 120 C	
≥ 3.6			
3.5			
3.1			
2.9			
2.5			
2.1			
\$1.0			
			<del></del>



TEST PERFORMED:	DECLIENCY VIDRAT	TION , 100 to 2000 cps	TYPE TEST	SIZE 10		
TARIADELI	REGIOEITCT VIBRA	11014, 100 10 2000 гда	317314		i	
INITIAL DISTRIBUTION	TRABAMETER	EHAVIOR ANALYSI	<u> </u>			
	PARAMETER	EHAVIOR ANAL TSI		·	· · · · · · · · · · · · · · · · · · ·	T
INTER- VALS			20 G		<u></u>	30 G
INPUT CURREN	T AT V <sub>CC</sub> = 6V, V	11N = 2.0 N = 0, TA	= 125°C			
JIAMPS						
≥67.5 65						
60 55						
50						
45						
35						
25						
517.5						
ON LEVEL AT V	cc = 6V, VIN = 2.	0, N = 0, TA = 125 <sup>C</sup>	'c			
VOLTS						
2.30 .29		<del> </del>				
.27						
.25						
.19						
.17						
.13		E				
\$ 10			<del></del>			<del></del>
OFF LEVEL AT	V <sub>CC</sub> = 6V. V <sub>IN</sub> = 0	0.30 , N = 0, T <sub>A</sub> = 12	5°C			
≥ 5.9 5.8						
5.6 5.4						
5.2		<b>P</b>				
4.8						
4.4						
4.2 5 4.1						
OFF LEVEL (LO	ADED) AT V <sub>CC</sub> =	6V, VIN = 0.30, N	5 TA = 12	:5 <sup>°</sup> C		
VOLTS		<u> </u>				
≥ 3.6						
3.3						
3.1						
2.7						
2.3						
1.9 ≤1.8						
- 1.0						
		<u> </u>	<del></del>			<del></del>

TEST PERFORMED:



TYPE TESTED SAMPLE

L	· · · · · · · · · · · · · · · · · · ·	VI	IBRATION FATIGL	JE, 96 hours at	60 cps	SN511	3122 10	
INITIAL	DISTRIBUTION	1	PARAMETER	BEHAVIOR A	NALYSIS			 
INTER- VALS	1					20 G		 30 G
	INPUT CURRE	EN T	T AT V <sub>CC</sub> = 6V,	V <sub>IN</sub> = 2.0 N	= 0. TA	= 125 <sup>0</sup> C		
TAMPS		}			<u> </u>			
≥ 67.5 65		7			-			
60		1						
55 50		1						<b></b>
45		1						
35 30		1						
25		t			<u> </u>			
20 ≤17.5	-	1						
	ON LEVEL AT	٠ ٧	cc = 6V, VIN = 2	.0, N = 4 , 1	r_ = 125°C	<del>, , , , , , , , , , , , , , , , , , , </del>		A 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4
VOLTS		<u>֓</u> ֡֝֞֝֞֝֝֡						
≥.30 .29		ł						
.29		1						
. 25		1						
. 23		1						
.19	<b></b>	1						
.15		1						
.11		İ						
\$.10		<b>.</b>				<del>,,,,,</del>		<del>                                      </del>
VOLTS	I LEVEL A	i `	V <sub>CC</sub> = 6V, V <sub>IN</sub> =	0.30 , N = 0,	T <sub>A</sub> = 128	-		
≥ 5.9		1						
5.8								
5.6 5.4	<del>-</del>	ł						
5.2 5.0		1						
4.8		1						
4.4		1						
4.2 ≤ 4.1		ł			<u> </u>			
	1	, ,	ADED) AT V <sub>CC</sub> =		 	<del>, , , , , ,</del>	••	<del></del>
VOLTS	I	]	ADEDIAI VCC	64, VIN - C	7.30, N =			
≥ 3,6	ļ							
3.5		1						
3.3								
2.9		1						
2.5 2.3								
2.1								
1.9 ≤1.8					<u> </u>			
		l						
	<del>*</del>	7				<del>, , , , ,</del>		<del></del>



## SEMICONDUCTOR NETWORKS RELIABILITY DATA QUALITY AND RELIABILITY ASSURANCE DEPARTMENT

TEST PERFORMED:		TYPE TESTED SAMPLE	
CONSTA	NT ACCELERATION (CENTRIF	UGE) SN511 512E 10	
INITIAL DISTRIBUTION	PARAMETER BEHAVIOR ANAI	LYSIS	
INTER- VALS		20,000 G	35,000 G
INPUT CURRENT	TAT VCC = 6V. VIN = 2.0 N = 0	, T <sub>A</sub> = 125°C	
//AMPS			
≥ 67.5			
65			
5.5 50			
45			
35			
30 25 20			
20 £17.5			
	cc = 6V. VIN = 2.0, N = 4, TA =	125°C	<del></del>
VOLTS			
≥.30			<del></del>
.29			
.25			
.21			
.19			
.15			
5.10			
	rcc = 6V, VIN = 0.30 , N = 0, TA	= 125°C	<del></del>
VOLTS			
5 2.9			
5.8 5.6			
5. 4 5. 2			
5.0			
4.6			
4.4			
5 4.1			
OFF LEVEL (LOA	DED) AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30,	N = 4 , TA = 125°C	
VOLTS			
₹ 3.6 3.5			
3.3			
2.9			
2.7			
2.3			
1.9 £1.8			
		<del></del>	

One failure occurred after 35,000 G testing.



## SEMICONDUCTOR NETWORKS RELIABILITY DATA QUALITY AND RELIABILITY ASSURANCE DEPARTMENT

MOISTURE RESISTAN	CE (1 day per cycle)	SN513	SIZE 10	
INITIAL DISTRIBUTION PARAMETER	R BEHAVIOR ANALYS	S		
INTER- VALS		10 Cycles		30 Cycles
INPUT CURRENT AT VCC = 6V	, VIN = 2.0 N = 0, T	_ = 125 <sup>O</sup> C		
// AMPS	F			
≥ 67.5				
65	E			
55	-			
45				
35				
25				
25 20 £17.5	-			
ON LEVEL AT VCC = 6V. VIN =	2.0. N = 0. TA = 125	<del></del>		
VOLTS				
≥.30				
.29	<u> </u>			
25				
21				
.19				
.15				
5,10				
OFF LEVEL AT VCC = 6V. VIN	= 0.30 , N = 0, TA = 1	25 <sup>°</sup> C		
VOLTS				
≥ 5.9		*		
5.8 5.6 5.4				
5.4	_			
5.0 4.8				
4.6	F			
4.2				
\$ 4.1	<u> </u>			
	L	<del></del>	0_	L
OFF LEVEL (LOADED) AT VC	= 6V, V <sub>IN</sub> = 0.30, N	= 5 , T <sub>A</sub> = 125	С	
	<u></u>			
2 3. 6 3. 5	<u></u>			
3.3				
2.9				
2.5				
2, 1				
1.9 ≤ 1.8	<u> </u>			
	E			
				<u></u>

 $\star$  The shift in Voff after 30 cycles of moisture resistance was due to improper reading of initial and post 10 cycle Voff parameters.



TEST PERFORMED:	SALT ATMOSPHERE	SN513 SIZE 10	
INITIAL DISTRIBUTION	PARAMETER BEHAVIOR ANA	LYSIS	
INTER- VALS		24 Hours	48 Hours
INPUT CURREN	IT AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 2.0 N = 0	. TA = 128°C	
JIAMPS			
65			
55 50			
45 40			
35 30			
25 20			
517.5			<del></del>
ON LEVEL AT V	CC = 6V, VIN = 2.0, N = 0, TA =	125°C	
≥.30			
.29			
.25			
.19			
.17			
.13 .11 £.10			
	V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30 , N = 0, T <sub>A</sub>	= 125°C	<del></del>
VOLTS			
≥ 5.9 5.8			
5.6 5.4			
5.2 5.0			
4.6			
4.4			
5.4.1			
OFF LEVEL (LO	ADED) AT V <sub>CC</sub> = 6V, V <sub>IN</sub> = 0.30,	N= 5 TA=125 C	<del></del>
VOLTS	The state of the s		
₹ 3.6			
3.3			
2.9			
2.5 2.3			
2.1			
\$1.8			

#### F. FAILURE ANALYSIS

The Quality Assurance department performs an analysis on the failures experienced in the test programs described. Through centralization of this activity, two advantages are obtained: (1) Cross pollination of techniques from analysis of other semiconductor device failures. (2) The ability to run a more efficient, better equipped activity on a large scale basis. The failure analysis activity contains over 55 pieces of equipment which are used in analysis. The equipment includes a complete photographic layout, a chlorine etch apparatus for evaluation of oxide surface porosity, a complete metallurgical capability which utilizes a high resolution metalograph and microsection equipment, and an electrical probe capability which allows complete voltage probing under a variety of circuit bias conditions. The flow diagram in Fig. 5 shows the procedures and equipment used in performing failure analysis on semiconductor networks. Results of analyses performed are constantly fed back to product department personnel responsible for process corrective action.

The major reason for failure analysis is to uncover failure mechanisms and develop information to make corrective action possible. There is another reason for failure analysis which becomes more important in highly accelerated testing. This is the discovery that the failure mechanism uncovered cannot exist at lower temperatures. A recent example of this typifies this case: device failures exhibiting high leakage on a 200°C storage test were found to be conductive externally. Analysis of 125°C data using non-parametric statistics showed, with 80% confidence, that this mechanism was non-existent at the lower stress levels. Proper failure analysis is also necessary to separate test error — a difficult task on some of the more complex networks.

Results of failure analysis are utilized in process control changes as well as process changes. These process controls are threefold: quality assurance controls, manufacturing controls, and engineering controls. These controls, together with the utilization of quality material — properly specified and inspected, make up the total control system.

Fig. 5. Semiconductor Network Failure Analysis Procedure

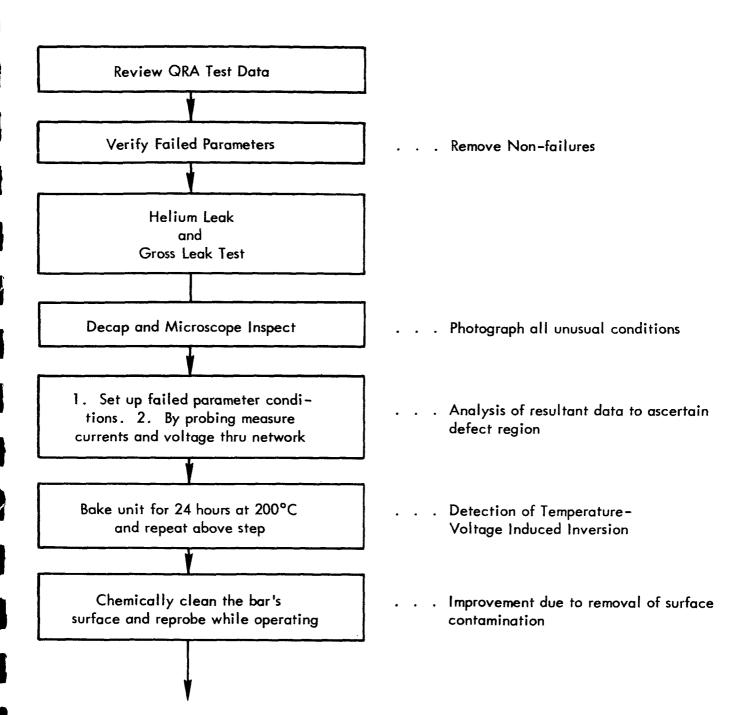
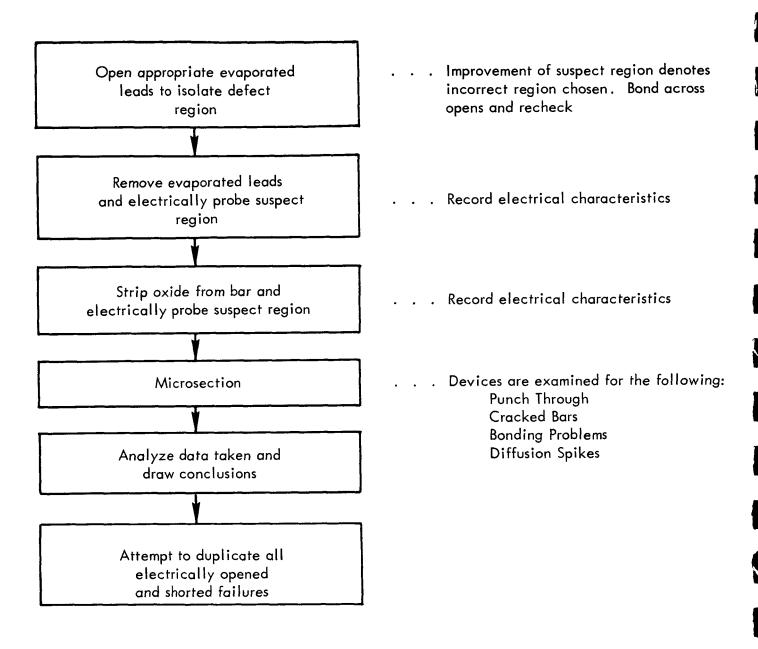


Fig. 5. (Continued)



APPENDIX D

NETWORK APPLICATIONS

#### NETWORK APPLICATIONS

The applications report for the Series 53 SOLID CIRCUIT semiconductor network is due to be published in July. As soon as copies are available, they will be forwarded to JPL.

APPENDIX E

TEST PROCEDURES

DASH NO. REVISIONS SYM ZONE DESCRIPTION DATE **APPROVED** Ā NEXT ASSY NO. INSPECTION TEST PROCEDURE PART I INDIVIDUAL TEST FOR INTEGRATED CIRCUIT SEQUENCE GENERATOR JET PROPULSION LABORATORY CONTRACT NO. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514722 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE TEXAS INSTRUMENTS GOVT OR INDUSTRY ITEM **DWG** NOMENCLATURE OR DESCRIPTION NO. SIZE QTY REQD PART OR IDENTIFYING NO. LIST O F MATERIALS DR TEXAS INSTRUMENTS bd/ INCORPORATED APPARATUS DIVISION DALLAS, TEXAS TITLE **ENGR** TEST PROCEDURE, INSPECTION, PART I, INDIVIDUAL TEST, APPD, INTEGRATED CIRCUIT SEQUENCE GENERATOR W. N. 5-27-64 DESIGN ACTIVITY RELEASE CODE IDENT NO. SIZE DRAWING NO. 514715 96214 5-27-64 1 of 12 SCALE WT SHEET TI-1E1793.A

### TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	4
3.1	Preparation	4
3.2	Room Temperature Test	4
3.2.1	Performance Test No. 1	4
<b>3.</b> 2.2	Performance Test No. 2	5
3.2.3	Performance Test No. 3	6
3.2.4	Performance Test No. 4	6
3.3	Low Temperature Test	6
3.4	High Temperature Test	7
3.5	Vibration Test	7
3.6	Final Test	8
4.	DIAGRAMS	9-10
5.	TABLES	11
5.1	Table I	11
5 <b>.</b> 2	Table II	12

Г	لے	ᢛ	TE	XA	s in	ST	RŲ	ME	NTS	,	CODE IDENT NO.	SIZE	DRAWING NO.		
_	_	4	APP			VISION				•	96214	A	514715		
SYM.	-	+	-		ļ				_		SCALE	WT		SHEET	2

1.	TABLE OF TESTS	Paragraph No.
1.1	Preparation	3.1
1.2	Room Temperature Test	<b>3.</b> 2
1.2.1	Performance Test No. 1	3.2.1
1.2.2	Performance Test No. 2	3.2.2
1.2.3	Performance Test No. 3	3.2.3
1.2.4	Performance Test No. 4	3.2.4
1.3	Low Temperature Test	3.3
1.4	High Temperature Test	3.4
1.5	Vibration Test	<b>3.</b> 5
1.6	Final Test	3.6
2.	LIST OF TEST EQUIPMENT	
2.1	Data Sheet (TI Drawing 514722) shall be completed as part of	this test.
2.2	Verify that test equipment designated WORKING STANDARD, or be currently certified per TI Standard Procedure No. 12-28.	tter, is
2.3	Commercial Test Equipment - The following commercially availa equipment (or equivalent) is required to complete the tests r by this specification.	
2.3.1	Oscilloscope - Tektronix 543/ Plug-in Type CA	
2.3.2	Power Supply, dc, 0-50 VDC, 1.5 amp Sorenson T50-1.5	
2.3.3	Pulse Generator, TI Model 6563 (or equivalent)	
2.3.4	Temperature Chamber - TI Controlled Environmental Unit	
2.3.5	Recorder 18 Channel Visicorder - Honeywell Model 1012	
2.4	Special Test Equipment - The following special test equipment to complete the test required by this specification.	is required
2.4.1	Control Box, TI Drawing 514713	

	ر	78	٦ ٦	ΈX	AB	In	ST	RUI	ME	NTS	CODE IDENT NO.	SIZE	DRAWING NO.		
×		<b>₹</b>	) <u>,</u>				FION			TEXAS	96214	Α	514715		
2	Г										SCALE	WT		SHEET	3

TI-8419

1

The following test procedures cover the systems test requirements to evaluate the Integrated Circuit Sequence Generator.

- 3.1 Preparation
- 3.1.1 Visually inspect the chassis, modules, printed circuit board, etc. for any mechanical faults such as wiring mistakes, broken leads, open welds, etc. before making any connections to the system.
- 3.1.2 Adjust  $V_{cc}$  supply voltage to 3.1 VDC  $\pm$  0.1 VDC.
- 3.1.3 Adjust pulse generator for a partial going pulse (50 nsec to 500 nsec wide) from 0 to  $+3V \pm 0.1V$  at a rate of 1mc  $\pm$  50KC with rise and fall times at a minimum (minimum ringing at 0 and +3 volts).

Caution: Only a positive going signal is to be applied to this system.

#### 3.1.4 Connect Control Box to recorder as follows:

Function	Test Point	Recorder Channel
A Code	7	1
A Word	<b>1</b> 9	2
B Code	5	3
B Word	18	4
C Code	9	5
C Word	10	6
D C <b>ode</b>	12	7
D Word	20	8
E Code	8	9
E Word	16	10
X C <b>ode</b>	6	11
X W <b>or</b> d	4	12
CL	2	13
SP	14	14
TR Code	23	<b>1</b> 5
TR Code	21	16
R Code	13	17
R Code	24	18

- 3.1.5 Set recorder paper feed to 2 inches/second.
- 3.1.6 Connect unit to control box.
- 3.2 Room Temperature Test
- 3.2.1 Performance Test No. 1

	7		TE	XAS	IN	STRU	JME	NTS	CODE IDENT NO.	SIZE	DRAWING NO. 514715			
×	APPARATUS DIVISION DALLAS, YEXAS								96214	Α				
S									SCALE	WT		SHEET	4	

- Connect Ac pin 22 and Co pin 11 to ground.
- Observe the code component outputs on the oscilloscope. See Diagram, Ъ. Section 4 and Table I, Section 5.
  - A Code
  - 2. A Word
  - B Code 3.
  - B Word
  - 5. C Code
  - C Word
  - 7. D Code
  - 8. D Word
  - 9. E Code
  - 10. E Word
  - 11. X Code
  - 12. X Word
  - 13. CL
  - 14. S.P.

The oscilloscope should be triggered on the positive going Note: edge of the specific code's and word detector pulse; i.e., sync on A Word when observing the A Code.

- Reduce the repetition rate of the pulse generator to 10 cps. c.
- d. Turn on recorder for approximately 10 seconds.
- Check the recorded waveforms by performing the following manipulations: e.
  - Check TR Code for Mode 1 operation.
  - 2. Check R Code

Note: See Table II, Section 5 for TR and R Code evaluation.

#### 3.2.2 Performance Test No. 2

Connect Ac pin 22 to ground and Co pin 11 to  $V_{\text{cc}}$ .

Γ	TEXAS INSTRUMENTS								ME	NTS	\$	CODE IDENT NO.	SIZE				
L									•	96214	Δ	514715					
13				L								30214	^				
Ľ	1			<u>L</u>								SCALE	WT		SHEET	5	

- b. Repeat 3.2.1.b.
- c. Repeat 3.2.1.c.
- d. Repeat 3.2.1.d.
- e. Check the recorded waveforms by performing the following manipulations:
  - 1. Check TR Code for Mode 1.
  - 2. Check R Code.

#### 3.2.3 Performance Test No. 3

- a. Connect Ac pin 22 to  $V_{\mbox{cc}}$  and Co pin 11 to ground.
- b. Repeat 3.2.1.b.
- c. Repeat 3.2.1.c.
- d. Repeat 3.2.1.d.
- e. Check the recorded waveforms by performing the following manipulations:
  - Check TR Code for Mode 2.
  - 2. Check R Code.

#### 3.2.4 Performance Test No. 4

- a. Connect Ac pin 22 and Co pin 11 to  $V_{\text{cc}}$ .
- b. Repeat 3.2.1.b.
- c. Repeat 3.2.1.c.
- d. Repeat 3.2.1.d.
- e. Check the recorded waveforms by performing the following manipulations:
  - 1. Check TR Code for Mode 3.
  - 2. Check R Code.
- 3.3 Low Temperature Test
- 3.3.1 Precool temperature chamber to -25°C. Place system connected to control box inside and allow one half hour for stabilization.
- 3.3.2 Repeat 3.2.1.

Γ	TEXAS INSTRUMENTS								M	ENTS	•	CODE IDENT NO.	SIZE	DRAWING NO.	-	
+	ž		ري	APP						TEXA	•	96214	Α	514715		
I	8									SCALE	WT		SHEET	6		

3.3.3	Repeat 3.2.2.
3.3.4	Repeat 3.2.3.
3.3.5	Repeat 3.2.4.
3.4	High Temperature Test
3.4.1	Preheat temperature chamber to $+\ 100^{\rm o}{\rm C}$ . Place system connected to control box inside and allow one half hour for stabilization.
3.4.2	Repeat 3.2.1.
3.4.3	Repeat 3.2.2.
3.4.4	Repeat 3.2.3.
3.4.5	Repeat 3.2.4.
3.5	Vibration Test - The following tests will be performed while repeating paragraph 3.2. (sections d and e).
3.5.1	The assembly shall be attached firmly and securely to the vibration exciter by its normal attachment points. The vibration level shall be observed on the exciter as near to the supporting bracket as possible. The assembly shall be subjected to the vibration test in three mutually perpendicular directions, one of which shall conform as nearly as possible to the booster thrust axis.
3.5.2	Low Frequency Vibration Test - The assembly shall be subjected to sinusoidal vibrations at frequencies between 12 cps and 40 cps for 5 minutes in each of three orthogonal directions. The frequency of vibration shall be swept at a rate varying directly with frequency. The levels and sweep procedures are as follows:
	Amplitude Frequency Time Sweep Method
	3 g's peak 12 to 40 cps 5 minutes Swept once from 12 to 40 cps and back to 12 cps
3.5.3	High Frequency Complex Wave Vibration Test - The test shall consist of the following two segments of combined white Gaussian noise (WGN) band-limited between 40 and 1500 cps and sweeping simusoidal vibration. The sinusoid shall be swept once from 35 cps to 1500 cps and back to 35 cps in the time period of the segment. The total test time shall be eight minutes in each

	TEXAS INSTRUMENTS INCORPORATED APPARATUS DIVISION DALLAS, TEXAS							D	CODE IDENT NO. 96214	SIZE	DRAWING NO. 514715		
SYM.									SCALE	WT		SHEET 7	,

Segment (1) - Combined 10g rms WGN and 4g rms sweeping sinusoid for

of the three directions.

2 minutes.

- b. Segment (2) Combined 5g rms and 4g rms sweeping sinusoid for 6 minutes.
- c. Notes on vibration test:

Note 1 - The complex wave test signal will have the following characteristics.

Partic at Test Level

Time (sec)	Type of Signal	Ratio at Test Level to Calibration	rms g level
0-15	Noise (calibration)	1	2
0-30	None	0	0
Segment 1			
30 <b>~</b> 150	Noise plus sinusoid	5.4	10.8
	Noise only	5	10
	Sinusoid only	2	4
Segment 2			
150-510	Noise plus simusoid	<b>3.</b> 2	6.4
	Noise only	2.5	5
	Sinusoid only	2	4

Note 2 - For creating the random noise, the output of a random noise generator, General Radio Model 1390-A or equivalent, may be used if proper care is taken to ensure the correct amplitude distribution of the signal. For testing the noise generator or any associated equipment, the use of amplitude distribution analyzer, described in JPL Memorandum No. 20-190, is suggested. For ensuring correct noise bandwidth, a filter with an asymptotic slope of at least 24 db per octave and 3 db points at 40 and 1500 cps shall be considered acceptable.

3.6.1 Performance Test No. 1

a. Repeat 3.2.1.

3.6.2 Performance Test No. 2

b. Repeat 3.2.2.

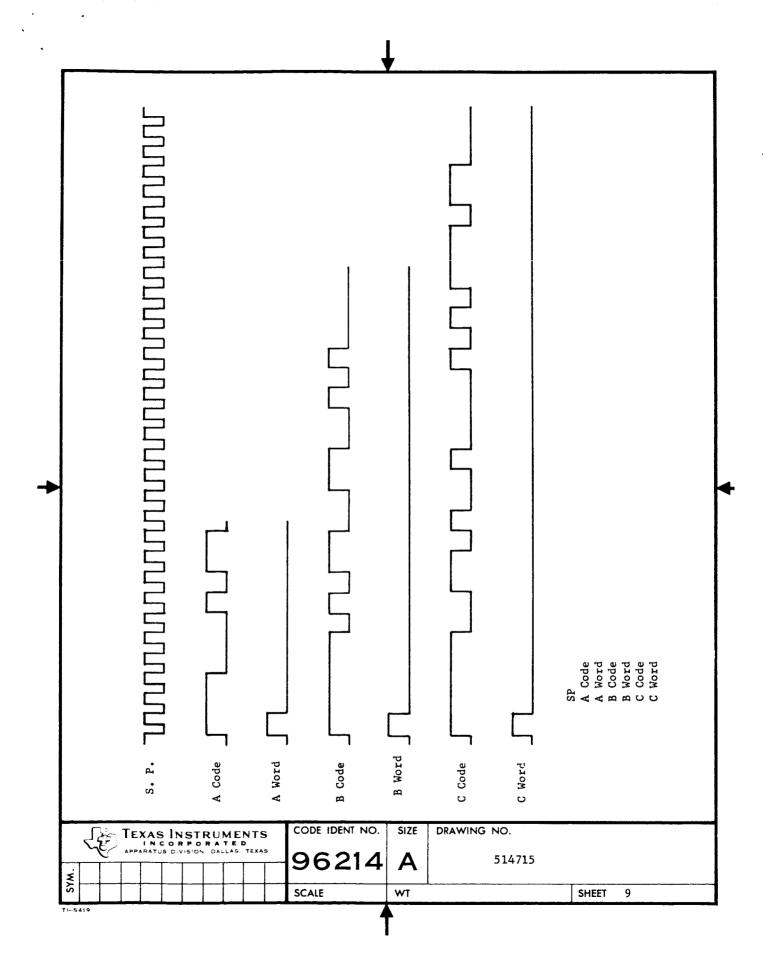
3.6.3 Performance Test No. 3

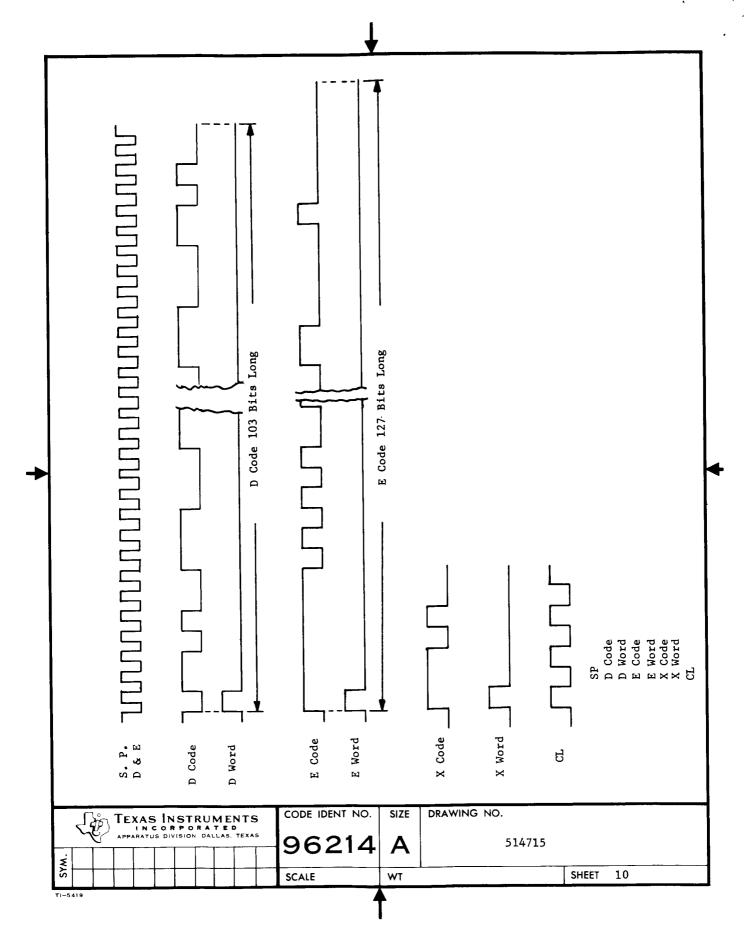
c. Repeat 3.2.3.

3.6.4 Performance Test No. 4

d. Repeat 3.2.4.

		ا مور	TEX	AS	Ins	STRU	ME	NTS	CODE IDENT NO.	SIZE	DRAWING NO.		
<u>₹</u>	LU INCOMPONATED								96214	Α	<b>A</b> 514715		
Š									SCALE	WT		SHEET	8





5. TABLES 5.1 Table I Function Output A Code 11100010110 10000000000 A Word B Code 11111010110011001010000 B Word 1000000000000000000000 C Code 1111100110100100001010111011000 C Word 011010011100011111110001011011101110101 D Code 0010000100110100110111101101010001000100 101110000000111000110100 D Word E Code 1111000101000011000001000000 E Word X Code 1110100 1000000 X Word CL10

r	لے	ने	\ <b>T</b>	ΈX	AS	l N	ST	RU	ME	NTS	;	CODE IDENT NO.	SIZE	DRAWING NO.	
×	APPARATUS DIVISION DALLAS, TEXAS				•	96214	Α	514715							
λ			$\perp$									SCALE	W		SHEET 11

TI--5419

5.2 Table II

Output

Code Combination

Rtn+2 Code

 $(\mathtt{A} \oplus \mathtt{B} \oplus \mathtt{C} \oplus \mathtt{D} \oplus \mathtt{E})_{\mathtt{tn}} \oplus \mathtt{X}_{\mathtt{tn+1}}$ 

TRtn+2 Code

Mode 1  $\mathtt{CL}_{\mathtt{tn+l}}$ 

TRtn+2 Code

Mode 2

TR<sub>tn+2</sub> Code

Mode 2

	۲	48 I	TE	KAS	IN	STR	UM	ENTS		CODE IDENT NO.	SIZE	DRAWING NO. 514715		
ا	IN CORPORATED APPARATUS DIVISION DALLAS, TEXAS				•	96214	96214 A							
8	$\vdash$	$T^-$			$\forall$		+	+		SCALE	WT	<u> </u>	SHEET	12

DASH NO. REVISIONS SYM ZONE DESCRIPTION DATE APPROVED ΩŢ NEXT ASSY NO. INSPECTION TEST PROCEDURE Š Š Š 9 PART I INDIVIDUAL TEST FOR TRANSMITTER AND RECEIVER NO. 2 MODULE INTEGRATED CIRCUIT SEQUENCE GENERATOR Contract No. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514723 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE -1 TEXAS INSTRUMENTS GOVT OR INDUSTRY ITEM DWG NOMENCLATURE OR DESCRIPTION SIZE QTY REQD PART OR IDENTIFYING NO. LIST O F MATERIALS DR TEXAS INSTRUMENTS INCORPORATED CKD APPARATUS DIVISION DALLAS, TEXAS 5-26-64 TITLE TEST PROCEDURE, INSPECTION, PART I, INDIVIDUAL TEST, TRANSMITTER AND RECEIVER NO. 2 MODULE 5-21-64 DESIGN ACTIVITY RELEASE CODE IDENT NO. SIZE DRAWING NO. 514716 96214 Α 5-27-64 **SCALE** WT SHEET 1 of 12

# TABLE OF CONTENTS

Paragraph No.	Ti	tle	Sheet N	lo•
1.	TABLE OF TESTS		3	
2.	LIST OF TEST EQUIPMENT		3	
3.	TEST PROCEDURES		4	
3.1	Preparation		4	
3.2	Room Temperature Test		4	
3.3	Low Temperature Test		7	
3.4	High Temperature Test		8	
4.	DIAGRAMS		9-10	)
5.	TABLE I		11-1:	2

Texas Instruments	CODE IDENT NO.	SIZE	DRAWING NO.		
INCORPORATED APPARATUS DIVISION DALLAS, TEXAS	96214	Α	514716		
XS SX	SCALE	WT		SHEET	2

	Pa	ragraph No.
1.	TABLE OF TESTS	
1.1	Preparation	3.1
1.2	Room Temperature Test	3.2
1.3	Low Temperature Test	3.3
1.4	High Temperature Test	3.4
2.	LIST OF TEST EQUIPMENT	
2.1	Data Sheets (TI Drawing 514723) shall be completed as part of thi	s test.
2.2	Verify that test equipment designated WORKING STANDARD, or better currently certified per TI Std. Procedure No. 12-28.	, is
2.3	Commercial Test Equipment - The following commercially available equipment (or equivalent) is required to complete the test requirthis specification.	
2.3.1	Oscilloscope - Tektronix 543/Plug-in Type CA	
2.3.2	Power Supply, de. 0-50 VDC, 1.5 amp Sorenson T50-1.5	
2.3.3	Pulse Generator, TI Model 6563	
2.3.4	Temperature Chamber - TI Controlled Environmental Unit	
2.4	Special Test Equipment - The following special test equipment is to complete the test required by this specification.	required
2.4.1	Test Set, Module, TI Drawing 514711	
2.4.2	Control Box, TI Drawing 514713	
2.4.3	Five Stage Counter, TI Drawing 514714	

TEXAS INSTRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.		
APPARATUS DIVISION DALLAS, TEXAS	96214	Α	514716		
	SCALE	WT		SHEET	3

#### TEST PROCEDURES

The following test procedure covers the module test requirements to evaluate the Transmitter and Receiver No. 2 module of the Integrated Circuit Sequence Generator.

- 3.1 Preparation
- 3.1.1 Visually inspect module for any mechanical faults such as wiring mistakes, broken leads, bad welds, etc. before plugging module into test set.
- 3.1.2 Adjust  $V_{cc}$  supply voltage to 3.1 VDC  $\pm$  0.1 VDC
- 3.1.3 Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide) from 0 to  $+3V \pm 0.1V$  at a rate of lmc  $\pm 50KC$  with rise and fall times at a minimum (minimum ringing at 0 and +3 volts).

Caution: Only a positive going signal is to be applied to these modules.

- 3.1.4 Plug module into test set.
- 3.1.5 Connect test set to control box.
- 3.1.6 Connect  $V_{cc}$  to test point 25 and GRD to test point 26 of control box.
- 3.1.7 Connect the five stage counter to control box as follows:

Counter Lead	Control Box
$s_1$	Test Point 20 $(\underline{X})$
$\frac{S_1}{S_1}$	Test Point 15 $(\overline{X})$
	Test Point 3 ( $\underline{D}$ )
<u>S2</u> S2	Test Point 17 $(\overline{D})$
	Test Point 19 ( $\underline{\mathbf{E}}$ )
<u>83</u> 83	Test Point 7 $(\overline{E})$
	Test Point 2 (1)
<u>\$4</u> \$4	No Connection
<u>S</u> 5	Test Point 10 (2)
<u>55</u>	No Connection

3.1.8 Connect pulse generator to test point 13 of the control box.

Note: Oscilloscope should be triggered on the positive going edge of  $\overline{S_5}$ .

- 3.2 Room Temperature Test
- 3.2.1 Performance Test No. 1
  - a. Connect the following test points to GRD.
    - 1. TP 14 (CL)

	Texas Instruments									CODE IDENT NO.	SIZE			
i i	INCORPORATED					•	96214	Α	514716					
=										SCALE	WT		SHEET	4

TI-5419			<b>†</b>	
		SCALE	WT	SHEET 5
( <b>5 W</b> ) 1 K	CORPOR	CODE IDENT NO.	SIZE DRAWING NO. 51471	
	a.	Connect the fo <u>llowing</u> t  1. TP 6 (CL)  2. TP 9 (CO)	est points to GRD.	
3.2.4	Perfo	mance Test No. 4		
	c.	Observe the outputs of Diagram, Section 4, and 1. R TP 22 2. R TP 21 3. TR TP 8 4. TR TP 16	the module on the oscillo Table I, Section 5.	scope. See
i	b.	Connect the fo <u>llowing</u> to the following	est points to $V_{CC}$ .	
	а.	Connect the following t  1. TP 14 (CL)  2. TP 9 (CO)	est points to GRD.	
3.2.3	Perfo	mance Test No. 3		
	c.	Observe the outputs of Diagram, Section 4, and 1. R TP 22 2. R TP 21 3. TR TP 8 4. TR TP 16	the module on the oscillo Table I, Section 5.	scope. See
	b.	Connect the following to 1. TP 14 (CL) 2. TP 1 (AC) 3. TP 9 (CO)	est points to V <sub>cc</sub> .	
	a.	Connect the following to the following t	est points to GRD.	
3.2.2	Perfor	mance Test No. 2		
	c.	Observe the outputs of Diagram, Section 4, and 1. R TP 22 2. R TP 21 3. TR TP 8 4. TR TP 16	the module on the oscillon Table I, Section 5.	scope. See
	b.	Connect the fo <u>llowing</u> t  1. TP 6 (CL)  2. TP 1 (AC)  3. TP 9 (CO)	est points to $V_{cc}$ .	

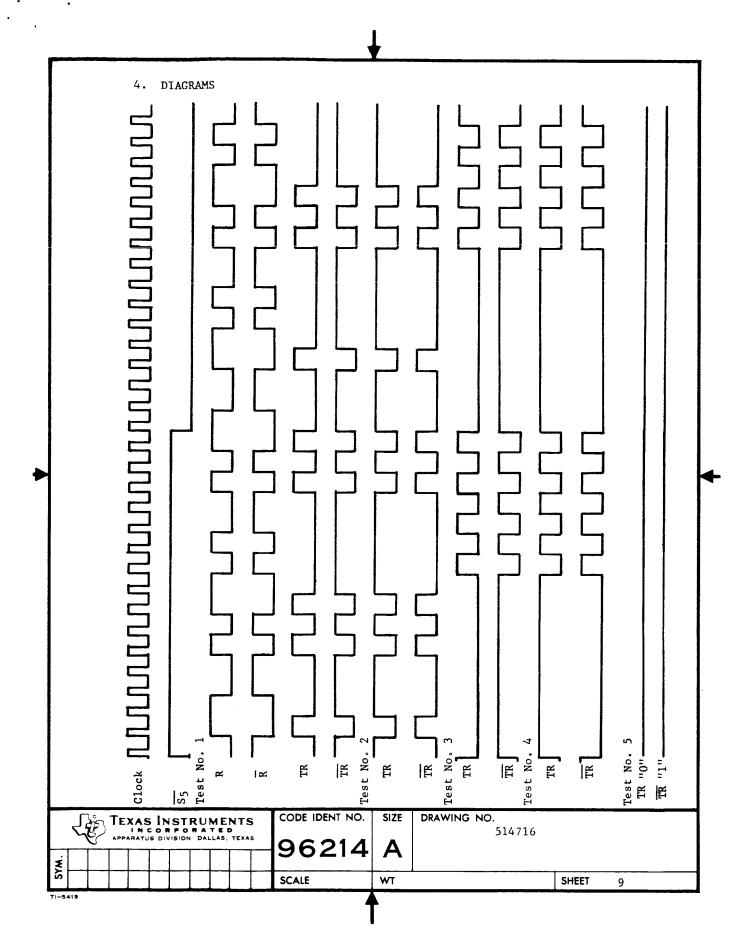
	b.	1.	the f CP 14 CP 1		points	to V <sub>cc</sub> .		
	с.	Diagram 1. 1 2. 1	, Sect R 7 <u>TR</u> 7	outputs of the tion 4, and Tab TP 22 TP 21 TP 8 TP 16	module	on the oscilloscope. Section 5.	See	
3.2.5	Perf	ormance To	est No	o. 5				
	а.	1.	the f TP 14 TP 1		points	to GRD.		
	b.	1.	the : TP 6 TP 9		points	to V <sub>cc</sub> .		
	c.	Diagram 1. 2. 3.	, Sec R R TR	outputs of the tion 4, and Tal TP 22 TP 21 TP 8 TP 16		on the oscilloscope. Section 5.	See	
3.2.6	Perf	ormance T	est No	o. 6				
	а.	1.	the : TP 6 TP 1		points	to GRD.		
	ь.	1.	the TP 14 TP 9		points	s to V <sub>CC</sub> .		
	с.	Diagram 1. 2. 3.	, Sec <u>R</u> R <u>TR</u>	outputs of the tion 4, and Ta TP 22 TP 21 TP 8 TP 16		e on the oscilloscope. Section 5.	See	
3.2.7	Perf	ormance T	est N	o. 7				
	a.	1. 2.	TP 14 TP 1	following test (CL) (AC) (CO)	points	s to GRD.		
<b>₹₩</b>	NCORP	TRUMENTO RATED		CODE IDENT NO. 96214	SIZE	DRAWING NO. 514716		
**				90214			SHEET	6
					l wt			

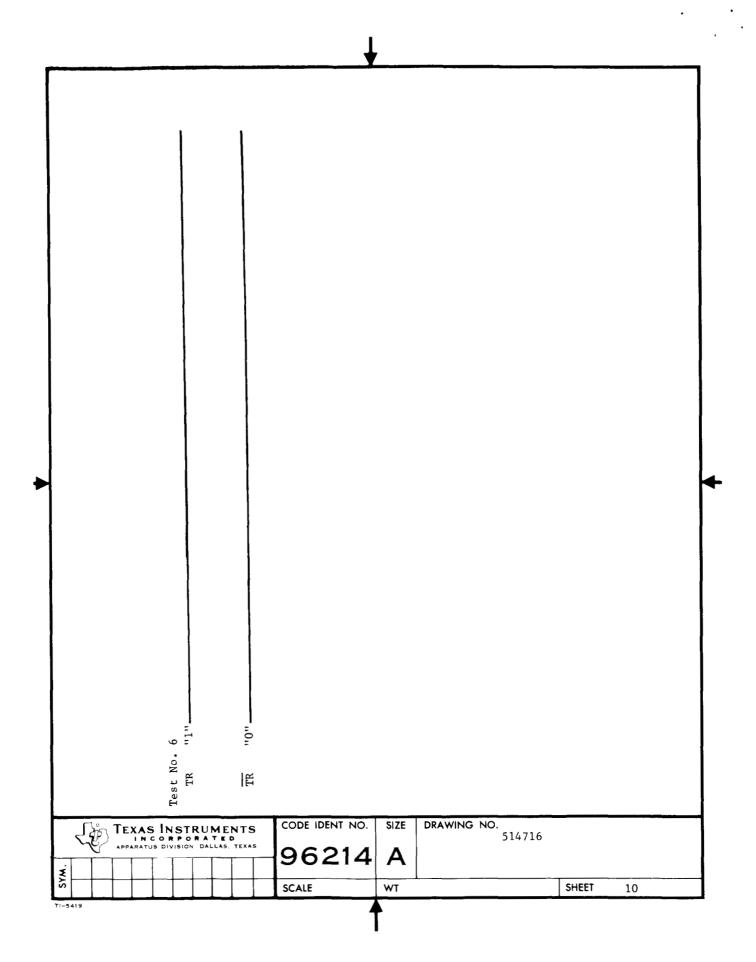
- Connect the following test points to  $V_{cc}$ . b. TP 6 (CL)
- Observe the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
  - TP 22 1. R
  - TP 21 2. R
  - 3. TP 8 TR
  - TP 16 TR
- 3.2.8 Performance Test No. 8
  - Connect the following test points to GRD. a.
    - TP 6 (CL) 1.
    - TP 1 (AC) 2.
    - 3. TP 9 (CO)
  - Connect the following test points to  $V_{\mbox{cc}}$ . ъ.
    - TP 14 (CL)
  - Observe the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
    - TP 22 R
    - 2. R TP 21
    - 3. TR TP 8
    - 4. TR TP 16
- 3.3 Low Temperature Test
- 3.3.1 Precool temperature chamber to -25°C. Place test set with module plugged-in, inside and allow one half hour for stabilization.
- 3.3.2 Repeat 3.2.1
- 3.3.3 Repeat 3.2.2
- 3.3.4 Repeat 3.2.3
- 3.3.5 Repeat 3.2.4
- 3.3.6 Repeat 3.2.5
- 3.3.7 Repeat 3.2.6
- 3.3.8 Repeat 3.2.7
- 3.3.9 Repeat 3.2.8

TEXAS IN	STRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.		
	PORATED VISION DALLAS, TEXAS	96214	<b>A</b> 514716			
\$		SCALE	WT		SHEET	7

3.4	High Temperature Test
3.4.1	Preheat temperature chamber to $+100^{\rm o}{\rm C}$ . Place test set, with module plugged-in, inside and allow one half hour for temperature stabilization.
3.4.2	Repeat 3.2.1
3.4.3	Repeat 3.2.2
3.4.4	Repeat 3.2.3
3.4.5	Repeat 3.2.4
3.4.6	Repeat 3.2.5
3.4.7	Repeat 3.2.6
3.4.8	Repeat 3.2.7
3.4.9	Repeat 3.2.8

	TEXAS INSTRUMENTS									NTS	•	CODE IDENT NO.	SIZE	E DRAWING NO. 514716			
L	<b></b>								•	96214	Α	5247.20					
										SCALE	WT		SHEET	8			





5.	TA	BL	E	Ι

I

---

Performance Test	<u>Function</u>	Output
No. 1	R R TR TR S5	01100101101001011001101001011010 10011010010
No. 2	R TR TR S5	Same as $\underline{R}$ for Performance Test No. 1 Same as $\overline{R}$ for Performance Test No. 1 101110101111110101111101011111 01000101000001010001000001010000 Same as $\overline{S5}$ for Performance Test No.1
No. 3	R R TR <u>TR</u> S <sub>5</sub>	Same as R for Performance Test No. 1 Same as R for Performance Test No. 1 000000000101010101000000000101010111111
No. 4	R R TR TR S5	Same as $\overline{R}$ for Performance Test No. 1 Same as $\overline{R}$ for Performance Test No. 1 11111111110101010111111111111111111
No. 5	<u>R</u> R TR TR S <sub>5</sub>	Same as $\frac{R}{R}$ for Performance Test No. 1 Same as $\frac{R}{R}$ for Performance Test No. 1 All zero's All one's Same as $\frac{8}{8}$ for Performance Test No.1
No. 6	<u>R</u> R <u>TR</u> T <u>R</u> S <sub>5</sub>	Same as $\overline{R}$ for Performance Test No. 1 Same as $\overline{R}$ for Performance Test No. 1 All one's All zero's Same as $\overline{S_5}$ for Performance Test No.1
No. 7	R R TR TR S <sub>5</sub>	Same as $R$ for Performance Test No. 1 Same as $R$ for Performance Test No. 1 All zero's All one's Same as $\overline{S}_5$ for Performance Test No. 1

	۲	å	TE	XA	s la	ISTI	RUN	1 E	NTS		CODE IDENT NO.	SIZE	DRAWING NO.		
¥.	Γ	6	\ \			VISION				$\dashv$	96214	Α	514716	514716	
\ XS										1	SCALE	WT		SHEET	11

1

Performance Test	<u>Function</u>	Output
No. 8	<u>R</u> R <u>TR</u> <u>TR</u> S 5	Same as $\overline{R}$ for Performance Test No. 1 Same as $\overline{R}$ for Performance Test No. 1 All one's All zero's Same as $\overline{S_5}$ for Performance Test No. 1

Γ	TEXAS INSTRUMENTS									CODE IDENT NO.	SIZE	DRAWING NO. 514716		
-	<b>L</b>						DALI	LAS,	TEXAS	96214	Α			
\$										SCALE	WT		SHEET	12

DASH NO. REVISIONS SYM ZONE DESCRIPTION DATE APPROVED QTY <u>S</u> S INSPECTION TEST PROCEDURE PART I INDIVIDUAL TEST FOR TRANSMITTER AND RECEIVER NO. 1 MODULE INTEGRATED CIRCUIT SEQUENCE GENERATOR CONTRACT NO. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514724 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE. TEXAS INSTRUMENTS GOVT OR INDUSTRY -1 ITEM DWG NOMENCLATURE OR DESCRIPTION QTY REQD SIZE PART OR IDENTIFYING NO. LIST O F MATERIALS DR DATE TEXAS INSTRUMENTS 123/64 INCORPORATED APPARATUS DIVISION DALLAS, TEXAS TITLE TEST PROCEDURE, INSPECTION, PART I, INDIVIDUAL TEST, TRANSMITTER AND RECEIVER NO. 1 MODULE 5-27-64 DESIGN ACTIVITY RELEASE CODE IDENT NO. DRAWING NO. SIZE 96214 5-27-64 514717 WT SHEET 1 of 7 SCALE TI-1E1793-A

### TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	3
3,1	Preparation	3
3.2	Room Temperature Test	4
3.3	Low Temperature Test	4
3.4	High Temperature Test	5
4.	DIAGRAMS	6
5.	TABLE I	7

And lexas instruments	CODE IDENT NO.	SIZE	DRAWING NO.	
APPARATUS DIVISION DALLAS TEXAS	96214	Α	514717	
X X X X X X X X X X X X X X X X X X X	SCALE	WT		SHEET 2

TI--JE1793-1-A

1.1	TABLE OF TESTS			•	D 1					
1.1		Paragraph No.								
	Preparation				3.1					
1.2	Room Temperature	Test			3.2					
1.3	Low Temperature T	es <b>t</b>			3.3					
1.4	High Temperature	Test		3.4						
2.	LIST OF TEST EQUI	PMENT								
2.1	Data Sheets (TI I	rawing 514724)	shall	be completed as part	of this test.					
2.2	Verify that test currently certifi	equipment designed per TI Stand	gnated lard Pi	WORKING STANDARD, or cocedure No. 12-28.	better, is					
2.3	Commercial Test F equipment (or equ by this specifica	ivalent) is red	follow quired	ving commercially ava to complete the test	ilable test s required					
2.3.1	Oscilloscope - Te	scope - Tektronix 543/Plug-in Type CA								
2.3.2	Power Supply, dc,	Supply, dc, 0-50 VDC, 1.5 amp Sorenson T50-1.5								
2.3.3	Pulse Generator, TI Model 6563									
2.3.4	Temperature Chamber - TI Controlled Environmental Unit									
2.4		Test Equipment - The following special test equipment is to complete the test required by this specification.								
2.4.1	Test Set, Module,	odule, TI Drawing 514711								
2.4.2	Control Box, TI	rawing 514713								
2.4.3	Five Stage Counte	er, TI Drawing	14714							
3.	TEST PROCEDURES									
		smitter and Rec		ne module test requir No. 1 Module of the						
3.1	Preparation				!					
3.1.1				nical faults such as volugging module into						
TEXAS	INSTRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.						
APPARATUS DI	VISION DALLAS TEXAS	96214	Α	514717						
		SCALE	WT SHEET 3							

- 3.1.2 Adjust  $V_{CC}$  supply voltage to 3.1  $VDC \pm 0.1$  VDC.
- 3.1.3 Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide) from 0 to  $+3V \pm 0.1V$  at a rate of  $1mc \pm 50kc$ , with rise and fall times at a minimum (minimum ringing at 0 and +3 volts).

CAUTION: Only a positive going signal is to be applied to these modules.

- 3.1.4 Plug module into test set.
- 3.1.5 Connect test set to control box.
- 3.1.6 Connect V<sub>CC</sub> to test point 25 and ground to test point 26 of control box.
- 3.1.7 Connect the five stage counter to control box as follows:

Counter Lead	Control Box
$s_1$	Test Point 14 (A)
$\overline{s_1}$	Test Point 15 $(\overline{A})$
$s_2$	Test Point 6 (B)
$\overline{s_2}$	Test Point $7(\overline{B})$
s <sub>3</sub>	Test Point 12 (C)
$\overline{s_3}$	Test Point 5 $(\overline{C})$
s <sub>4</sub>	Test Point 17 (D)
<u>s</u> 4	No Connection
s <sub>5</sub>	Test Point 19 (E)
<u>s</u> 5	No Connection

3.1.8 Connect pulse generator positive output to test point 20 of the control box.

NOTE: Oscilloscope should be triggered on the positive going edge of  $\overline{S_5}$ .

- 3.2 Room Temperature Test
- 3.2.1 Observe the output (Section 4 and 5) of the module on the oscilloscope.
- 3.3 Low Temperature Test
- 3.3.1 Precool temperature chamber to -25 °C. Place test set with module connected inside chamber and allow one half hour for stabilization.

r	Texas Instruments										s	CODE IDENT NO.	SIZE	SIZE DRAWING NO.			
\\	INCORPORATED APPARATUS DIVISION DALLAS TEXAS										5	96214	Α	514717			
3	\$									SCALE	WT		SHEET 4				

1E1793-1-A

3.3.2 Repeat 3.2.1

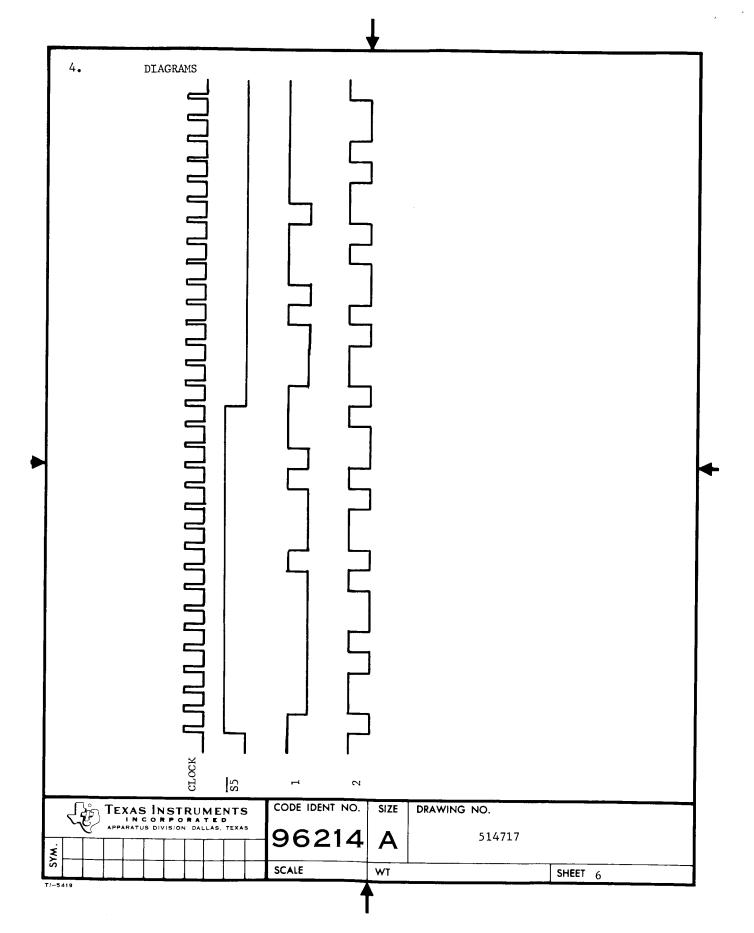
3.4 High Temperature Test

3.4.1 Preheat temperature chamber to +100°C. Place test set with module connected inside chamber and allow one half hour for stabilization.

3.4.2 Repeat 3.2.1

r	ſ	Jos Ons	7								CODE IDENT NO.	SIZE	DRAWING NO.		
	INCORPORATED APPARATUS DIVISION DALLAS TEXAS									96214	Α	514717			
3	5			+	t	<u> </u>	1-	$\vdash$	$\vdash$	† † † †	SCALE	WT		SHEET	5

TI--1E1793-1-A



5. TABLE I

Function

Output

1 (Test Point 22)

10000000100010111000101110111111

2 (Test Point 21)

01101001011010010110100101101001

TEXAS INSTRUMENTS
INCORPORATED
APPARATUS DIVISION DALLAS. TEXAS

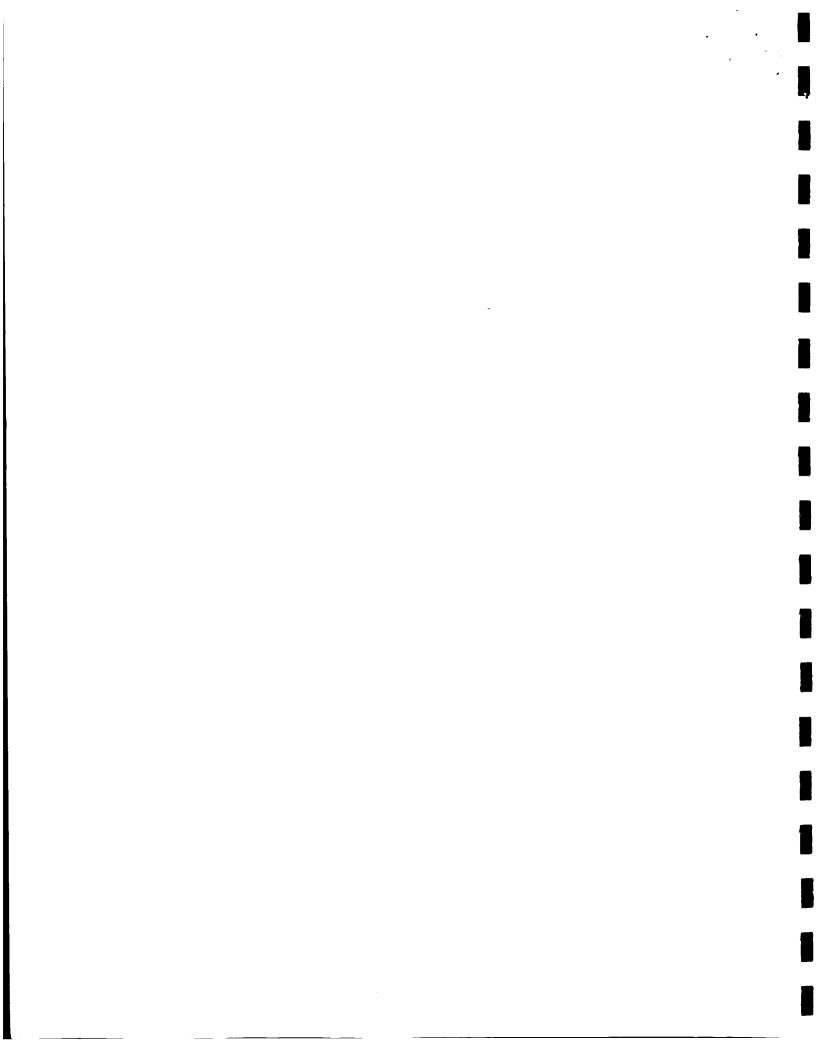
96214

SCALE

WT

SHEET 7

--5A19



DASH NO. REVISIONS SYM ZONE DESCRIPTION DATE APPROVED QTY  $\omega$ 1 NEXT ASSY NO. 5/4 INSPECTION TEST PROCEDURE S<sub>O</sub> e PART I INDIVIDUAL TEST FOR D SEQUENCE GENERATOR MODULE INTEGRATED CIRCUIT SEQUENCE GENERATOR Contract No. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514725 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE TEXAS INSTRUMENTS GOVT OR INDUSTRY ITEM DWG NOMENCLATURE OR DESCRIPTION QTY REQD NO. PART OR IDENTIFYING NO. LIST O F MATERIALS DR BD/ DATE TEXAS INSTRUMENTS 3/26/64 INCORPORATED CKD APPARATUS DIVISION DALLAS. TEXAS 526 64 TEST PROCEDURE, INSPECTION, PART I, INDIVIDUAL TEST, APPD D SEQUENCE GENERATOR MODULE homa, 201 5-27-69 DESIGN ACTIVITY RELEASE CODE IDENT NO. SIZE DRAWING NO. 514718 96214 A 5-27.64 **SCALE** WT SHEET 1 of 9 T! 1E1793 A

## TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	4
3.1	Preparation	4
3.2	Room Temperature Test	4
3.3	Low Temperature Test	5
3.4	High Temperatore Test	5
4.	DIAGRAMS	6-7
5.	TABLE I	8-9

Texas Instruments	CODE IDENT NO.	SIZE	DRAWING NO.	,	
I EXAS INSTRUMENTS IN CORPORATED APPARATUS DIVISION DALLAS, TEXAS	96214	Α	514718		
8	SCALE	WT		SHEET	2

1-5419

		Paragraph No.
1.	TABLE OF TESTS	
1.1	Preparation	3.1
1.2	Room Temperature Test	3.2
1.3	Low Temperature Test	3.3
1.4	High Temperatore Test	3.4
2.	LIST OF TEST EQUIPMENT	
2.1	Data Sheets (TI Drawing 514725) shall be completed as p	art of this test.
2.2	Verify that test equipment designated WORKING STANDARD, currently certified per TI Std. Procedure No. 12-28.	or better, is
2.3	Commercial Test Equipment - The following commercially equipment (or equivalent) is required to complete the tthis specification.	available test est required by
2.3.1	Oscilloscope - Tektronix 543/Plug in Type CA	
2.3.2	Power Supply, de, 0-50 VDC, 1.5 amp Sorenson T50-1.5	
2.3.3	Pulse Generator, TI Model 6563	
2.3.4	Temperature Chamber - TI Controlled Environmental Unit	
2.4	Special Test Equipment - The following special test equ to complete the test required by this specification.	ipment is required
2.4.1	Test Set, Module, TI Drawing 514711	
2.4.2	Control Box, TI Drawing 514713	

	TEXAS INSTRUMENTS INCORPORATED APPARATUS DIVISION DALLAS, TEXAS						•	CODE IDENT NO.		DRAWING NO.	/ING NO. 514718			
ž								96214	A					
S								SCALE	WT			SHEET	3	

	3.	TEST PROCEDURES
		The following test procedure covers the module test requirements to evaluate the D Sequence Generator Module of the Integrated Circuit Sequence Generator.
	3.1	Preparation
	3.1.1	Visually inspect module for any mechanical faults such as wiring mistakes, broken leads, bad welds, etc. before plugging module into test set.
	3.1.2	Adjust $V_{cc}$ supply voltage to 3.1 VDC $\pm$ 0.1 VDC.
	3.1.3	Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide) from 0 to $+3V \pm 0.1V$ at a rate of lmc $\pm$ 50KC with rise and fall times at a minimum (minimum ringing at 0 and $+3$ volts).
		Caution: Only a positive going signal is to be applied to these modules.
	3.1.4	Plug module into test set.
	3.1.5	Connect test set to control box.
	3.1.6	Connect $V_{\text{CC}}$ to test point 25, and ground to test point 26 of control box.
	3.1.7	Connect pulse generator positive output to test point 7 of control box.
		Note: Oscilloscope should be triggered on the positive going edge of D Word.
	3.2	Room Temperature Test
		Observe the following outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
		a. <u>D7</u> TP 5
		b. $\overline{D7}$ TP 19 c. $\underline{D6}$ TP 18
		d. D <sub>6</sub> TP 1
		e. $\overline{D_5}$ TP 11 f. $\overline{D_5}$ TP 4
		$h. \frac{\overline{Q}}{\overline{Q}_L}$ TP 24
		i. D3 TP 16 j. D3 TP 17
		i. $D_3$ TP 16         j. $\overline{D_3}$ TP 17         k. $D_2$ TP 8         1. $\overline{D_2}$ TP 21
		1. $\frac{-2}{D_2}$ TP 21
		$\begin{array}{ccc} \mathbf{m} \bullet & \underline{\mathbf{D}}_{\underline{1}} & \mathbf{TP} & 22 \\ \mathbf{n} \bullet & \overline{\mathbf{D}}_{\underline{1}} & \mathbf{TP} & 9 \end{array}$
		o. D Word TP 3
	Jan Texas	INSTRUMENTS CODE IDENT NO. SIZE DRAWING NO.
	APPARATUS	OR FOR A T E D OR FOR A T E D OR FOR A T E D OR FOR A T E D  514718
ż		96214 A
SYM		SCALE WT SHEET 4
_		

TI--5419

3.3	Low Temperature Test
3.3.1	Precool temperature chamber to $-25^{\rm o}{\rm C}$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
3.3.2	Repeat 3.2.1
3.4	High Temperature Test
3.4.1	Preheat temperature chamber to $100^{\circ}\text{C}$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
3.4.2	Repeat 3.2.1

	TEXAS INSTRUMENTS									CODE IDENT NO.	SIZE	DRAWING NO.	514718		
-									 96214	Α					
λX	$\vdash$							SCALE	WT	· · · · · · · · · · · · · · · · · · ·		SHEET	5		

Ti-5419

4. DIAGRAMS JUNION MONOMENT ğ D1 15  $\mathbf{D_2}$  $\frac{D}{2}$ **D**3 13 D4 107 5 **D**5 **D**6 90 TEXAS INSTRUMENTS
INCORPORATED
APPARATUS DIVISION DALLAS, TEXAS CODE IDENT NO. DRAWING NO. SIZE 514718 96214 A SYM. SCALE WT SHEET 6

monument 103 bits Ā 16  $D_7$ TEXAS INSTRUMENTS
INCORPORATED
APPARATUS DIVISION DALLAS, TEXAS CODE IDENT NO. SIZE DRAWING NO. 514718 96214 A SYM. SHEET SCALE WT 7

-	m. n. r		
5.	TABLE	4 1	
	Funct	ion	Output
	a.	D <sub>7</sub>	11111110000001000101110011101010 111110100001110001001
	ъ.	<del>D</del> 7	00000001111110111010011000101011 000001011110001110110
	c.	D <sub>6</sub>	11111100000010001011001110101001 11110100001110001001
	d.	D <sub>6</sub>	00000011111101110100110001010110 00001011110001110110
	e.	D <sub>5</sub>	11111000000100010110011101010011 1110100001110001001
	f.	D <sub>5</sub>	000001111111011101001100010101100 0001011110001110110
	g.	D4	11110000001000101100111010100111 110100001110001001
	h.	<u>D4</u>	000011111101110100110001010111000 001011110001110110
	<b>i.</b>	D <sub>3</sub>	11100000010001011001110101001111 10100001110001001

	TEXAS INSTRUMENTS									NTS	CODE IDENT NO.	SIZE	DRAWING NO.	514718		
Ŀ	APPARATUS DIVISION DALLAS, TEXAS					TEXAS	96214	96214 A								
SYA											 SCALE	WT		-	SHEET	8

**Function** Output 00011111101110100110001010110000 j. D<sub>3</sub> 01011110001110110110010010100100 00100111001011010001000110011010 1010000 k. 11000000100010110011101010011111  $D_2$ 01000011100010010011011010110111 10110001101001011101110001100101 01011111  $\overline{D}_2$ 001111110111010011000101011000001. 10111100011101101100100101001000 01001110010110100010001100110101 0100000 10000001000101100111010100111110 m.  $D_1$ 10000111000100100110110101101111 01100011010010111011100011001010 10111111  $\overline{\mathtt{D}_1}$ 01111110111010011000101011000001n. 0111100011101101100100101001000010011100101101000100011001101010 1000000 ο. D Word 000000

				STRU	MENTS	CODE IDENT NO.	SIZE	DRAWING NO. 514718	,		-
<u> </u>	<b>6</b> 57					96214	Α				
l S						SCALE	WT		SHEET	9	

T!-5419

DASH NO. REVISIONS SYM DATE APPROVED ZONE DESCRIPTION SIZE INSPECTION TEST PROCEDURE Š Š PART I INDIVIDUAL TEST FOR D OUTPUT GATING NO. 2 MODULE INTEGRATED CIRCUIT SEQUENCE GENERATOR CONTRACT NO. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514726 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE TEXAS INSTRUMENTS | GOVT OR INDUSTRY -2 DWG ITEM NOMENCLATURE OR DESCRIPTION NO. QTY REQD PART OR IDENTIFYING NO. MATERIALS LIST O F DR DATE Texas Instruments BD/ 3/26/64 INCORPORATED CKD APPARATUS DIVISION DALLAS, TEXAS 5-26-64 TITLE ENGR TEST PROCEDURE, INSPECTION, PART I, APPD INDIVIDUAL TEST, W D OUTPUT GATING NO. 2 MODULE CODE IDENT NO. DESIGN ACTIVITY RELEASE SIZE DRAWING NO. 514719 5-27-44 96214 Α SHEET 1 of 8 SCALE WT

### TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	4
3.1	Preparation	4
3.2	Room Temperature Test	4
3.3	Low Temperature Test	6
3.4	High Temperature Test	6
4.	DIAGRAMS	7
5.	TABLE I	. 8

	TEXAS INSTRUMENTS IN CORPORATED APPARATUS DIVISION DALLAS, TEXAS									NTS	3	CODE IDENT NO.	SIZE	DRAWING NO. 514719	514719			
<u> </u>	T	~ <u>~</u> ⊤	3	APP.	ARATI	19 81	VISIO	N DA	LLAS	TEXA	<u>•</u>	96214	Α					
3	$\mid$	1										SCALE	WT		SHEET	2		

		Paragraph No.					
1.	TABLE OF TESTS						
1.1	Preparation	3.1					
1.2	Room Temperature Test	3.2					
1.3	Low Temperature Test	3.3					
1.4	High Temperature Test	3.4					
2.	LIST OF TEST EQUIPMENT						
2.1	Data Sheets (TI Drawing 514726) shall be completed a	as part of this test.					
2.2	Verify that test equipment designated WORKING STANDARD, or better, is currently certified per TI Standard Procedure No. 12-28.						
2.3	Commercial Test Equipment - The following commercially available test equipment (or equivalent) is required to complete the test required by this specification.						
2.3.1	Oscilloscope - Tektronix 543/Plug in Type CA						
2.3.2	Power Supply, dc, 0-50 VDC, 5 amp Sorenson T50-1.5						
2.3.3	Pulse Generator, TI Model 6563						
2.3.4	Temperature Chamber - TI Controlled Environmental Un	nit					
2.4	Special Test Equipment - The following special test to complete the test required by this specification						
2.4.1	Test Set, Module, TI Drawing 514711						
2.4.2	Control Box, TI Drawing 514713						
2.4.3	Five Stage Counter, TI Drawing 514714						

TEXAS INSTRUMENTS							CODE IDENT NO.	SIZE	DRAWING NO. 514719		
5	<b>1</b>						96214	Α			
λS							SCALE	WT		SHEET	3

3.	TEST PROCEDURES
	The following test procedure covers the module test requirements to evaluate the D Output Gating No. 2 Module of the Integrated Circuit Sequence Generator.

- 3.1 Preparation
- 3.1.1 Visually inspect module for any mechanical faults such as wiring mistakes, broken leads, bad welds, etc. before plugging module into test set.
- 3.1.2 Adjust  $V_{cc}$  supply voltage to 3.1 VDC  $\pm$  0.1 VDC.
- 3.1.3 Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide) from 0 to  $+3V \pm 0.1V$  at a rate of  $1mc \pm 50KC$  with rise and fall times at a minimum (minimum ringing at 0 and +3 volts).

Caution: Only a positive going signal is to be applied to these modules.

- 3.1.4 Plug module into test set.
- 3.1.5 Connect test set to control box.
- 3.1.6 Connect  $V_{CC}$  to test point 25 and ground to test point 26 of control box.
- 3.1.7 Connect the five stage counter to control box as follows:

Counter Lead	Control Box					
<b>S</b> 1	No Connection					
<u>81</u>	Test Point 22 $(\overline{D_1})$					
<b>S</b> 2	Test Point 21 (D2)					
<u>\$2</u> <b>\$</b> 2	Test Point 8 $\overline{(D_2)}$					
S3	Test Point 16 (D <sub>3</sub> )					
<u>₹</u> 3	Test Point 23 $(\overline{D_3})$					
s <sub>4</sub>	Test Point 17 (D <sub>4</sub> )					
<del>3</del> 4	Test Point 10 $(\overline{D4})$					
s <sub>5</sub>	Test Point 24 (D <sub>5</sub> )					
<u>85</u>	Test Point 18 $(\overline{D_5})$					

Note: Oscilloscope should be triggered on the positive going edge of  $\overline{S_5}$ .

- 3.2 Room Temperature Test
- 3.2.1 Performance Test No. 1
  - a. Connect the following test points to Ground.
    - 1. TP 11 (D<sub>6</sub>)
    - 2. TP 4 (D<sub>7</sub>)

	TEXAS INSTRUMENTS							RUN	IEN	rs	CODE IDENT NO.	SIZE	DRAWING NO.	514719			
	56/					-AS. Y	XAS	96214	Α								
Š		$\top$				1					SCALE	WT			SHEET	4	

ъ	Connect the following test points to $V_{cc}$ .  1. TP 1 $(\overline{D_6})$ 2. TP 19 $(\overline{D_7})$
c.	Observe the output of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.  1. 3 - TP 20
3.2.2 Pe	erformance Test No. 2
a	Connect the following test points to Ground.  1. TP 1 (D6)  2. TP 4 (D7)
ъ	Connect the following test points to V <sub>cc</sub> .  1. TP 11 (D <sub>6</sub> )  2. TP 19 (D <sub>7</sub> )
c.	Observe the output of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.  1. 3 - TP 20
3.2.3 Pe	erformance Test No. 3
a	Connect the following test points to Ground.  1. TP 11 $(\underline{D}_6)$ 2. TP 19 $(\overline{D}_7)$
ь	Connect the following test points to $V_{CC}$ .  1. TP 1 $(\overline{D_6})$ 2. TP 4 $(D_7)$
c	Observe the output of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.  1. 3 - TP 20
3.2.4 P	erformance Test No. 4
а	Connect the following test points to Ground.  1. TP 1 (D <sub>6</sub> ) 2. TP 19 (D <sub>7</sub> )
Ъ	Connect the following test points to V <sub>CC</sub> .  1. TP 11 (D <sub>6</sub> ) 2. TP 4 (D <sub>7</sub> )
c	Observe the output of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.  1. 3 - TP 20
TEYAS IN	STRUMENTS CODE IDENT NO. SIZE DRAWING NO.
INCOR	ISION DALLAS, TEXAS 96214 A

SCALE

WT

SHEET

5

.....

3.3	Low Temperature Test
3.3.1	Precool temperature chamber to $-25^{\rm o}{\rm C}$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
3.3.2	Repeat 3.2.1
3.3.3	Repeat 3.2.2
3.3.4	Repeat 3.2.3
3.3.5	Repeat 3.2.4
3.4	High Temperature Test
3.4.1	Preheat temperature chamber to $+100^{\rm o}{\rm C}$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
3.4.2	Repeat 3.2.1
3.4.3	Repeat 3.2.2
3.4.3 3.4.4	Repeat 3.2.2 Repeat 3.2.3

	۲	47	TE	XAS	i l	STR	LUM	ENT	s	CODE IDENT NO.	SIZE	DRAWING NO.	514719		
<u> </u>	_	<b>&amp;</b>	APP	ARATU	18 81	/ISION	DALL	\S. TE	(AB	96214	Α	i			
SYM							$\perp$		1_	SCALE	WT			SHEET	6

CODE IDENT NO. CLOCK 55 SIZE DRAWING NO. TEXAS INSTRUMENTS
INCORPORATED
APPARATUS DIVISION DALLAS, TEXAS 514719 96214 A SYM. SCALE WT SHEET 7

2-5411

# 5. TABLE I

Performance Test	Function	<u>Output</u>
No. 1	3 8 <sub>5</sub>	111111110101010101011111101011111 111111
No. 2	3 \$5	00001101010111110011000100010011 1111111
No. 3	3 \$5	01110111010101011111111111111111111111
No. 4	3 S <sub>5</sub>	0000010101 <b>0</b> 1110111111110101111111 1111111111

	۲,	<b>42</b> 1	TE	XAS	IN	STR	UME	NTS	CODE IDENT NO.	SIZE	DRAWING NO.	L47 <b>1</b> 9			
-								96214	96214 A						
SYN									<b>\$CALE</b>	WT			SHEET	8	

REVISIONS SYM ZONE DESCRIPTION DATE **APPROVED** 0 Ñ NEXT ISSY NO. Š Š 0 INSPECTION TEST PROCEDURE PART I INDIVIDUAL TEST FOR D OUTPUT GATING NO. 1 MODULE INTEGRATED CIRCUIT SEQUENCE GENERATOR CONTRACT NO. 950693 MANUFACTURER - TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514727 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE. TEXAS INSTRUMENTS GOVT OR INDUSTRY ITEM DWG NOMENCLATURE OR DESCRIPTION NO. QTY REQD PART OR IDENTIFYING NO. LIST O F MATERIALS DR DATE Texas Instruments 27/64 INCORPORATED APPARATUS DIVISION DALLAS, TEXAS TITLE **ENGR** TEST PROCEDURE, INSPECTION, APPD PART I, INDIVIDUAL TEST, D OUTPUT GATING NO. 1 MODULE DESIGN ACTIVITY RELEASE CODE IDENT NO. SIZE DRAWING NO. 96214 5-27-64 Α 514720 1 of 9 **SCALE** WT SHEET TI-1E1793.A

## TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	3
3.1	Preparation	3
3.2	Room Temperature Test	5
3.3	Low Temperature Test	6
3.4	High Temperature Test	7
4.	DIAGRAMS	8
5.	TABLE I	9

Γ	TEXAS INSTRUMENTS								ENTS	CODE IDENT NO.	SIZE	SIZE DRAWING NO.		
										96214	96214 A 514720			
λX										SCALE	WT	SHEET	2	

Paragraph No.

3.4

#### 1. TABLE OF TESTS

1.4

1.1	Preparation	3.1
1.2	Room Temperature Test	3.2
1.3	Low Temperature Test	3.3

## 2. LIST TEST EQUIPMENT

High Temperature Test

- 2.1 Data Sheets (TI Drawing 514727) shall be completed as part of this test.
- 2.2 Verify that equipment designated working standard, or better, is currently certified per TI Std. Procedure No. 12-28.
- 2.3 Commercial Test Equipment The following commercially available test equipment (or equivalent) is required to complete the test required by this specification.
- 2.3.1 Oscilloscope Tektronix 543/Plug-in Type CA.
- 2.3.2 Power Supply Sorenson T50-1.5.
- 2.3.3 Pulse Generator TI Model 6563.
- 2.3.4 Temperature Chamber TI Controlled Environmental Unit.
- 2.4 Special Test Equipment The following special test equipment is required to complete the test required by this specification.
- 2.4.1 Test Set, Module, TI Drawing 514711.
- 2.4.2 Control Box, TI Drawing 514713.
- 2.4.3 Five Stage Counter, TI Drawing 514714.

#### TEST PROCEDURES

The following test procedure covers the module test requirements to evaluate the D Output Gating No. 1 Module of the Integrated Circuit Sequence Generator.

## 3.1 Preparation

	TEXAS INSTRUMENTS								CODE IDENT NO.	SIZE	DRAWING NO.		
¥.	<b>50</b> /								96214	96214 A 514720			
Š									SCALE	WT		SHEET	3

- 3.1.1 Visually inspect module for any mechanical faults such as wiring mistakes, broken leads, bad welds, etc.before plugging module into test set.
- 3.1.2 Adjust  $V_{CC}$  supply voltage to 3.1 VDC  $\pm$ 0.1 VDC.
- 3.1.3 Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide). from 0 to  $+3V \pm 0.1V$  at a rate of 1 mc  $\pm 50KC$  with rise and fall times at a minimum (minimum ringing at 0 and  $\pm 3$  volts).

CAUTION: Only a positive going signal is to be applied to these modules.

- 3.1.4 Plug module into test set.
- 3.1.5 Connect GRD to TP 26 of control box.
- 3.1.6 Connect  $V_{CC}$  to TP 25 of control box.
- 3.1.7 Connect test set to control box.
- 3.1.8 Connect five stage counter to control.box as follows.

	Counter	Control Box
a.	$s_1$	T.P. 2 (D <sub>1</sub> )
ъ.	s <sub>2</sub>	T.P. 16 (D <sub>2</sub> )
c.	$\overline{s_2}$	T.P. 8 $(\overline{D_2})$
d.	s <sub>3</sub>	T.P. 1 (D <sub>3</sub> )
e.	$\overline{s_3}$	T.P. 10 $(\overline{D_3})$
f.	s <sub>4</sub>	T.P. 3 (D4)
g.	$\overline{s_4}$	T.P. 11 $(\overline{D_4})$
h.	s <sub>5</sub>	T.P. 24 (D <sub>5</sub> )
i.	<u>s</u>	T.P.18 (D <sub>5</sub> )

Note: Oscilloscope should be triggered on the positive going edge of  $\overline{S_5}$  of the five bit counter.

r	TEXAS INSTRUMENTS											CODE IDENT NO.	SIZE	SIZE DRAWING NO.		
<b> </b>										96214	Α	514720				
2	<u>;</u>											SCALE	WT		SHEET 4	

3.2	Room	Temperature	Test
-----	------	-------------	------

## 3.2.1 Performance Test No. 1

- a. Connect the following test points to GRD.
  - 1. T.P. 4 (D<sub>6</sub>)
  - 2. T.P. 12 (D<sub>7</sub>)
- b. Connect V<sub>CC</sub> to the following test points.
  - 1. T.P. 9  $(\overline{D_6})$
  - 2. T.P. 5  $(\overline{D_7})$
- c. Observe the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
  - 1. 3

T.P. 6

2. I

T.P. 17

3.  $\overline{D}$ 

T.P. 21

## 3.2.2 Performance Test No. 2

- a. Connect the following test points to GRD.
  - 1. T.P. 9  $(\overline{D_6})$
  - 2. T.P. 12 (D<sub>7</sub>)
- b. Connect the following test points to  $V_{\mbox{\footnotesize CC}}$ .
  - 1. T.P. 4  $(D_6)$
  - 2. T.P. 5  $(\overline{D_7})$
- c. Osberve the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
  - 1. 3

T.P. 6

2. D

T.P. 17

3.  $\overline{D}$ 

T.P. 21

	TEXAS INSTRUMENTS								CODE IDENT NO.	SIZE	DRAWING NO.		
5	<b>40</b> /								96214	Α	514720		
2									SCALE	WT		SHEET 5	

Ti-5419

3.	.2,	. 3	Performance	Test	No,	3
----	-----	-----	-------------	------	-----	---

- Connect the following test points to GRD.
  - 1. T.P. 4 (D<sub>6</sub>)
  - 2. T.P. 5  $(\overline{D_7})$
- b. Connect the following test points to  $V_{\rm CC}$ .
  - 1. T.P. 9  $(\overline{D_6})$
  - 2. T.P. 12 (D<sub>7</sub>)
- c. Observe the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
  - 1. 3

T.P.

2. D

T.P. 17

3. D

T.P. 21

## 3.2.4 Performance Test No. 4

- a. Connect the following test points to GRD.
  - 1. T.P. 9  $(\overline{D_6})$
  - 2. T.P. 5  $(\overline{D_7})$
- b. Connect the following test points to  $V_{CC}$ .
  - 1. T.P. 4  $(D_6)$
  - 2. T.P. 12 (D<sub>7</sub>)
- c. Observe the outputs of the module on the oscilloscope. See Diagram, Section 4, and Table I, Section 5.
  - 1 3

T.P. 6

2. D

T.P. 17

3. D

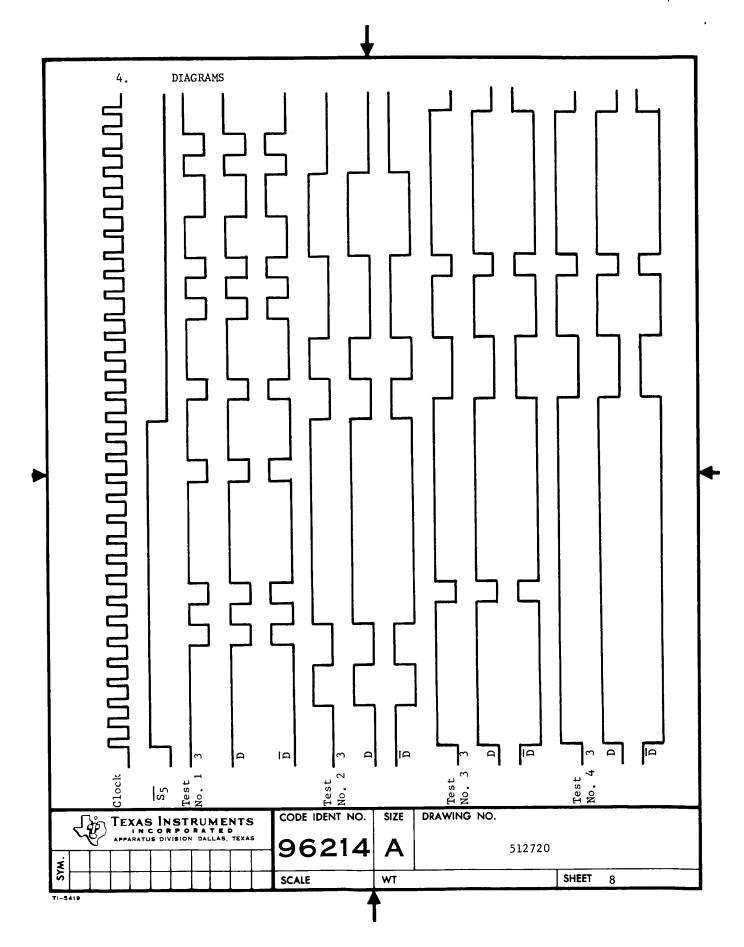
T. P. 21

## 3.3 Low Temperature Test

	TEXAS INSTRUMENTS								NTS	CODE IDENT NO.	SIZE	SIZE DRAWING NO.			
¥		<b>8</b>							TEXAS	96214	Α	514720			
λS		T	1	$\top$	$\top$	$\top$				SCALE	WT		SHEET 6		

- 3.3.1 Precool temperature chamber to  $-25^{\circ}\text{C}$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
- 3.3.2 Repeat 3.2.1.
- 3.3.3 Repeat 3.2.2.
- 3.3.4. Repeat 3.2.3.
- 3.3.5 Repeat 3.2.4.
- 3.4 High Temperature Test
- 3.4.1 Preheat temperature chamber to  $\pm 100^{\circ} C$ . Place test set, with module plugged-in, inside and allow one half hour for stabilization.
- 3.4.2 Repeat 3.2.1.
- 3.4.3 Repeat 3.2.2.
- 3.4.4 Repeat 3.2.3.
- 3.4.5 Repeat 3.2.4.

TEXAS INSTRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.		
50/	96214	Α	514720		
۵	SCALE	WT		SHEET 7	



# 5. TABLE I

Performance Test	Function	Output
No. 1	3	11111010111110111011101011001011
	D	111110101111110111011101011001011
	$\overline{\mathtt{D}}$	00000101000001000100010100110100
	$\overline{s_5}$	111111111111111110000000000000000000000
No. 2	3	001100111111111110011000011110000
	D	0011001111111111100110000111110000
	$\overline{\mathtt{D}}$	11001100000000001100111100001111
	$\overline{s_5}$	111111111111111110000000000000000000000
No. 3	3	1111111011111111110001110111111110
	D	1111111011111111110001110111111110
	$\overline{\mathtt{D}}$	00000001000000000111000100000001
	$\overline{s_5}$	111111111111111110000000000000000000000
No. 4	3	1111111111111111110001110111111110
	D	1111111111111111110001110111111110
	$\overline{\overline{D}}$	0000000000000000111000100000001
	$\overline{s_5}$	111111111111111100000000000000000000000

TEXAS INSTRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.		
APPARATUS DIVISION DALLAS, TEXAS	96214	Α	514720		
8	SCALE	WT		SHEET 9	

1-5411

REVISIONS SYM ZONE DESCRIPTION DATE APPROVED **2** 0 INSPECTION TEST PROCEDURE PART I INDIVIDUAL TEST FOR X, A, B, C, AND E CODE SEQUENCE GENERATOR MODULES INTEGRATED CIRCUIT SEQUENCE GENERATOR CONTRACT NO. 950693 MANUFACTURER- TEXAS INSTRUMENTS INCORPORATED TEST DATA SHEET 514728 TO BE FILLED OUT AS PART OF THIS TEST PROCEDURE TEXAS INSTRUMENTS GOVT OR INDUSTRY ITEM DWG NOMENCLATURE OR DESCRIPTION SIZE NO. QTY REQD PART OR IDENTIFYING NO. LIST O F MATERIALS DR DATE TEXAS INSTRUMENTS jc/ < INCORPORATED CKD APPARATUS DIVISION DALLAS, TEXAS TITLE ENGR TEST PROCEDURE, INSPECTION, PART I, INDIVIDUAL TEST, X, A, B, C, AND E CODE SEQUENCE GENERATOR MODULES DESIGN ACTIVITY RELEASE CODE IDENT NO. SIZE DRAWING NO. Pet 5.77.10 96214 514721 **SCALE** WT SHEET 1 of 7 TI-1E1793.A

## TABLE OF CONTENTS

Paragraph No.	Title	Sheet No.
1.	TABLE OF TESTS	3
2.	LIST OF TEST EQUIPMENT	3
3.	TEST PROCEDURES	3
3.1	Preparation	4
3.2	Room Temperature Test	4
3.3	Low Temperature Test	5
3.4	High Temperature Test	5
4.	DIAGRAMS	6
5.	TABLE I	7

T AT IEXAS INSTRUMENTS	CODE IDENT NO.	SIZE	DRAWING NO.
<b>CAC</b> 3/	96214	Α	514721
5	SCALE	WT	SHEET 2

Paragraph No. 1. TABLE OF TESTS 1.1 Preparation 3.1 1.2 Room Temperature Test 3.2 1.3 Low Temperature Test 3.3 1.4 High Temperature Test 3.4 2. LIST OF TEST EQUIPMENT 2.1 Data Sheets (TI Drawing 514728) shall be completed as a part of this test. 2.2 Verify that test equipment designated WORKING STANDARD, or better, is currently certified per TI Std. Procedure No. 12-28. Commercial Test Equipment - The following commercially available test 2.3 equipment (or equivalent) is required to complete the tests required by this specification. 2.3.1 Oscilloscope - Tektronix 543/Plug in type CA 2.3.2 Power Supply - Sorenson T50 - 1.5 2.3.3 Pulse Generator - TI Model 6563 2.3.4 Temperature Chamber - TI Controlled Environmental Unit 2.4 Special Test Equipment - The following special test equipment is required to complete the tests required by this specification. 2.4.1 Test Set, Module, (Red, White, Green Connector), TI Drawing No. 514710. 2.4.2 Control Box, TI Drawing No. 514712. 3. TEST PROCEDURES The following test procedures cover the module test requirements to evaluate the X, A, B, C, and E Code Sequence Generator Modules of the

	INCORPORATED							LUM	ENT	S	CODE IDENT NO.	ODE IDENT NO. SIZE DRAWING NO			
·	Ī	T	<u>}</u>						AS, TE	ias	96214	Α	514721		
λ											SCALE	WT		SHEET	3

Integrated Circuit Sequence Generator.

- 3.1.1 Visually inspect module for any mechanical faults such as wiring mistakes, broken leads, bad welds, etc. before plugging module into test set.
- 3.1.2 Adjust  $V_{CC}$  supply voltage to 3.1V.D.C.  $\pm$ 0.1V.D.C.
- 3.1.3 Adjust pulse generator for a positive going pulse (50 nsec to 500 nsec wide) from 0 to +3V ±0.1V at a rate of 1 mc ±50KC with rise and fall times at a minimum (minimum ringing at 0 and 3V).

  CAUTION: Only a positive-going signal is to be applied to these

3.1.4 Plug module into test set.

modules.

a. X Code Generator

Red Connector

b. A Code Generator

White or Green Connector

c. B Code Generator

White or Green Connector

d. C Code Generator

White or Green Connector

e. E Code Generator

White or Green Connector

- 3.2 Room Temperature Test
- 3.2.1 Connect test set to control box.
- 3.2.2 Observe the outputs of the module under test on oscilloscope at the test points on the control box. See Diagram, Section 4, and Table I, Section 5.

	Output	Test	Point
а.	X Code	Red	1
ъ.	$\overline{X}$ Code	Red	2
c.	X Word	Red	3
d.	CL	Red	4
e.	CL	Red	5
f.	S.P.	Red	6
۷.	T	Red	. 7

Г	TEXAS INSTRUMENTS							RU	ΜE	NTS	}	CODE IDENT NO.	SIZE	SIZE DRAWING NO.		
<u> </u>	APPARATUS DIVISION DALLAS, TEXAS											96214	Α	514721		
ζ			Ţ									SCALE	WT	SHEET 4		

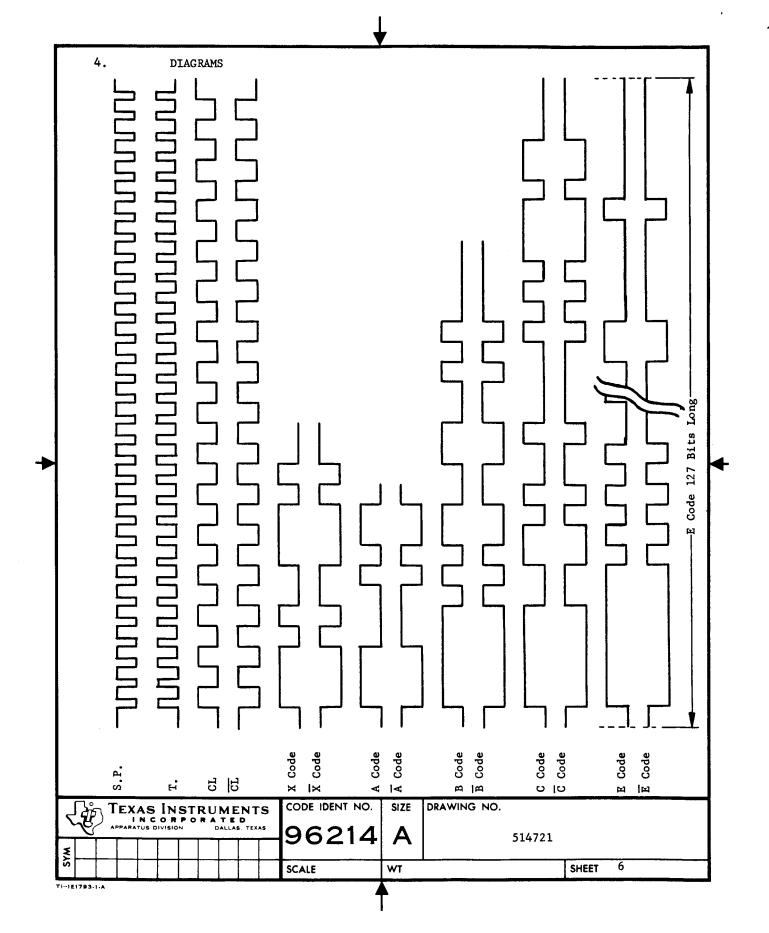
	Output	Test Point				
h.	A Code	White 6	Green 6			
i.	Ā Code	White 2	Green 2			
j.	A Word	White 5	Green 5			
k.	B Code	White 5	Green 5			
1.	B Code	White 6	Green 6			
m.	B Word	White 4	Green 4			
n.	C Code	White 3	Green 3			
٥.	$\overline{C}$ Code	White 5	Green 5			
p.	C Word	White 1	Green 1			
q.	E Code	White 3	Green 3			
r.	E Code	White 5	Green 5			
8.	E Word	White 6	Green 6			

NOTE: More than one module may be tested at a time. The outputs of the modules under test will appear at test points corresponding to the color of the module connector. The oscilloscope should be triggered on the positive-going edge of the module word under test.

- 3.3 Low Temperature Test.
- 3.3.1 Precool temperature chamber to -25°C. Place test set, with module plugged in, inside and allow one half hour for stabilization.
- 3.3.2 Repeat paragraph 3.2.1.
- 3.3.3 Repeat paragraph 3.2.2.
- 3.4 High Temperature Test
- 3.4.1 Preheat temperature chamber to +100°C. Place test set, with module plugged in, inside and allow one half hour for stabilization.
- 3.4.2 Repeat paragraph 3.2.1.
- 3.4.3 Repeat paragraph 3.2.2.

Г	TEXAS INSTRUMENTS								CODE IDENT NO.	SIZE	DRAWING NO.	
	<b>C</b>								96214	Α	514721	
XX									SCALE	WT		SHEET 5

T!-5419



5. TABLE I

> Function Output X Code 1110100

> $\overline{X}$  Code 0001011

CL 10 CL 01

A Code 11100010110

 $\overline{A}$  Code 00011101001 B Code 11111010110011001010000

B Code 00000101001100110101111

C Code 1111100110100100001010111011000

C Code 0000011001011011110101000100111

E Code

111000101000011000001000000

E Code 

0001110101111100111110111111

Γ	TEXAS INSTRUMENTS CODE IDEN								CODE IDENT NO.	SIZE	DRAWING NO.		
×	Γ	1	APP	RATUS	DIVIS	ON DA	ALLAS, TEXA	5	96214	Α	514721		
Š									SCALE	WT	1	SHEET	7

Ti-5419